- 8- to 14-bit parallel camera interface up to 54 Mbytes/s
- 96-bit unique ID
- RTC: subsecond accuracy, hardware calendar
- True random number generator
- CRC calculation unit

Table 1.	Device	summary

Reference	Part number
STM32F405xx	STM32F405RG, STM32F405VG, STM32F405ZG, STM32F405OG, STM32F405OE
STM32F407xx	STM32F407VG, STM32F407IG, STM32F407ZG, STM32F407VE, STM32F407ZE, STM32F407IE



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## 1 Introduction

This datasheet provides the description of the STM32F405xx and STM32F407xx lines of microcontrollers. For more details on the whole STMicroelectronics STM32<sup>™</sup> family, please refer to Section 2.1: Full compatibility throughout the family.

The STM32F405xx and STM32F407xx datasheet should be read in conjunction with the STM32F4xx reference manual which is available from the STMicroelectronics website *www.st.com*.

For information on the Arm<sup>®(a)</sup> Cortex<sup>®</sup>-M4 core, please refer to the Cortex<sup>®</sup>-M4 programming manual (PM0214) available from <u>www.st.com</u>.





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## 2 Description

The STM32F405xx and STM32F407xx family is based on the high-performance Arm<sup>®</sup> Cortex<sup>®</sup>-M4 32-bit RISC core operating at a frequency of up to 168 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all Arm single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F405xx and STM32F407xx family incorporates high-speed embedded memories (Flash memory up to 1 Mbyte, up to 192 Kbytes of SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers. a true random number generator (RNG). They also feature standard and advanced communication interfaces.

- Up to three I<sup>2</sup>Cs
- Three SPIs, two I<sup>2</sup>Ss full duplex. To achieve audio class accuracy, the I2S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus two UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- An SDIO/MMC interface
- Ethernet and the camera interface available on STM32F407xx devices only.

New advanced peripherals include an SDIO, an enhanced flexible static memory control (FSMC) interface (for devices offered in packages of 100 pins and more), a camera interface for CMOS sensors. Refer to *Table 2: STM32F405xx and STM32F407xx: features and peripheral counts* for the list of peripherals available on each part number.

The STM32F405xx and STM32F407xx family operates in the –40 to +105 °C temperature range from a 1.8 to 3.6 V power supply. The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor: refer to *Section : Internal reset OFF*. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F405xx and STM32F407xx family offers devices in various packages ranging from 64 pins to 176 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F405xx and STM32F407xx microcontroller family suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances



Figure 5 shows the general block diagram of the device family.

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		ladi	Iable 2. STIM32F405XX and STIM32F40/XX: reatures and peripheral counts		zr 40 / XX: Teatur	es and peripne	eral cou	nts				
Perip	Peripherals	STM32F405RG	STM32F405OG STM32F405VG	STM32F405VG	STM32F405ZG	STM32F405OE	STM32F407Vx	407Vx	STM32F407Zx	=407Zx	STM32F407Ix	=407Ix
Flash memory in Kbytes	nory in		1024	24		512	512	1024	512	1024	512	1024
SRAM in	System				192(112+16+64)	16+64)						
Kbytes	Backup				4							
FSMC memory controller	mory	No				Yes <sup>(1)</sup>						
Ethernet				No					Yes	s		
	General- purpose				10							
	Advanced -control				2							
Timers	Basic				2							
	IWDG				Yes							
	WWDG				Yes							
	RTC				Yes							
True rando generator	True random number generator				Yes							

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5			Table 2. STM32F	ТМ32F405хх аі	nd STM32F407	'xx: features an	:405xx and STM32F407xx: features and peripheral counts (continued)	ounts (continu	ed)	
7/	Perip	Peripherals	STM32F405RG	STM32F4050G	STM32F405VG	STM32F405ZG	STM32F405OE	STM32F407Vx	STM32F407Zx	STM32F407Ix
		SPI / 12S				3/2 (full duplex) <sup>(2)</sup>	uplex) <sup>(2)</sup>			
		l <sup>2</sup> C				3				
		USART/ UART				4/2	6			
	Communi cation interfaces	USB OTG FS				Yes	ω			
		USB OTG HS				Yes	S			
		CAN				0				
		SDIO				Yes	S			
	Camera interface	terface			No				Yes	
DS8	GPIOs		51	72	82	114	72	82	114	140
626	12-bit ADC					3				
Rev	Number of channels	<sup>c</sup> hannels	16	13	16	24	13	16	24	24
/ 9	12-bit DAC Number of channels	channels				Yes 2	- v			
	Maximum CPU frequency	сРU				168 MHz	MHz			
	Operating voltage	voltage				1.8 to 3.6 V <sup>(3)</sup>	.6 V <sup>(3)</sup>			
	Operating				Ambient te	mperatures: -40	Ambient temperatures: –40 to +85 $^\circ\text{C}$ /–40 to +105 $^\circ\text{C}$	+105 °C		
	temperatures	es			Jur	nction temperature	Junction temperature: -40 to + 125 °C			
	Package		LQFP64	WLCSP90	LQFP100	LQFP144	WLCSP90	LQFP100	LQFP144	UFBGA176 LQFP176
	<ol> <li>For the L Select. B package.</li> <li>The SPI2</li> </ol>	QFP100 and ank2 can on and SPI3 in	J WLCSP90 package Ily support a 16- or 8 Interfaces give the fley	es, only FSMC Bank -bit NAND Flash me cibility to work in an	1 or Bank2 are ava mory using the NC exclusive way in eit	ilable. Bank1 can o E2 Chip Select. The ther the SPI mode o	For the LQFP100 and WLCSP90 packages, only FSMC Bank1 or Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package. The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I <sup>2</sup> S audio mode.	exed NOR/PSRAV t be used since Po	l memory using the rt G is not available	NE1 Chip in this

## STM32F405xx, STM32F407xx

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с.

V<sub>DD</sub>V<sub>DDA</sub> minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to Section : Internal reset OFF).

## 2.1 Full compatibility throughout the family

The STM32F405xx and STM32F407xx are part of the STM32F4 family. They are fully pinto-pin, software and feature compatible with the STM32F2xx devices, allowing the user to try different memory densities, peripherals, and performances (FPU, higher frequency) for a greater degree of freedom during the development cycle.

The STM32F405xx and STM32F407xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F405xx and STM32F407xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F40xxx family remains simple as only a few pins are impacted.

*Figure 4*, *Figure 3*, *Figure 2*, and *Figure 1* give compatible board designs between the STM32F40xxx, STM32F2, and STM32F10xxx families.

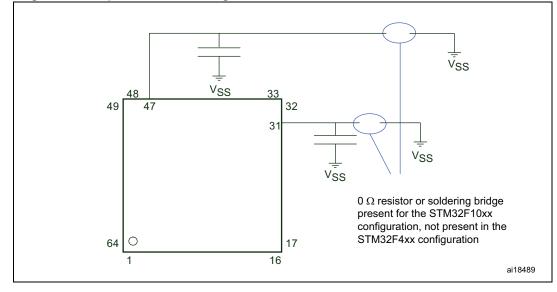
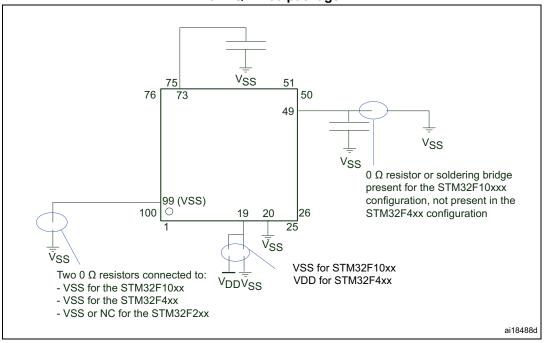


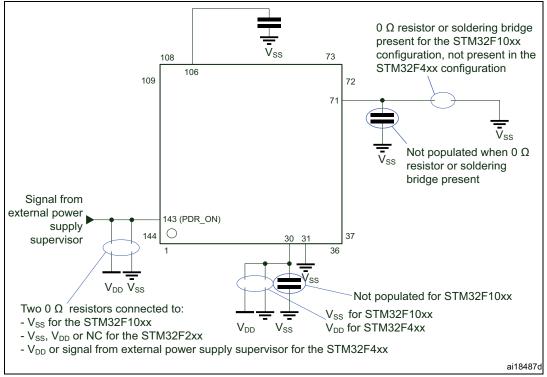
Figure 1. Compatible board design between STM32F10xx/STM32F40xxx for LQFP64





#### Figure 2. Compatible board design STM32F10xx/STM32F2/STM32F40xxx for LQFP100 package

Figure 3. Compatible board design between STM32F10xx/STM32F2/STM32F40xxx for LQFP144 package



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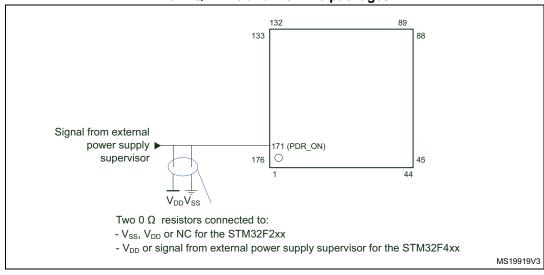
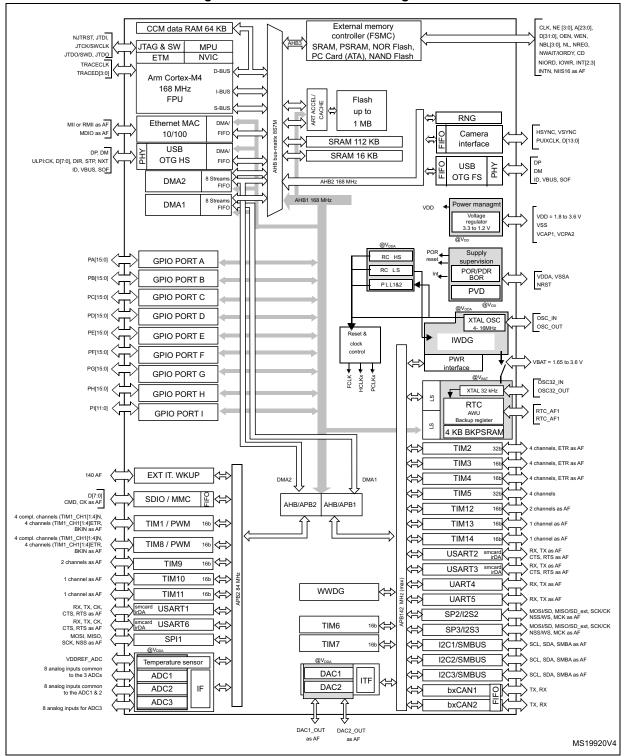


Figure 4. Compatible board design between STM32F2 and STM32F40xxx for LQFP176 and BGA176 packages



## 2.2 Functional overview



#### Figure 5. STM32F40xxx block diagram

1. The camera interface and ethernet are available only on STM32F407xx devices.



## 2.2.1 Arm<sup>®</sup> Cortex<sup>®</sup>-M4 core with FPU and embedded Flash and SRAM

The Arm Cortex-M4 processor with FPU is the latest generation of Arm processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The Arm Cortex-M4 32-bit RISC processor with FPU features exceptional code-efficiency, delivering the high-performance expected from an Arm core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU (floating point unit) speeds up software development by using metalanguage development tools, while avoiding saturation.

The STM32F405xx and STM32F407xx family is compatible with all Arm tools and software.

*Figure 5* shows the general block diagram of the STM32F40xxx family.

Note: Cortex-M4 with FPU is binary compatible with Cortex-M3.

### 2.2.2 Adaptive real-time memory accelerator (ART Accelerator)

The ART Accelerator is a memory accelerator which is optimized for STM32 industrystandard Arm<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU processors. It balances the inherent performance advantage of the Arm Cortex-M4 with FPU over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor full 210 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 128-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 168 MHz.

## 2.2.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

## 2.2.4 Embedded Flash memory

The STM32F40xxx devices embed a Flash memory of 512 Kbytes or 1 Mbytes available for storing programs and data, plus 512 bytes of OTP memory.



## 2.2.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

## 2.2.6 Embedded SRAM

All STM32F40xxx products embed:

 Up to 192 Kbytes of system SRAM including 64 Kbytes of CCM (core coupled memory) data RAM

RAM memory is accessed (read/write) at CPU clock speed with 0 wait states.

4 Kbytes of backup SRAM

This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

## 2.2.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS) and the slaves (Flash memory, RAM, FSMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.



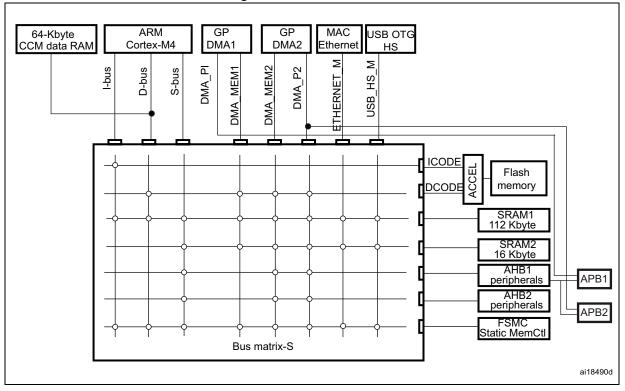


Figure 6. Multi-AHB matrix

## 2.2.8 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals:

- SPI and I<sup>2</sup>S
- I<sup>2</sup>C
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Camera interface (DCMI)
- ADC.



## 2.2.9 Flexible static memory controller (FSMC)

The FSMC is embedded in the STM32F405xx and STM32F407xx family. It has four Chip Select outputs supporting the following modes: PCCard/Compact Flash, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- Write FIFO
- Maximum FSMC\_CLK frequency for synchronous accesses is 60 MHz.

## LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

## 2.2.10 Nested vectored interrupt controller (NVIC)

The STM32F405xx and STM32F407xx embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 82 maskable interrupt channels plus the 16 interrupt lines of the Cortex<sup>®</sup>-M4 with FPU core.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

## 2.2.11 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 23 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 140 GPIOs can be connected to the 16 external interrupt lines.

## 2.2.12 Clocks and startup

On reset the 16 MHz internal RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy over the full temperature range. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock can be monitored for failure. If a failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 168 MHz. Similarly, full interrupt management of the PLL



clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the three AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the three AHB buses is 168 MHz while the maximum frequency of the high-speed APB domains is 84 MHz. The maximum allowed frequency of the low-speed APB domain is 42 MHz.

The devices embed a dedicated PLL (PLLI2S) which allows to achieve audio class performance. In this case, the  $I^2S$  master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

### 2.2.13 Boot modes

At startup, boot pins are used to select one out of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART1 (PA9/PA10), USART3 (PC10/PC11 or PB10/PB11), CAN2 (PB5/PB13), USB OTG FS in Device mode (PA11/PA12) through DFU (device firmware upgrade).

#### 2.2.14 Power supply schemes

- V<sub>DD</sub> = 1.8 to 3.6 V: external power supply for I/Os and the internal regulator (when enabled), provided externally through V<sub>DD</sub> pins.
- V<sub>SSA</sub>, V<sub>DDA</sub> = 1.8 to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL. V<sub>DDA</sub> and V<sub>SSA</sub> must be connected to V<sub>DD</sub> and V<sub>SS</sub>, respectively.
- V<sub>BAT</sub> = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V<sub>DD</sub> is not present.

Refer to Figure 21: Power supply scheme for more details.

*Note:* V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to Section : Internal reset OFF).

Refer to Table 2 in order to identify the packages supporting this option.

#### 2.2.15 Power supply supervisor

#### Internal reset ON

On packages embedding the PDR\_ON pin, the power supply supervisor is enabled by holding PDR\_ON high. On all other packages, the power supply supervisor is always enabled.

The device has an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR/PDR is always active and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default BOR threshold levels, or to disable BOR permanently. Three BOR thresholds are available through option bytes. The device remains in reset mode when V<sub>DD</sub> is below a specified threshold, V<sub>POR/PDR</sub> or V<sub>BOR</sub>, without the need for an external reset circuit.



The device also features an embedded programmable voltage detector (PVD) that monitors the  $V_{DD}/V_{DDA}$  power supply and compares it to the  $V_{PVD}$  threshold. An interrupt can be generated when  $V_{DD}/V_{DDA}$  drops below the  $V_{PVD}$  threshold and/or when  $V_{DD}/V_{DDA}$  is higher than the  $V_{PVD}$  threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

#### **Internal reset OFF**

This feature is available only on packages featuring the PDR\_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled with the PDR\_ON pin.

An external power supply supervisor should monitor  $V_{DD}$  and should maintain the device in reset mode as long as  $V_{DD}$  is below a specified threshold. PDR\_ON should be connected to this external power supply supervisor. Refer to *Figure 7: Power supply supervisor interconnection with internal reset OFF*.

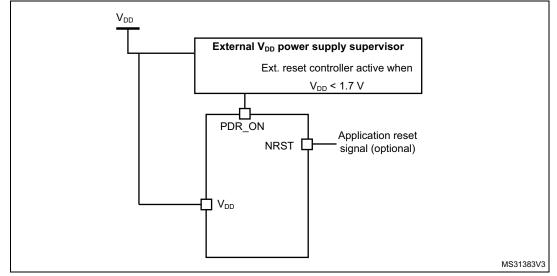


Figure 7. Power supply supervisor interconnection with internal reset OFF

1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

The V<sub>DD</sub> specified threshold, below which the device must be maintained under reset, is 1.8 V (see *Figure 7*). This supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range.

A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry is disabled
- The embedded programmable voltage detector (PVD) is disabled
- V<sub>BAT</sub> functionality is no more available and V<sub>BAT</sub> pin should be connected to V<sub>DD</sub>

All packages, except for the LQFP64 and LQFP100, allow to disable the internal reset through the PDR\_ON signal.



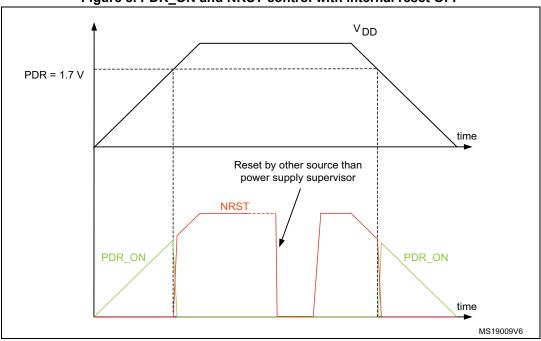


Figure 8. PDR\_ON and NRST control with internal reset OFF

1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

## 2.2.16 Voltage regulator

The regulator has four operating modes:

- Regulator ON
  - Main regulator mode (MR)
  - Low-power regulator (LPR)
  - Power-down
- Regulator OFF

### **Regulator ON**

On packages embedding the BYPASS\_REG pin, the regulator is enabled by holding BYPASS\_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when regulator is ON:

- MR is used in the nominal regulation mode (With different voltage scaling in Run) In Main regulator mode (MR mode), different voltage scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption. Refer to *Table 14: General operating conditions*.
- LPR is used in the Stop modes
   The LP regulator mode is configured by software when entering Stop mode.
- Power-down is used in Standby mode.
  - The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost)



Two external ceramic capacitors should be connected on  $V_{CAP_1} \& V_{CAP_2}$  pin. Refer to *Figure 21: Power supply scheme* and *Figure 16: VCAP\_1/VCAP\_2 operating conditions*.

All packages have regulator ON feature.

#### **Regulator OFF**

This feature is available only on packages featuring the BYPASS\_REG pin. The regulator is disabled by holding BYPASS\_REG high. The regulator OFF mode allows to supply externally a  $V_{12}$  voltage source through  $V_{CAP}$  1 and  $V_{CAP}$  2 pins.

Since the internal voltage scaling is not manage internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 14: General operating conditions*.

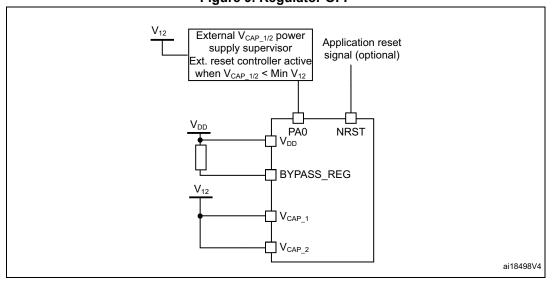
The two 2.2  $\mu\text{F}$  ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

Refer to Figure 21: Power supply scheme

When the regulator is OFF, there is no more internal monitoring on  $V_{12}$ . An external power supply supervisor should be used to monitor the  $V_{12}$  of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on  $V_{12}$  power domain.

In regulator OFF mode the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V<sub>12</sub> logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The standby mode is not available



#### Figure 9. Regulator OFF



The following conditions must be respected:

- V<sub>DD</sub> should always be higher than V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> to avoid current injection between power domains.
- If the time for V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> to reach V<sub>12</sub> minimum value is faster than the time for V<sub>DD</sub> to reach 1.8 V, then PA0 should be kept low to cover both conditions: until V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> reach V<sub>12</sub> minimum value and until V<sub>DD</sub> reaches 1.8 V (see *Figure 10*).
- Otherwise, if the time for V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> to reach V<sub>12</sub> minimum value is slower than the time for V<sub>DD</sub> to reach 1.8 V, then PA0 could be asserted low externally (see *Figure 11*).
- If V<sub>CAP\_1</sub> and V<sub>CAP\_2</sub> go below V<sub>12</sub> minimum value and V<sub>DD</sub> is higher than 1.8 V, then a reset must be asserted on PA0 pin.
- Note: The minimum value of V<sub>12</sub> depends on the maximum frequency targeted in the application (see Table 14: General operating conditions).

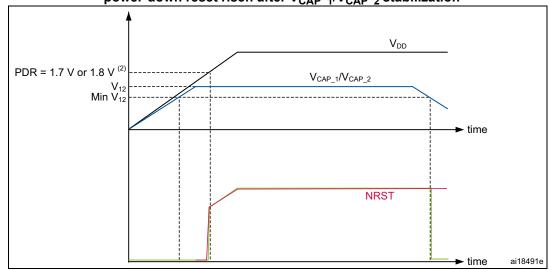


Figure 10. Startup in regulator OFF mode: slow  $V_{DD}$  slope - power-down reset risen after  $V_{CAP}$   $_1/V_{CAP}$   $_2$  stabilization

1. This figure is valid both whatever the internal reset mode (ON or OFF).

2. PDR = 1.7 V for reduced temperature range; PDR = 1.8 V for all temperature ranges.



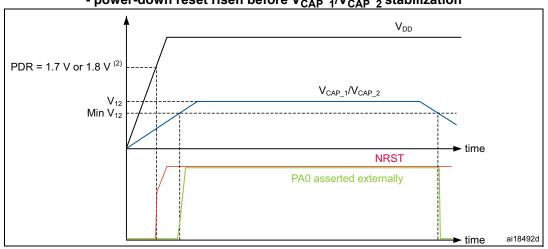


Figure 11. Startup in regulator OFF mode: fast  $V_{DD}$  slope - power-down reset risen before  $V_{CAP}$  <sub>1</sub>/ $V_{CAP}$  <sub>2</sub> stabilization

1. This figure is valid both whatever the internal reset mode (ON or OFF).

2. PDR = 1.7 V for a reduced temperature range; PDR = 1.8 V for all temperature ranges.

## 2.2.17 Regulator ON/OFF and internal reset ON/OFF availability

	Regulator ON	Regulator OFF	Internal reset ON	Internal reset OFF
LQFP64 LQFP100	Yes	No	Yes	No
LQFP144				Yes
WLCSP90 UFBGA176 LQFP176	Yes BYPASS_REG set to V <sub>SS</sub>	Yes BYPASS_REG set to V <sub>DD</sub>	Yes PDR_ON set to V <sub>DD</sub>	PDR_ON connected to an external power supply supervisor

Table 3. Regulator ON/OFF and internal reset ON/OFF availability

## 2.2.18 Real-time clock (RTC), backup SRAM and backup registers

The backup domain of the STM32F405xx and STM32F407xx includes:

- The real-time clock (RTC)
- 4 Kbytes of backup SRAM
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC



has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 µs to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The 4-Kbyte backup SRAM is an EEPROM-like memory area. It can be used to store data which need to be retained in  $V_{BAT}$  and standby mode. This memory area is disabled by default to minimize power consumption (see *Section 2.2.19: Low-power modes*). It can be enabled by software.

The backup registers are 32-bit registers used to store 80 bytes of user application data when  $V_{DD}$  power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see Section 2.2.19: Low-power modes).

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the  $V_{DD}$  supply when present or from the  $V_{BAT}$  pin.

### 2.2.19 Low-power modes

The STM32F405xx and STM32F407xx support three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

#### Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

#### Stop mode

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the  $V_{12}$  domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup).

#### • Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire  $V_{12}$  domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering



Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

The standby mode is not supported when the embedded voltage regulator is by passed and the  $V_{12}$  domain is controlled by an external power.

## 2.2.20 V<sub>BAT</sub> operation

The  $V_{BAT}$  pin allows to power the device  $V_{BAT}$  domain from an external battery, an external supercapacitor, or from  $V_{DD}$  when no external battery and an external supercapacitor are present.

 $V_{BAT}$  operation is activated when  $V_{DD}$  is not present.

The V<sub>BAT</sub> pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from  $V_{BAT}$ , external interrupts and RTC alarm/events do not exit it from  $V_{BAT}$  operation.

When PDR\_ON pin is not connected to  $V_{DD}$  (internal reset OFF), the  $V_{BAT}$  functionality is no more available and  $V_{BAT}$  pin should be connected to  $V_{DD}$ .

#### 2.2.21 Timers and watchdogs

The STM32F405xx and STM32F407xx devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

*Table 4* compares the features of the advanced-control, general-purpose and basic timers.

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complemen- tary output	Max interface clock (MHz)	Max timer clock (MHz)
Advanced -control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	84	168

Table 4. Timer feature comparison



Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complemen- tary output	Max interface clock (MHz)	Max timer clock (MHz)
	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	42	84
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	42	84
General purpose	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	84	168
	TIM10 TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	84	168
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	42	84
	TIM13 , TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	42	84
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	42	84

Table 4. Timer feature comparison (continued)

### Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 and TIM8 support independent DMA request generation.



#### General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F40xxx devices (see *Table 4* for differences).

• TIM2, TIM3, TIM4, TIM5

The STM32F40xxx include 4 full-featured general-purpose timers: TIM2, TIM5, TIM3, and TIM4.The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.

The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

Any of these general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

#### • TIM9, TIM10, TIM11, TIM12, TIM13, and TIM14

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10, TIM11, TIM13, and TIM14 feature one independent channel, whereas TIM9 and TIM12 have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

#### **Basic timers TIM6 and TIM7**

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.

TIM6 and TIM7 support independent DMA request generation.

#### Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

#### Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.



#### SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

## 2.2.22 Inter-integrated circuit interface (I<sup>2</sup>C)

Up to three I<sup>2</sup>C bus interfaces can operate in multimaster and slave modes. They can support the Standard-mode (up to 100 kHz) and Fast-mode (up to 400 kHz). They support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

### 2.2.23 Universal synchronous/asynchronous receiver transmitters (USART)

The STM32F405xx and STM32F407xx embed four universal synchronous/asynchronous receiver transmitters (USART1, USART2, USART3 and USART6) and two universal asynchronous receiver transmitters (UART4 and UART5).

These six interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to communicate at speeds of up to 10.5 Mbit/s. The other available interfaces communicate at up to 5.25 Mbit/s.

USART1, USART2, USART3 and USART6 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.



USART name	Standard features	Modem (RTS/ CTS)	LIN	SPI master	irDA	Smartcard (ISO 7816)	Max. baud rate in Mbit/s (oversampling by 16)	Max. baud rate in Mbit/s (oversampling by 8)	APB mapping
USART1	х	х	х	х	х	х	5.25	10.5	APB2 (max. 84 MHz)
USART2	х	х	x	х	х	х	2.62	5.25	APB1 (max. 42 MHz)
USART3	х	х	x	х	х	х	2.62	5.25	APB1 (max. 42 MHz)
UART4	х	-	x	-	х	-	2.62	5.25	APB1 (max. 42 MHz)
UART5	х	-	x	-	х	-	2.62	5.25	APB1 (max. 42 MHz)
USART6	х	х	х	х	х	х	5.25	10.5	APB2 (max. 84 MHz)

Table 5. USART feature comparison

## 2.2.24 Serial peripheral interface (SPI)

The STM32F40xxx feature up to three SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1 can communicate at up to 42 Mbits/s, SPI2 and SPI3 can communicate at up to 21 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

## 2.2.25 Inter-integrated sound (I<sup>2</sup>S)

Two standard I<sup>2</sup>S interfaces (multiplexed with SPI2 and SPI3) are available. They can be operated in master or slave mode, in full duplex and half-duplex communication modes, and can be configured to operate with a 16-/32-bit resolution as an input or output channel. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I<sup>2</sup>S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All  $I^2Sx$  can be served by the DMA controller.



## 2.2.26 Audio PLL (PLLI2S)

The devices feature an additional dedicated PLL for audio I<sup>2</sup>S application. It allows to achieve error-free I<sup>2</sup>S sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

The PLLI2S configuration can be modified to manage an  $I^2S$  sample rate change without disabling the main PLL (PLL) used for CPU, USB and Ethernet interfaces.

The audio PLL can be programmed with very low error to obtain sampling rates ranging from 8 KHz to 192 KHz.

In addition to the audio PLL, a master clock input pin can be used to synchronize the  $I^2S$  flow with an external PLL (or Codec output).

## 2.2.27 Secure digital input/output interface (SDIO)

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 48 MHz, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

## 2.2.28 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

Peripheral available only on the STM32F407xx devices.

The STM32F407xx devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard mediumindependent interface (MII) or a reduced medium-independent interface (RMII). The STM32F407xx requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). the PHY is connected to the STM32F407xx MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) from the STM32F407xx.



The STM32F407xx includes the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors (see the STM32F40xxx/41xxx reference manual for details)
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

### 2.2.29 Controller area network (bxCAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for each CAN.

### 2.2.30 Universal serial bus on-the-go full-speed (OTG\_FS)

The STM32F405xx and STM32F407xx embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator. The major features are:

- Combined Rx and Tx FIFO size of 320 × 35 bits with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 4 bidirectional endpoints
- 8 host channels with periodic OUT support
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed in case bus-powered devices are connected



## 2.2.31 Universal serial bus on-the-go high-speed (OTG\_HS)

The STM32F405xx and STM32F407xx devices embed a USB OTG high-speed (up to 480 Mb/s) device/host/OTG peripheral. The USB OTG HS supports both full-speed and high-speed operations. It integrates the transceivers for full-speed operation (12 MB/s) and features a UTMI low-pin interface (ULPI) for high-speed operation (480 MB/s). When using the USB OTG HS in HS mode, an external PHY device connected to the ULPI is required.

The USB OTG HS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 1 Kbit × 35 with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 6 bidirectional endpoints
- 12 host channels with periodic OUT support
- Internal FS OTG PHY support
- External HS or HS OTG operation supporting ULPI in SDR mode. The OTG PHY is connected to the microcontroller ULPI port through 12 signals. It can be clocked using the 60 MHz output.
- Internal USB DMA
- HNP/SNP/IP inside (no need for any external resistor)
- for OTG/Host modes, a power switch is needed in case bus-powered devices are connected

## 2.2.32 Digital camera interface (DCMI)

The camera interface is *not* available in STM32F405xx devices.

STM32F407xx products embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to 54 Mbyte/s at 54 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

## 2.2.33 True random number generator (RNG)

All STM32F405xx and STM32F407xx products embed a true random number generator (RNG) that provides full entropy outputs to the application as 32-bit samples. It is composed of a live entropy source (analog) and an internal conditioning component.

## 2.2.34 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down)



or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allowing maximum I/O toggling up to 84 MHz.

## 2.2.35 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

## 2.2.36 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.8 V and 3.6 V. The temperature sensor is internally connected to the ADC1\_IN16 input channel which is used to convert the sensor output voltage into a digital value.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

## 2.2.37 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.



This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 12-bit monotonic output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V<sub>REF+</sub>

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

## 2.2.38 Serial wire JTAG debug port (SWJ-DP)

The Arm SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

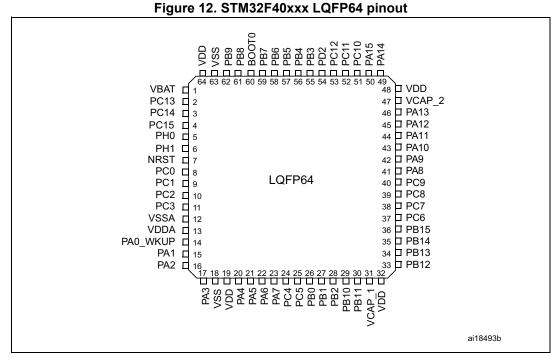
## 2.2.39 Embedded Trace Macrocell™

The Arm Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F40xxx through a small number of ETM pins to an external hardware trace port analyser (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.



## 3 Pinouts and pin description



1. The above figure shows the package top view.



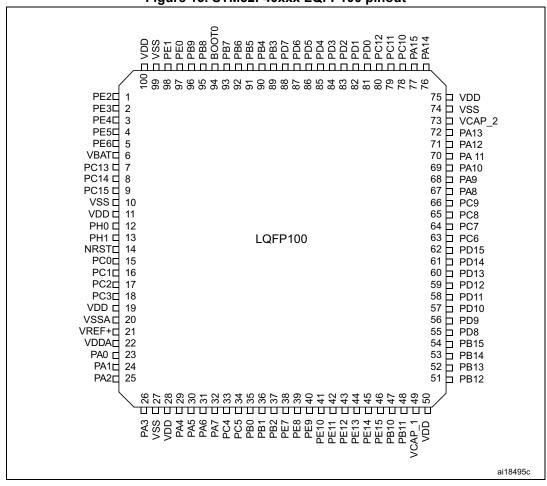


Figure 13. STM32F40xxx LQFP100 pinout

1. The above figure shows the package top view.

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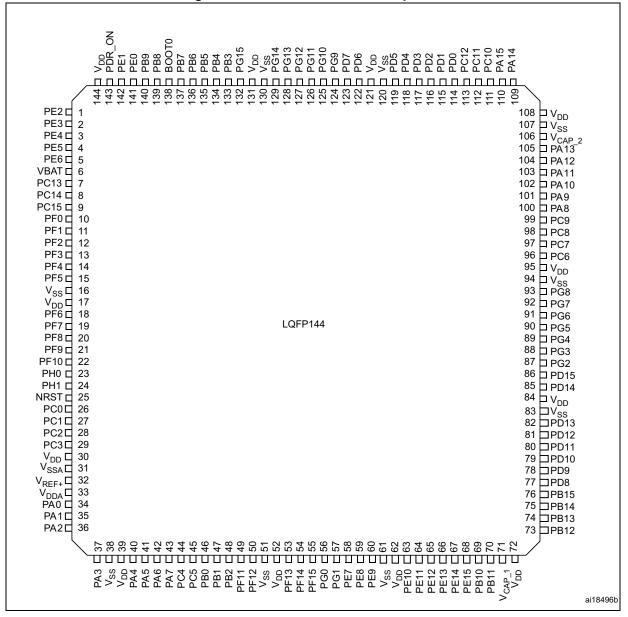
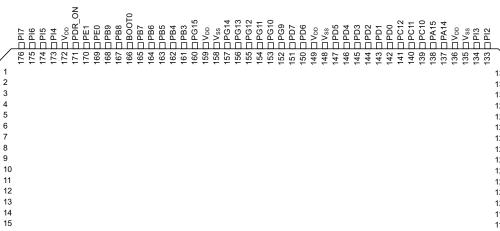


Figure 14. STM32F40xxx LQFP144 pinout

1. The above figure shows the package top view.





## Figure 15. STM32F40xxx LQFP176 pinout

PE2 C PE3 C 132 🗖 PI1 2 131 PE4 3 130 D PH15 PE5 4 рн14 129 PE6 5 128 🗆 PH13 127 🗆 V<sub>DD</sub> 6 VBAT 126 UV<sub>SS</sub> 125 V<sub>CAP\_2</sub> 7 PC13 8 PC14 9 124 PA13 PC15 10 123 D PA12 PI9 11 122 D PA11 PI10 12 121 🗖 PA10 13 120 🗖 PA9 V<sub>SS</sub> □ 14 V<sub>DD</sub> □ 15 119 D PA8 118 D PC9 □ PC8 □ PC7 PF0 16 117 PF1 17 116 PF2 18 115 D PC6 114 PF3 19 PF4 20 113 U Vss PF5 21 112 D PG8 LQFP176 V<sub>SS</sub> 22 111 🗅 PG7 V<sub>DD</sub> 23 110 🕁 PG6 PF6 24 D PG5 109 108 || PG4 107 || PG3 PF7 25 PF8 26 PF9 27 106 D PG2 PF10 28 105 D PD15 PH0 29 104 D PD14 PH1 30 NRST 31 103 VDD 102 🗘 Vss PC0 
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PC1 33 101 D PD13 100 PD12 99 | PD11 98 | PD10 PC2 34 PC3 35 97 | PD9 96 | PD8 V<sub>DD</sub> \_ 36 V<sub>SSA</sub> 37 95 PB15 V<sub>REF+</sub> 38 V<sub>DDA</sub> □ 39 PA0 □ 40 D PB14 94 93 PB13 PA1 [ 41 PA2 [ 42 PH2 [ 43 92 D PB12 91 || V<sub>DD</sub> 90 || V<sub>SS</sub> 89 || PH12 РН3 🕇 44 

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1. The above figure shows the package top view.



	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
А	PE3	PE2	PE1	PE0	PB8	PB5	PG14	PG13	PB4	PB3	PD7	PC12	PA15	PA14	PA13
В	PE4	PE5	PE6	PB9	PB7	PB6	PG15	PG12	PG11	PG10	PD6	PD0	PC11	PC10	PA12
с	VBAT	PI7	Pl6	P15	VDD	PDR_ON	VDD	VDD	VDD	PG9	PD5	PD1	PI3	PI2	PA11
D	PC13	PI8	PI9	PI4	VSS	BOOT0	VSS	VSS	VSS	PD4	PD3	PD2	PH15	PI1	PA10
Е	PC14	PF0	PI10	PI11								PH13	PH14	P10	PA9
F	PC15	VSS	VDD	PH2		VSS	VSS	VSS	VSS	VSS		VSS	VCAP_2	PC9	PA8
G	PH0	VSS	VDD	PH3		VSS	VSS	VSS	VSS	VSS		VSS	VDD	PC8	PC7
н	PH1	PF2	PF1	PH4		VSS	VSS	VSS	VSS	VSS		VSS	VDD	PG8	PC6
J	NRST	PF3	PF4	PH5		VSS	VSS	VSS	VSS	VSS		VDD	VDD	PG7	PG6
к	PF7	PF6	PF5	VDD		VSS	VSS	VSS	VSS	VSS		PH12	PG5	PG4	PG3
L	PF10	PF9	PF8	BYPASS_ REG								PH11	PH10	PD15	PG2
М	VSSA	PC0	PC1	PC2	PC3	PB2	PG1	VSS	VSS	VCAP_1	PH6	PH8	PH9	PD14	PD13
Ν	VREF-	PA1	PA0	PA4	PC4	PF13	PG0	VDD	VDD	VDD	PE13	PH7	PD12	PD11	PD10
Ρ	VREF+	PA2	PA6	PA5	PC5	PF12	PF15	PE8	PE9	PE11	PE14	PB12	PB13	PD9	PD8
R	VDDA	PA3	PA7	PB1	PB0	PF11	PF14	PE7	PE10	PE12	PE15	PB10	PB11	PB14	PB15
															ai18497b

Figure 16. STM32F40xxx UFBGA176 ballout

1. This figure shows the package top view.



	10	9	8	7	6	5	4	3	2	1
A	VBAT	PC13	PDR_ON	BOOT0	PB4	PD7	PD4	PC12	PA14	VDD
В	PC14	PC15	VDD	PB7	PB3	PD6	PD2	PA15	PI1	VCAP_2
С	PA0	vss	PB9	PB6	PD5	PD1	PC11	P10	PA12	PA11
D	PC2	BYPASS_ REG	PB8	PB5	PD0	PC10	PA13	PA10	PA9	PA8
Е	PC0	PC3	VSS	VSS	VDD	VSS	VDD	PC9	PC8	PC7
F	PH0	PH1	PA1	VDD	PE10	PE14	VCAP_1	PC6	PD14	PD15
G	NRST	VDDA	PA5	PB0	PE7	PE13	PE15	PD10	PD12	PD11
н	VSSA	PA3	PA6	PB1	PE8	PE12	PB10	PD9	PD8	PB15
J	PA2	PA4	PA7	PB2	PE9	PE11	PB11	PB12	PB14	PB13
		:					1		1	

Figure 17. STM32F40xxx WLCSP90 ballout

1. This figure shows the package bump view.

Name	Abbreviation	Definition						
Pin name		specified in brackets below the pin name, the pin function during and after as the actual pin name						
	S	Supply pin						
Pin type	I	Input only pin						
	I/O	Input / output pin						
	FT	5 V tolerant I/O						
	TTa	3.3 V tolerant I/O directly connected to ADC						
I/O structure	В	Dedicated BOOT0 pin						
	RST	Bidirectional reset pin with embedded weak pull-up resistor						
Notes	Unless otherwise	specified by a note, all I/Os are set as floating inputs during and after reset						
Alternate functions	Functions selected through GPIOx_AFR registers							
Additional functions	Functions directly selected/enabled through peripheral registers							



	F	Pin r	numb	er							
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	-	1	1	A2	1	PE2	I/O	FT	-	TRACECLK/ FSMC_A23 / ETH_MII_TXD3 / EVENTOUT	-
-	-	2	2	A1	2	PE3	I/O	FT	-	TRACED0/FSMC_A19 / EVENTOUT	-
-	-	3	3	B1	3	PE4	I/O	FT	-	TRACED1/FSMC_A20 / DCMI_D4/ EVENTOUT	-
-	-	4	4	B2	4	PE5	I/O	FT	-	TRACED2 / FSMC_A21 / TIM9_CH1 / DCMI_D6 / EVENTOUT	-
-	-	5	5	B3	5	PE6	I/O	FT	-	TRACED3 / FSMC_A22 / TIM9_CH2 / DCMI_D7 / EVENTOUT	-
1	A10	6	6	C1	6	V <sub>BAT</sub>	S	-	-	-	-
-	-	-	-	D2	7	PI8	I/O	FT	(3)( 4)	EVENTOUT	RTC_TAMP1, RTC_TAMP2, RTC_TS
2	A9	7	7	D1	8	PC13	I/O	FT	(3) (4)	EVENTOUT	RTC_OUT, RTC_TAMP1, RTC_TS
3	B10	8	8	E1	9	PC14/OSC32_IN (PC14)	I/O	FT	(3)( 4)	EVENTOUT	OSC32_IN <sup>(5)</sup>
4	В9	9	9	F1	10	PC15/ OSC32_OUT (PC15)	I/O	FT	(3)( 4)	EVENTOUT	OSC32_OUT <sup>(5)</sup>
-	-	-	-	D3	11	PI9	I/O	FT	-	CAN1_RX / EVENTOUT	-
-	-	-	-	E3	12	PI10	I/O	FT	-	ETH_MII_RX_ER / EVENTOUT	-
-	-	-	-	E4	13	PI11	I/O	FT	-	OTG_HS_ULPI_DIR / EVENTOUT	-
-	-	-	-	F2	14	V <sub>SS</sub>	S	-	-	-	-
-	-	-	-	F3	15	V <sub>DD</sub>	S	-	-	-	-
-	-	-	10	E2	16	PF0	I/O	FT	-	FSMC_A0 / I2C2_SDA / EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions <sup>(1)</sup>
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	I	Pin r	numb							efinitions <sup>(1)</sup> (continued)	
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	-	-	11	H3	17	PF1	I/O	FT	-	FSMC_A1 / I2C2_SCL / EVENTOUT	-
-	-	-	12	H2	18	PF2	I/O	FT	-	FSMC_A2 / I2C2_SMBA / EVENTOUT	-
-	-	-	13	J2	19	PF3	I/O	FT	(5)	FSMC_A3/EVENTOUT	ADC3_IN9
-	-	-	14	J3	20	PF4	I/O	FT	(5)	FSMC_A4/EVENTOUT	ADC3_IN14
-	-	-	15	K3	21	PF5	I/O	FT	(5)	FSMC_A5/EVENTOUT	ADC3_IN15
-	C9	10	16	G2	22	V <sub>SS</sub>	S	-	-	-	-
-	B8	11	17	G3	23	$V_{DD}$	S	-	-	-	-
-	-	-	18	K2	24	PF6	I/O	FT	(5)	TIM10_CH1 / FSMC_NIORD/ EVENTOUT	ADC3_IN4
-	-	-	19	K1	25	PF7	I/O	FT	(5)	TIM11_CH1/FSMC_NREG/ EVENTOUT	ADC3_IN5
-	-	-	20	L3	26	PF8	I/O	FT	(5)	TIM13_CH1 / FSMC_NIOWR/ EVENTOUT	ADC3_IN6
-	-	-	21	L2	27	PF9	I/O	FT	(5)	TIM14_CH1 / FSMC_CD/ EVENTOUT	ADC3_IN7
-	-	-	22	L1	28	PF10	I/O	FT	(5)	FSMC_INTR/ EVENTOUT	ADC3_IN8
5	F10	12	23	G1	29	PH0/OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN <sup>(5)</sup>
6	F9	13	24	H1	30	PH1/OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT <sup>(5)</sup>
7	G10	14	25	J1	31	NRST	I/O	RST	-	-	-
8	E10	15	26	M2	32	PC0	I/O	FT	(5)	OTG_HS_ULPI_STP/ EVENTOUT	ADC123_IN10
9	-	16	27	М3	33	PC1	I/O	FT	(5)	ETH_MDC/ EVENTOUT	ADC123_IN11
10	D10	17	28	M4	34	PC2	I/O	FT	(5)	SPI2_MISO / OTG_HS_ULPI_DIR / ETH_MII_TXD2 /I2S2ext_SD/ EVENTOUT	ADC123_IN12

Table 7. STM32F40xxx	pin and ball (	definitions <sup>(1)</sup>	(continued)
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	F	Pin r	umb	er							
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
11	E9	18	29	M5	35	PC3	I/O	FT	(5)	SPI2_MOSI / I2S2_SD / OTG_HS_ULPI_NXT / ETH_MII_TX_CLK/ EVENTOUT	ADC123_IN13
-	-	19	30	-	36	V <sub>DD</sub>	S	-	-	-	-
12	H10	20	31	M1	37	V <sub>SSA</sub>	S	-	-	-	-
-	-	-	-	N1	-	V <sub>REF-</sub>	S	-	-	-	-
-	-	21	32	P1	38	V <sub>REF+</sub>	S	-	-	-	-
13	G9	22	33	R1	39	V <sub>DDA</sub>	S	-	-	-	-
14	C10	23	34	N3	40	PA0/WKUP (PA0)	I/O	FT	(6)	USART2_CTS/ UART4_TX/ ETH_MII_CRS / TIM2_CH1_ETR/ TIM5_CH1 / TIM8_ETR/ EVENTOUT	ADC123_IN0/WKU P <sup>(5)</sup>
15	F8	24	35	N2	41	PA1	I/O	FT	(5)	USART2_RTS / UART4_RX/ ETH_RMII_REF_CLK / ETH_MII_RX_CLK / TIM5_CH2 / TIM2_CH2/ EVENTOUT	ADC123_IN1
16	J10	25	36	P2	42	PA2	I/O	FT	(5)	USART2_TX/TIM5_CH3 / TIM9_CH1 / TIM2_CH3 / ETH_MDIO/ EVENTOUT	ADC123_IN2
-	-	-	-	F4	43	PH2	I/O	FT	-	ETH_MII_CRS/EVENTOUT	-
-	-	-	-	G4	44	PH3	I/O	FT	-	ETH_MII_COL/EVENTOUT	-
-	-	-	-	H4	45	PH4	I/O	FT	-	I2C2_SCL / OTG_HS_ULPI_NXT/ EVENTOUT	-
-	-	-	-	J4	46	PH5	I/O	FT	-	I2C2_SDA/ EVENTOUT	-
17	H9	26	37	R2	47	PA3	I/O	FT	(5)	USART2_RX/TIM5_CH4 / TIM9_CH2 / TIM2_CH4 / OTG_HS_ULPI_D0 / ETH_MII_COL/ EVENTOUT	ADC123_IN3
18	E5	27	38	-	-	V <sub>SS</sub>	S	-	-	-	-

		(1)	
Table 7. STM32F40xxx pin	and ball	definitions <sup>(1)</sup>	(continued)



	I	Pin r	numb							efinitions <sup>(1)</sup> (continued)	
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
	D9			L4	48	BYPASS_REG	Ι	FT	-	-	-
19	E4	28	39	K4	49	V <sub>DD</sub>	S	-	-	-	-
20	J9	29	40	N4	50	PA4	I/O	TTa	(5)	SPI1_NSS / SPI3_NSS / USART2_CK / DCMI_HSYNC / OTG_HS_SOF/ I2S3_WS/ EVENTOUT	ADC12_IN4 /DAC_OUT1
21	G8	30	41	P4	51	PA5	I/O	ТТа	(5)	SPI1_SCK/ OTG_HS_ULPI_CK / TIM2_CH1_ETR/ TIM8_CH1N/ EVENTOUT	ADC12_IN5/DAC_ OUT2
22	H8	31	42	P3	52	PA6	I/O	FT	(5)	SPI1_MISO / TIM8_BKIN/TIM13_CH1 / DCMI_PIXCLK / TIM3_CH1 / TIM1_BKIN/ EVENTOUT	ADC12_IN6
23	J8	32	43	R3	53	PA7	I/O	FT	(5)	SPI1_MOSI/ TIM8_CH1N / TIM14_CH1/TIM3_CH2/ ETH_MII_RX_DV / TIM1_CH1N / ETH_RMII_CRS_DV/ EVENTOUT	ADC12_IN7
24	-	33	44	N5	54	PC4	I/O	FT	(5)	ETH_RMII_RX_D0 / ETH_MII_RX_D0/ EVENTOUT	ADC12_IN14
25	-	34	45	P5	55	PC5	I/O	FT	(5)	ETH_RMII_RX_D1 / ETH_MII_RX_D1/ EVENTOUT	ADC12_IN15
26	G7	35	46	R5	56	PB0	I/O	FT	(5)	TIM3_CH3 / TIM8_CH2N/ OTG_HS_ULPI_D1/ ETH_MII_RXD2 / TIM1_CH2N/ EVENTOUT	ADC12_IN8
27	H7	36	47	R4	57	PB1	I/O	FT	(5)	TIM3_CH4 / TIM8_CH3N/ OTG_HS_ULPI_D2/ ETH_MII_RXD3 / TIM1_CH3N/ EVENTOUT	ADC12_IN9
28	J7	37	48	M6	58	PB2/BOOT1 (PB2)	I/O	FT	-	EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions <sup>(1)</sup> (continued)
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	I	Pin r	numb	er							
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	-	-	49	R6	59	PF11	I/O	FT	-	DCMI_D12/ EVENTOUT	-
-	-	-	50	P6	60	PF12	I/O	FT	-	FSMC_A6/ EVENTOUT	-
-	-	-	51	M8	61	V <sub>SS</sub>	S	-	-	-	-
-	-	-	52	N8	62	V <sub>DD</sub>	S	-	-	-	-
-	-	-	53	N6	63	PF13	I/O	FT	-	FSMC_A7/ EVENTOUT	-
-	-	-	54	R7	64	PF14	I/O	FT	-	FSMC_A8/ EVENTOUT	-
-	-	-	55	P7	65	PF15	I/O	FT	-	FSMC_A9/ EVENTOUT	-
-	-	-	56	N7	66	PG0	I/O	FT	-	FSMC_A10/ EVENTOUT	-
-	-	-	57	M7	67	PG1	I/O	FT	-	FSMC_A11/ EVENTOUT	-
-	G6	38	58	R8	68	PE7	I/O	FT	-	FSMC_D4/TIM1_ETR/ EVENTOUT	-
-	H6	39	59	P8	69	PE8	I/O	FT	-	FSMC_D5/ TIM1_CH1N/ EVENTOUT	-
-	J6	40	60	P9	70	PE9	I/O	FT	-	FSMC_D6/TIM1_CH1/ EVENTOUT	-
-	-	-	61	M9	71	V <sub>SS</sub>	S	-	-	-	-
-	-	-	62	N9	72	V <sub>DD</sub>	S	-	-	-	-
-	F6	41	63	R9	73	PE10	I/O	FT	-	FSMC_D7/TIM1_CH2N/ EVENTOUT	-
-	J5	42	64	P10	74	PE11	I/O	FT	-	FSMC_D8/TIM1_CH2/ EVENTOUT	-
-	H5	43	65	R10	75	PE12	I/O	FT	-	FSMC_D9/TIM1_CH3N/ EVENTOUT	-
-	G5	44	66	N11	76	PE13	I/O FT - FSMC_D10/TIM1_CH3/ EVENTOUT		-		
-	F5	45	67	P11	77	PE14	I/O FT - FSMC_D11/TIM1_CH4/ EVENTOUT		-		
-	G4	46	68	R11	78	PE15	I/O	FT	-	FSMC_D12/TIM1_BKIN/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)



	I	Pin r	numb							efinitions <sup>(1)</sup> (continued)	
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
29	H4	47	69	R12	79	PB10	I/O	FT	-	SPI2_SCK / I2S2_CK / I2C2_SCL/ USART3_TX / OTG_HS_ULPI_D3 / ETH_MII_RX_ER / TIM2_CH3/ EVENTOUT	-
30	J4	48	70	R13	80	PB11	I/O	FT	-	I2C2_SDA/USART3_RX/ OTG_HS_ULPI_D4 / ETH_RMII_TX_EN/ ETH_MII_TX_EN / TIM2_CH4/ EVENTOUT	-
31	F4	49	71	M10	81	V <sub>CAP_1</sub>	S		-	-	-
32	-	50	72	N10	82	V <sub>DD</sub>	S		-	-	-
-	-	-	-	M11	83	PH6	I/O	FT	-	I2C2_SMBA / TIM12_CH1 / ETH_MII_RXD2/ EVENTOUT	-
-	-	-	-	N12	84	PH7	I/O	FT	-	I2C3_SCL / ETH_MII_RXD3/ EVENTOUT	-
-	-	-	-	M12	85	PH8	I/O	FT	-	I2C3_SDA / DCMI_HSYNC/ EVENTOUT	-
-	-	-	-	M13	86	PH9	I/O	FT	-	I2C3_SMBA / TIM12_CH2/ DCMI_D0/ EVENTOUT	-
-	-	-	-	L13	87	PH10	I/O	FT	-	TIM5_CH1 / DCMI_D1/ EVENTOUT	-
-	-	-	-	L12	88	PH11	I/O	I/O FT - TIM5_CH2 / DCMI_D2/ EVENTOUT		-	
-	-	-	-	K12	89	PH12	I/O FT - TIM5_CH3 / DCMI_D3/ EVENTOUT		-		
-	-	-	I	H12	90	V <sub>SS</sub>	S	S		-	
-	-	-	-	J12	91	$V_{DD}$			-		

 Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)



	Pin number										
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
33	J3	51	73	P12	92	PB12	I/O	FT	-	SPI2_NSS / I2S2_WS / I2C2_SMBA/ USART3_CK/ TIM1_BKIN / CAN2_RX / OTG_HS_ULPI_D5/ ETH_RMII_TXD0 / ETH_MII_TXD0/ OTG_HS_ID/ EVENTOUT	-
34	J1	52	74	P13	93	PB13	I/O	FT	-	SPI2_SCK / I2S2_CK / USART3_CTS/ TIM1_CH1N /CAN2_TX / OTG_HS_ULPI_D6 / ETH_RMII_TXD1 / ETH_MII_TXD1/ EVENTOUT	OTG_HS_VBUS
35	J2	53	75	R14	94	PB14	I/O	FT	-	SPI2_MISO/ TIM1_CH2N / TIM12_CH1 / OTG_HS_DM/ USART3_RTS / TIM8_CH2N/I2S2ext_SD/ EVENTOUT	-
36	H1	54	76	R15	95	PB15	I/O	FT	-	SPI2_MOSI / I2S2_SD/ TIM1_CH3N / TIM8_CH3N / TIM12_CH2 / OTG_HS_DP/ EVENTOUT	RTC_REFIN
-	H2	55	77	P15	96	PD8	I/O	FT	-	FSMC_D13 / USART3_TX/ EVENTOUT	-
-	H3	56	78	P14	97	PD9	I/O	FT	-	FSMC_D14/USART3_RX/ EVENTOUT	-
-	G3	57	79	N15	98	PD10	I/O	FT	-	FSMC_D15/USART3_CK/ EVENTOUT	-
-	G1	58	80	N14	99	PD11	I/O	FT	-	FSMC_CLE / FSMC_A16/USART3_CTS/ EVENTOUT	-
-	G2	59	81	N13	100	PD12	I/O	FT	-	FSMC_ALE/ FSMC_A17/TIM4_CH1 / USART3_RTS/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)



		Pin r	numb		Die /	. 3111132F40XXX	pine			efinitions <sup>(1)</sup> (continued)	
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	-	60	82	M15	101	PD13	I/O	FT	-	FSMC_A18/TIM4_CH2/ EVENTOUT	-
-	-	-	83	-	102	V <sub>SS</sub> SS		-			
-	-	-	84	J13	103	V <sub>DD</sub>	S		-	-	-
-	F2	61	85	M14	104	PD14	I/O	FT	-	FSMC_D0/TIM4_CH3/ EVENTOUT/ EVENTOUT	-
-	F1	62	86	L14	105	PD15	I/O	FT	-	FSMC_D1/TIM4_CH4/ EVENTOUT	-
-	-	-	87	L15	106	PG2	I/O	FT	-	FSMC_A12/ EVENTOUT	-
-	-	-	88	K15	107	PG3	I/O	FT	-	FSMC_A13/ EVENTOUT	-
-	-	-	89	K14	108	PG4	I/O	FT	-	FSMC_A14/ EVENTOUT	-
-	-	-	90	K13	109	PG5	I/O	FT	-	FSMC_A15/ EVENTOUT	-
-	-	-	91	J15	110	PG6	I/O	FT	-	FSMC_INT2/ EVENTOUT	-
-	-	-	92	J14	111	PG7	I/O	FT	-	FSMC_INT3/USART6_CK/ EVENTOUT	-
-	-	-	93	H14	112	PG8	I/O	FT	-	USART6_RTS / ETH_PPS_OUT/ EVENTOUT	-
-	-	-	94	G12	113	V <sub>SS</sub>	S		-	-	-
-	-	-	95	H13	114	V <sub>DD</sub>	S		-	-	-
37	F3	63	96	H15	115	PC6	I/O	FT	-	I2S2_MCK / TIM8_CH1/SDIO_D6 / USART6_TX / DCMI_D0/TIM3_CH1/ EVENTOUT	-
38	E1	64	97	G15	116	PC7	I/O	FT	-	I2S3_MCK / TIM8_CH2/SDIO_D7 / USART6_RX / DCMI_D1/TIM3_CH2/ EVENTOUT	-
39	E2	65	98	G14	117	PC8	I/O	FT	-	TIM8_CH3/SDIO_D0 /TIM3_CH3/ USART6_CK / DCMI_D2/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions <sup>(1)</sup> (continued)
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	I	Pin r	numb								
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	Pin type       I / O structure       Notes       Notes		Additional functions	
40	E3	66	99	F14	118	PC9	I/O	FT	-	I2S_CKIN/ MCO2 / TIM8_CH4/SDIO_D1 / /I2C3_SDA / DCMI_D3 / TIM3_CH4/ EVENTOUT	-
41	D1	67	100	F15	119	PA8	I/O	FT	-	MCO1 / USART1_CK/ TIM1_CH1/ I2C3_SCL/ OTG_FS_SOF/ EVENTOUT	-
42	D2	68	101	E15	120	PA9	I/O	FT	-	USART1_TX/ TIM1_CH2 / I2C3_SMBA / DCMI_D0/ EVENTOUT	OTG_FS_VBUS
43	D3	69	102	D15	121	PA10	I/O	FT	-	USART1_RX/ TIM1_CH3/ OTG_FS_ID/DCMI_D1/ EVENTOUT	-
44	C1	70	103	C15	122	PA11	I/O	FT	-	USART1_CTS / CAN1_RX / TIM1_CH4 / OTG_FS_DM/ EVENTOUT	-
45	C2	71	104	B15	123	PA12	I/O	FT	-	USART1_RTS / CAN1_TX/ TIM1_ETR/ OTG_FS_DP/ EVENTOUT	-
46	D4	72	105	A15	124	PA13 (JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO/ EVENTOUT	-
47	B1	73	106	F13	125	V <sub>CAP_2</sub>	S	-	-	-	-
-	E7	74	107	F12	126	V <sub>SS</sub>	S	-	-	-	-
48	E6	75	108	G13	127	V <sub>DD</sub>	S	-	-	-	-
-	-	-	-	E12	128	PH13	I/O	FT	-	TIM8_CH1N / CAN1_TX/ EVENTOUT	-
-	-	-	-	E13	129	PH14	I/O FT - TIM8_CH2N / DCMI_D4/ EVENTOUT		-		
-	-	-	-	D13	130	PH15	I/O FT - TIM8_CH3N / DCMI_D11/ EVENTOUT		-		
-	C3	-	-	E14	131	PI0	I/O FT - TIM5_CH4 / SPI2_NSS / I2S2_WS / DCMI_D13/ EVENTOUT		-		
-	B2	-	-	D14	132	PI1	I/O	FT	-	SPI2_SCK / I2S2_CK / DCMI_D8/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)



	I	Pin r	numb							efinitions <sup>(1)</sup> (continued)	
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	-	-	-	C14	133	PI2	I/O	FT	-	TIM8_CH4 /SPI2_MISO / DCMI_D9 / I2S2ext_SD/ EVENTOUT	-
-	-	-	-	C13	134	PI3	I/O	FT		TIM8_ETR / SPI2_MOSI / I2S2_SD / DCMI_D10/ EVENTOUT	-
-	-	-	-	D9	135	V <sub>SS</sub>	S	-	-	-	-
-	-	-	-	C9	136	V <sub>DD</sub>	S	-	-	-	-
49	A2	76	109	A14	137	PA14 (JTCK/SWCLK)	I/O	FT	-	JTCK-SWCLK/ EVENTOUT	-
50	В3	77	110	A13	138	PA15 (JTDI)	1/01 + 1 - 12S3 WS/11M2 CH1 + 1R +		-		
51	D5	78	111	B14	139	PC10	I/O	FT	-	SPI3_SCK / I2S3_CK/ UART4_TX/SDIO_D2 / DCMI_D8 / USART3_TX/ EVENTOUT	-
52	C4	79	112	B13	140	PC11	I/O	FT	-	UART4_RX/ SPI3_MISO / SDIO_D3 / DCMI_D4/USART3_RX / I2S3ext_SD/ EVENTOUT	-
53	A3	80	113	A12	141	PC12	I/O	FT	-	UART5_TX/SDIO_CK / DCMI_D9 / SPI3_MOSI /I2S3_SD / USART3_CK/ EVENTOUT	-
-	D6	81	114	B12	142	PD0	I/O	FT	-	FSMC_D2/CAN1_RX/ EVENTOUT	-
-	C5	82	115	C12	143	PD1	I/O FT - FSMC_D3 / CAN1_TX/ EVENTOUT		-		
54	B4	83	116	D12	144	PD2	I/O FT - TIM3_ETR/UART5_RX/ SDI0_CMD / DCMI_D11/ EVENTOUT		-		
-	-	84	117	D11	145	PD3	I/O	FT	-	FSMC_CLK/ USART2_CTS/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)



	Pin number										
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions
-	A4	85	118	D10	146	PD4	I/O	FT	-	FSMC_NOE/ USART2_RTS/ EVENTOUT	-
-	C6	86	119	C11	147	PD5	I/O	FT	-	FSMC_NWE/USART2_TX/ EVENTOUT	-
-	-	-	120	D8	148	V <sub>SS</sub>	S	-	-	_	-
-	-	-	121	C8	149	V <sub>DD</sub>	S	-	-	-	-
-	B5	87	122	B11	150	PD6	I/O	FT	-	FSMC_NWAIT/ USART2_RX/ EVENTOUT	-
-	A5	88	123	A11	151	PD7	I/O	FT	-	USART2_CK/FSMC_NE1/ FSMC_NCE2/ EVENTOUT	-
-	-	-	124	C10	152	PG9	I/O	FT	-	USART6_RX / FSMC_NE2/FSMC_NCE3/ EVENTOUT	-
-	-	-	125	B10	153	PG10	I/O	FT	-	FSMC_NCE4_1/ FSMC_NE3/ EVENTOUT	-
-	-	-	126	В9	154	PG11	I/O	FT	-	FSMC_NCE4_2 / ETH_MII_TX_EN/ ETH_RMII_TX_EN/ EVENTOUT	-
-	-	-	127	B8	155	PG12	I/O	FT	-	FSMC_NE4 / USART6_RTS/ EVENTOUT	-
-	-	-	128	A8	156	PG13	I/O	FT	FSMC_A24 / USART6_CTS - /ETH_MII_TXD0/ ETH_RMII_TXD0/ EVENTOUT		-
-	-	-	129	A7	157	PG14	I/O	FT	FSMC_A25 / USART6_TX /ETH_MII_TXD1/ ETH_RMII_TXD1/ EVENTOUT		-
-	E8	-	130	D7	158	$V_{SS}$	S	-	-		
-	F7	-	131	C7	159	V <sub>DD</sub>	S	I			-
-	-	-	132	B7	160	PG15	I/O	FT	-	USART6_CTS / DCMI_D13/ EVENTOUT	-

Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)



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	I	Pin r	numb							efinitions <sup>(+)</sup> (continued)	
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	(function after reset) <sup>(2)</sup>		Additional functions		
55	B6	89	133	A10	161	PB3 (JTDO/ TRACESWO)	I/O	FT	-	JTDO/ TRACESWO/ SPI3_SCK / I2S3_CK / TIM2_CH2 / SPI1_SCK/ EVENTOUT	-
56	A6	90	134	A9	162	PB4 (NJTRST)	I/O	FT	-	NJTRST/ SPI3_MISO / TIM3_CH1 / SPI1_MISO / I2S3ext_SD/ EVENTOUT	-
57	D7	91	135	A6	163	PB5	I/O	FT	-	I2C1_SMBA/ CAN2_RX / OTG_HS_ULPI_D7 / ETH_PPS_OUT/TIM3_CH2 / SPI1_MOSI/ SPI3_MOSI / DCMI_D10 / I2S3_SD/ EVENTOUT	-
58	C7	92	136	B6	164	PB6	I/O	FT	-	I2C1_SCL/ TIM4_CH1 / CAN2_TX / DCMI_D5/USART1_TX/ EVENTOUT	-
59	B7	93	137	В5	165	PB7	I/O	FT	-	I2C1_SDA / FSMC_NL / DCMI_VSYNC / USART1_RX/ TIM4_CH2/ EVENTOUT	-
60	A7	94	138	D6	166	BOOT0	Ι	В	-	-	V <sub>PP</sub>
61	D8	95	139	A5	167	PB8	I/O	FT	-	TIM4_CH3/SDIO_D4/ TIM10_CH1 / DCMI_D6 / ETH_MII_TXD3 / I2C1_SCL/ CAN1_RX/ EVENTOUT	-
62	C8	96	140	B4	168	PB9	I/O	FT	-	SPI2_NSS/ I2S2_WS / TIM4_CH4/ TIM11_CH1/ SDIO_D5 / DCMI_D7 / I2C1_SDA / CAN1_TX/ EVENTOUT	-
-	-	97	141	A4	169	PE0	I/O	FT	-	TIM4_ETR / FSMC_NBL0 / DCMI_D2/ EVENTOUT	-
-	-	98	142	A3	170	PE1	I/O FT - FSMC_NBL1 / DCMI_D3/ EVENTOUT		-		
63	-	99	-	D5	-	$V_{SS}$	S	-	-	-	-

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	Pin number											
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176	Pin name (function after reset) <sup>(2)</sup>	Pin type	I / O structure	Notes	Alternate functions	Additional functions	
-	A8	-	143	C6	171	PDR_ON	Ι	FT	-	-	-	
64	A1	10 0	144	C5	172	V <sub>DD</sub>	s	-	-	-	-	
-	-	-	-	D4	173	Pl4	I/O	FT	-	TIM8_BKIN / DCMI_D5/ EVENTOUT	-	
-	-	-	-	C4	174	PI5	I/O	FT	-	TIM8_CH1 / DCMI_VSYNC/ EVENTOUT	-	
-	-	-	-	C3	175	Pl6	I/O	FT	-	TIM8_CH2 / DCMI_D6/ EVENTOUT	-	
-	-	-	-	C2	176	PI7	I/O	FT	-	TIM8_CH3 / DCMI_D7/ EVENTOUT	-	

Table 7. STM32F40xxx pin and ball definitions<sup>(1)</sup> (continued)

UFBGA176 F6, F7, F8, F9, F10, G6, G7, G8, G9, G10, H6, H7, H8, H9, H10, J6, J7, J8, J9, J10, K6, K7, K8, K9 and K10 balls are connected to V<sub>SS</sub> for heat dissipation and package mechanical stability.

2. Function availability depends on the chosen device.

PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited:

 The speed should not exceed 2 MHz with a maximum load of 30 pF.
 These I/Os must not be used as a current source (e.g. to drive an LED).

- 4. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: www.st.com.
- 5. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
- If the device is delivered in an UFBGA176 or WLCSP90 and the BYPASS\_REG pin is set to VDD (Regulator off/internal reset ON mode), then PA0 is used as an internal Reset (active low). 6.

(4)			FSMC			WLCSP90 (2)	
Pins <sup>(1)</sup>	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit	LQFP100 <sup>(2)</sup>		
PE2	-	A23	A23	-	Yes	-	
PE3	-	A19	A19	-	Yes	-	
PE4	-	A20	A20	-	Yes	-	
PE5	-	A21	A21	-	Yes	-	
PE6	-	A22	A22	-	Yes	-	

## Table 8. FSMC pin definition



			FSMC		,	
Pins <sup>(1)</sup>	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit	LQFP100 <sup>(2)</sup>	WLCSP90 (2)
PF0	A0	A0	-	-	-	-
PF1	A1	A1	-	-	-	-
PF2	A2	A2	-	-	-	-
PF3	A3	A3	-	-	-	-
PF4	A4	A4	-	-	-	-
PF5	A5	A5	-	-	-	-
PF6	NIORD	-	-	-	-	-
PF7	NREG	-	-	-	-	-
PF8	NIOWR	-	-	-	-	-
PF9	CD	-	-	-	-	-
PF10	INTR	-	-	-	-	-
PF12	A6	A6	-	-	-	-
PF13	A7	A7	-	-	-	-
PF14	A8	A8	-	-	-	-
PF15	A9	A9	-	-	-	-
PG0	A10	A10	-	-	-	-
PG1		A11	-	-	-	-
PE7	D4	D4	DA4	D4	Yes	Yes
PE8	D5	D5	DA5	D5	Yes	Yes
PE9	D6	D6	DA6	D6	Yes	Yes
PE10	D7	D7	DA7	D7	Yes	Yes
PE11	D8	D8	DA8	D8	Yes	Yes
PE12	D9	D9	DA9	D9	Yes	Yes
PE13	D10	D10	DA10	D10	Yes	Yes
PE14	D11	D11	DA11	D11	Yes	Yes
PE15	D12	D12	DA12	D12	Yes	Yes
PD8	D13	D13	DA13	D13	Yes	Yes
PD9	D14	D14	DA14	D14	Yes	Yes
PD10	D15	D15	DA15	D15	Yes	Yes
PD11	-	A16	A16	CLE	Yes	Yes
PD12	-	A17	A17	ALE	Yes	Yes
PD13	-	A18	A18	-	Yes	-
PD14	D0	D0	DA0	D0	Yes	Yes

Table 8. FSMC	pin definit	ion (continued)
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			FSMC			M// 00000
Pins <sup>(1)</sup>	CF	NOR/PSRAM/ SRAM	NOR/PSRAM Mux	NAND 16 bit	LQFP100 <sup>(2)</sup>	WLCSP90 (2)
PD15	D1	D1	DA1	D1	Yes	Yes
PG2	-	A12	-	-	-	-
PG3	-	A13	-	-	-	-
PG4	-	A14	-	-	-	-
PG5	-	A15	-	-	-	-
PG6	-	-	-	INT2	-	-
PG7	-	-	-	INT3	-	-
PD0	D2	D2	DA2	D2	Yes	Yes
PD1	D3	D3	DA3	D3	Yes	Yes
PD3	-	CLK	CLK	-	Yes	-
PD4	NOE	NOE	NOE	NOE	Yes	Yes
PD5	NWE	NWE	NWE	NWE	Yes	Yes
PD6	NWAIT	NWAIT	NWAIT	NWAIT	Yes	Yes
PD7	-	NE1	NE1	NCE2	Yes	Yes
PG9	-	NE2	NE2	NCE3	-	-
PG10	NCE4_1	NE3	NE3	-	-	-
PG11	NCE4_2	-	-	-	-	-
PG12	-	NE4	NE4	-	-	-
PG13	-	A24	A24	-	-	-
PG14	-	A25	A25	-	-	-
PB7	-	NADV	NADV	-	Yes	Yes
PE0	-	NBL0	NBL0	-	Yes	-
PE1	-	NBL1	NBL1	-	Yes	-

Table 8. FSMC pin definition (continued)

1. Full FSMC features are available on LQFP144, LQFP176, and UFBGA176. The features available on smaller packages are given in the dedicated package column.

2. Ports F and G are not available in devices delivered in 100-pin packages.



							מאוס	J. AILEI			Rinde						
		AFO	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13		
μ	Port	SYS	TIM1/2	TIM 3/4/5	TIM8/9/10 /11	I2C1/2/3	SPI1/SPI2/ I2S2/I2S2e xt	SPI3/I2Sext /I2S3	USART1/2/3/ I2S3ext	UART4/5/ USART6	CAN1/2 TIM12/13/ 14	OTG_FS/ OTG_HS	ЕТН	FSMC/SDIO /OTG_FS	DCMI	AF14	AF15
	PA0		TIM2_CH1_ ETR	TIM 5_CH1	TIM8_ETR				USART2_CTS	UART4_TX			ETH_MILCRS				EVENTOUT
	PA1		TIM2_CH2	TIM5_CH2	I	I	ı	1	USART2_RTS	UART4_RX	ı		ETH_MII _RX_CLK ETH_RMII_REF _CLK	-	1	1	EVENTOUT
	PA2	,	TIM2_CH3	TIM5_CH3	TIM9_CH1	,	,	,	USART2_TX	,			ETH_MDIO	,	,		EVENTOUT
	PA3		TIM2_CH4	TIM5_CH4	TIM9_CH2				USART2_RX	,		OTG_HS_ULPI_ D0	ETH_MILCOL	1	,		EVENTOUT
	PA4		'	ŗ			SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK		,		1	OTG_HS_SOF	DCMI		EVENTOUT
	PA5		TIM2_CH1_ ETR	-	TIM8_CH1N		SPI1_SCK		-			OTG_HS_ULPI_ CK	1	1	,		EVENTOUT
	PA6		TIM1_BKIN	TIM3_CH1	TIM8_BKIN		SPI1_MISO		-		TIM13_CH1	ı	1	1	DCMI_ PIXCLK		EVENTOUT
Port A	PA7		TIM1_CH1N	TIM3_CH2	TIM8_CH1N		SPI1_MOSI	1	1	1	TIM14_CH1	,	ETH_MIL_RX_DV ETH_RMII _CRS_DV		1		EVENTOUT
	PA8	MCO1	TIM1_CH1	-		I2C3_SCL			USART1_CK			OTG_FS_SOF					EVENTOUT
	PA9		TIM1_CH2	-	-	I2C3_ SMBA		,	USART1_TX	'	,	ı	1	1	DCMI_D0		EVENTOUT
	PA10		TIM1_CH3			,			USART1_RX	,		OTG_FS_ID		,	DCMI_D1		EVENTOUT
	PA11	,	TIM1_CH4		,	,			USART1_CTS	,	CAN1_RX	OTG_FS_DM			,		EVENTOUT
	PA12		TIM1_ETR						USART1_RTS	-	CAN1_TX	OTG_FS_DP					EVENTOUT
	PA13	JTMS- SWDIO	-	ı			,		I	,		ı	1	1	'		EVENTOUT
	PA14	JTCK- SWCLK	'	T	I		,		1	I		ı			1		EVENTOUT
	PA15	ИТЛ	TIM 2_CH1 TIM 2_ETR		ı	ı	SPI1_NSS	SPI3_NSS/ I2S3_WS		ı	ı		ı		ı		EVENTOUT

Pinouts and pin description



		AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT
		AF14					,					1	,					
	AF13	DCMI				,		DCMI_D10	DCMI_D5	DCML_VSYN	DCMI_D6	DCMI_D7						,
	AF12	FSMC/SDIO /OTG_FS	,	-		I	-	-	-	FSMC_NL	SDIO_D4	spio_p5	-		OTG_HS_ID		OTG_HS_DM	OTG_HS_DP
	AF11	ЕТН	ETH_MILRXD2	ETH_MILRXD3	-	T	-	ETH_PPS_OUT	-	-	ETH_MIL_TXD3		ETH_ MII_RX_ER	ETH_MILTX_EN ETH _RMILTX_EN	ETH_MILTXD0 ETH_RMILTXD0	ETH_MILTXD1 ETH_RMILTXD1		-
ued)	AF10	OTG_FS/ OTG_HS	OTG_HS_ULPI_ D1	OTG_HS_ULPI_ D2	-		-	OTG_HS_ULPI_ D7	-	-	-		OTG_HS_ULPI_ D3	OTG_HS_ULPI_ D4	OTG_HS_ULPI_ D5	OTG_HS_ULPI_ D6		
(contin	AF9	CAN1/2 TIM12/13/ 14		-	-		-	CAN2_RX	CAN2_TX	-	CAN1_RX	CAN1_TX	-	-	CAN2_RX	CAN2_TX	TIM12_CH1	TIM12_CH2
apping	AF8	UART4/5/ USART6		-	-		-	-	-	-	-	-	-	-	-	-	-	-
Table 9. Alternate function mapping (continued)	AF7	USART1/2/3/ I2S3ext		Ţ		ı	I2S3ext_SD		USART1_TX	USART1_RX		-	USART3_TX	USART3_RX	USART3_CK	USART3_CTS	USART3_RTS	I
ernate fu	AF6	SPI3/I2Sext /I2S3		-		SPI3_SCK I2S3_CK	SPI3_MISO	SPI3_MOSI I2S3_SD	-	-			-		-	-	I2S2ext_SD	-
le 9. Alt	AF5	SPI1/SPI2/ I2S2/I2S2e xt	,		-	SPI1_SCK	SPI1_MISO	SPI1_MOSI	-			SPI2_NSS I2S2_WS	SPI2_SCK I2S2_CK	I	SPI2_NSS I2S2_WS	SPI2_SCK I2S2_CK	SPI2_MISO	SPI2_MOSI I2S2_SD
Tab	AF4	I2C1/2/3					-	I2C1_SMB	I2C1_SCL	I2C1_SDA	I2C1_SCL	I2C1_SDA	I2C2_SCL	I2C2_SDA	I2C2_ SMBA	-		
	AF3	TIM8/9/10 /11	TIM8_CH2N	TIM8_CH3N		ı					TIM10_CH1	TIM11_CH1	'	1			TIM8_CH2N	TIM8_CH3N
	AF2	TIM 3/4/5	TIM3_CH3	TIM3_CH4		ı	TIM3_CH1	TIM3_CH2	TIM4_CH1	TIM4_CH2	TIM4_CH3	TIM4_CH4	ı	ı	ī	ı		ı
	AF1	TIM1/2	TIM1_CH2N	TIM1_CH3N		TIM2_CH2							TIM2_CH3	TIM2_CH4	TIM1_BKIN	TIM1_CH1N	TIM1_CH2N	TIM1_CH3N
	AF0	SYS		-		JTDO/ TRACES WO	NUTRST	-	-	,			-	I	-	-		RTC_ REFIN
		Port	PBO	PB1	PB2	PB3	PB4	PB5	PB6	PB7	PB8	PB9	PB10	PB11	PB12	PB13	PB14	PB15
		٩									Port B							
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		AFO	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13		
ш	Port	SYS	Z/1 W1/2	TIM3/4/5	TIM8/9/10 /11	I2C1/2/3	SPI1/SPI2/ I2S2/I2S2e xt	SPI3/I2Sext /I2S3	USART1/2/3/ I2S3ext	UART4/5/ USART6	CAN1/2 TIM12/13/ 14	OTG_FS/ OTG_HS	ЕТН	FSMC/SDIO /OTG_FS	DCMI	AF14	AF15
	PC0			,			,			,		OTG_HS_ULPI_ STP	1		,		EVENTOUT
	PC1		,			,		,					ETH_MDC				EVENTOUT
	PC2	,		,	'		SPI2_MISO	I2S2ext_SD	,			OTG_HS_ULPI_ DIR	ETH_MIL_TXD2		'		EVENTOUT
	PC3		,		,		SPI2_MOSI I2S2_SD		,			OTG_HS_ULPI_ NXT	ETH MII_TX_CLK		'		EVENTOUT
	PC4		-	ı					1				ETH_MII_RXD0 ETH_RMII_RXD0		,	-	EVENTOUT
	PC5		-	'	'	ı	'		1	1		ı	ETH_MILRXD1 ETH_RMILRXD1		'	-	EVENTOUT
	PC6	-	-	TIM3_CH1	TIM8_CH1		12S2_MCK			USART6_TX				SDIO_D6	DCMI_D0	-	EVENTOUT
Port C	PC7	1		TIM3_CH2	TIM8_CH2			I2S3_MCK		USART6_RX				SDIO_D7	DCMI_D1		EVENTOUT
	PC8	I	1	TIM3_CH3	TIM8_CH3	I		'	'	USART6_CK	1			SDIO_D0	DCMI_D2		EVENTOUT
	PC9	MCO2		TIM3_CH4	TIM8_CH4	I2C3_SDA	I2S_CKIN	'						SDIO_D1	DCMI_D3		EVENTOUT
	PC10	1	1	ı		ı	'	SPI3_SCK/ I2S3_CK		UART4_TX		ı	ı	SDIO_D2	DCMI_D8	-	EVENTOUT
	PC11			-			I2S3ext_SD	SPI3_MISO/	USART3_RX	UART4_RX				SDIO_D3	DCMI_D4		EVENTOUT
	PC12	-	-	ı				SPI3_MOSI I2S3_SD	USART3_CK	UART5_TX		ı	ı	spio_cK	DCMI_D9	-	EVENTOUT
	PC13	-			-			-									EVENTOUT
	PC14	I	1		Ţ	ı		'	'	1							EVENTOUT
	PC15	ı	ı			·	ı					·	ı				EVENTOUT

# Table 9. Alternate function mapping (continued)

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		AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT
		AF14	-										ı					
	AF13	DCMI			DCML_D11	-	-	-	-	,	-	-	-	-	-	-	-	-
	AF12	FSMC/SDIO /OTG_FS	FSMC_D2	FSMC_D3	SDIO_CMD	FSMC_CLK	FSMC_NOE	FSMC_NWE	FSMC_NWAIT	FSMC_NE1/ FSMC_NCE2	FSMC_D13	FSMC_D14	FSMC_D15	FSMC_A16	FSMC_A17	FSMC_A18	FSMC_D0	FSMC_D1
	AF11	ETH								ı								
ied)	AF10	OTG_FS/ OTG_HS								ı								
continu	AF9	CAN1/2 TIM12/13/ 14	CAN1_RX	CAN1_TX						,								
apping (	AF8	UART4/5/ USART6			UART5_RX	-					-	-		-	-			
Table 9. Alternate function mapping (continued)	AF7	USART1/2/3/ I2S3ext				USART2_CTS	USART2_RTS	USART2_TX	USART2_RX	USART2_CK	USART3_TX	USART3_RX	USART3_CK	USART3_CTS	USART3_RTS			
ernate fu	AF6	SPI3/I2Sext /I2S3			-	-						-		-	-			
le 9. Alte	AF5	SPI1/SPI2/ I2S2/I2S2e xt			-	-					-	-		-	-			
Tab	AF4	I2C1/2/3	•		-	-	-			Ţ	-	-	1	-	-			1
	AF3	TIM8/9/10 /11			-	-	-				-	-		-	-			
	AF2	TIM 3/4/5			TIM3_ETR					,					TIM4_CH1	TIM4_CH2	TIM4_CH3	TIM4_CH4
	AF1	TIM1/2	,	,	,	,	-		1	'	,	,	1	,	,			
	AF0	SYS		,	,	,		1	ı	,	,	,	ı	,	,	1	1	ı
		Port	PDO	PD1	PD2	PD3	PD4	PD5	PD6	Port D	PD8	604	PD10	PD11	PD12	PD13	PD14	PD15
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	AF14 AF15	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT	- EVENTOUT
AF13	DCMI	DCML_D2	DCMI_D3			DCMI_D4	DCMI_D6	DCMI_D7									
AF12	FSMC/SDIO /OTG_FS	FSMC_NBL0 D	FSMC_NBL1 D	FSMC_A23	FSMC_A19	FSMC_A20 D	FSMC_A21 D	FSMC_A22 D	FSMC_D4	FSMC_D5	FSMC_D6	FSMC_D7	FSMC_D8	FSMC_D9	FSMC_D10	FSMC_D11	FSMC_D12
AF11	ETH		,	ETH_MIL_TXD3													
AF10	OTG_FS/ OTG_HS		,	1													
AF9	CAN1/2 TIM12/13/ 14		,		,				,		,	,	,	,		,	
AF8	UART4/5/ USART6																,
AF7	USART1/2/3/ I2S3ext			-													,
AF6	SPI3/I2Sext /I2S3		,														
AF5	SPI1/SPI2/ I2S2/I2S2e xt																
AF4	12C1/2/3		,	-	,						,						,
AF3	TIM8/9/10 /11	,					TIM9_CH1	TIM9_CH2				,					
AF2	TIM 3/4/5	TIM4_ETR	,														
AF1	TIM1/2								TIM1_ETR	TIM1_CH1N	TIM1_CH1	TIM1_CH2N	TIM1_CH2	TIM1_CH3N	TIM1_CH3	TIM1_CH4	TIM1 BKIN
AFO	SYS	,		TRACECL K	<b>TRACED0</b>	TRACED1	TRACED2	TRACED3									,
	Port	PEO	PE1	PE2	PE3	PE4	PE5	PE6	PE7	PE8	PE9	PE10	PE11	PE12	PE13	PE14	PE15
	ē.								Port E								

# Table 9. Alternate function mapping (continued)

Pinouts and pin description



		AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT
		AF14	,			,	,											i.
	AF13	DCMI												DCMI_D12				
	AF12	FSMC/SDIO /OTG_FS	FSMC_A0	FSMC_A1	FSMC_A2	FSMC_A3	FSMC_A4	FSMC_A5	FSMC_NIORD	FSMC_NREG	FSMC_ NIOWR	FSMC_CD	FSMC_INTR		FSMC_A6	FSMC_A7	FSMC_A8	FSMC_A9
	AF11	ЕТН			ı						ı							·
(pər	AF10	OTG_FS/ OTG_HS	,		ı						ı							ı
(continu	AF9	CAN1/2 TIM12/13/ 14				,					TIM13_CH1	TIM14_CH1						,
apping	AF8	UART4/5/ USART6	,	-	-													ı
Table 9. Alternate function mapping (continued)	AF7	USART1/2/3/ I2S3ext	,		ı	,	,		,								,	
ernate fu	AF6	SPI3/I2Sext /I2S3																,
le 9. Alte	AF5	SPI1/SPI2/ I2S2/I2S2e xt		-	-			-	-	-	-		-	-	-	-	-	
Tab	AF4	I2C1/2/3	I2C2_SDA	I2C2_SCL	I2C2_ SMBA_			-	-	-	-		-	-	-	-	-	I
	AF3	TIM8/9/10 /11	,		-				TIM10_CH1	TIM11_CH1				-				,
	AF2	TIM3/4/5	,	-	-			-	-	-	-		-	-	-	-	-	
	AF1	TIM1/2		-														
	AF0	SYS			-					-			-	-				
		Port	PFO	PF1	PF2	PF3	PF4	PF5	PF6	PF7	PF8	PF9	PF10	PF11	PF12	PF13	PF14	PF15
	7/		<b></b>									[	DS8	862	6 R	ev 9	9	

## STM32F405xx, STM32F407xx

## Pinouts and pin description

		AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT						
		AF14		-		-		-	-		-			-				
	AF13	DCMI	,	-									I	1				DCML_D13
	AF12	FSMC/SDIO /OTG_FS	FSMC_A10	FSMC_A11	FSMC_A12	FSMC_A13	FSMC_A14	FSMC_A15	FSMC_INT2	FSMC_INT3		FSMC_NE2/ FSMC_NCE3	FSMC_ NCE4_1/ FSMC_NE3	FSMC_NCE4_	FSMC_NE4	FSMC_A24	FSMC_A25	
	AF11	ЕТН	,	-	-	-		-	-		ETH_PPS_OUT	-	-	ETH_MIL_TX_EN ETH_RMIL_ TX_EN	-	ETH_MIL_TXD0 ETH_RMIL_TXD0	ETH_MIL_TXD1 ETH_RMIL_TXD1	
ued)	AF10	OTG_FS/ OTG_HS									ı		ı	r				
(contin	AF9	CAN1/2 TIM12/13/ 14	,			,	,		,	,								
apping	AF8	UART4/5/ USART6	,							USART6_CK	USART6_ RTS	USART6_RX			USART6_ RTS	UART6_CTS	USART6_TX	USART6_ CTS
Table 9. Alternate function mapping (continued)	AF7	USART1/2/3/ I2S3ext									ı	ı	ı	1	ı		ı	
ernate fu	AF6	SPI3/I2Sext /I2S3	,	-										1				
le 9. Alt	AF5	SPI1/SPI2/ I2S2/I2S2e xt				-		-	-				,	-		-		
Tab	AF4	I2C1/2/3																
	AF3	TIM8/9/10 /11		-	-	-		-	-		-	-			-	-	-	
	AF2	TIM 3/4/5										Ţ	ı	T	Ţ	T	Ţ	
	AF1	TIM1/2	,	-		,			,				I	1				
	AFO	SYS	,	-	1	,	,	,	,	,	-	-	-	-	-	-	-	-
		Port	PG0	PG1	PG2	PG3	PG4	PG5	PG6	PG7	PG8	PG9	PG10	PG11	PG12	PG13	PG14	PG15
		۵.										Port G						

Pinouts and pin description

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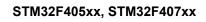
		AF15	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT	EVENTOUT
		AF14	•														-	
	AF13	DCMI					·				DCML	DCMLD0	DCMI_D1	DCMI_D2	DCMI_D3		DCMI_D4	DCMI_D11
	AF12	FSMC/SDIO /OTG_FS			-	-	-	-	-	-	-	-	-	-	-	-	-	
	AF11	ЕТН			ETH_MILCRS	ETH_MILCOL	Ţ	-	ETH_MILRXD2	ETH_MILRXD3		T						
ued)	AF10	OTG_FS/ OTG_HS					OTG_HS_ULPI_ NXT		I		I	I						
(contin	AF9	CAN1/2 TIM12/13/ 14			-		-	-	TIM12_CH1	-	-	TIM12_CH2	-	-	-	CAN1_TX	-	
apping	AF8	UART4/5/ USART6	,		-	-	-	-	-	-	-	-	-	-	-	-	-	
Table 9. Alternate function mapping (continued)	AF7	USART1/2/3/ I2S3ext																
ernate fu	AF6	SPI3/I2Sext /I2S3			-	-	-	-	-	-	-	-	-	-	-	-	-	
le 9. Alt	AF5	SPI1/SPI2/ I2S2/I2S2e xt			-	-	-	-	-	-	-	-	-	-	-	-	-	
Tab	AF4	I2C1/2/3		-	-	-	I2C2_SCL	I2C2_SDA	I2C2_ SMBA	12C3_SCL	I2C3_SDA	I2C3_ SMBA	-	-	-	-	-	
	AF3	TIM8/9/10 /11	,		-		'		,							TIM8_CH1N	TIM8_CH2N	TIM8_CH3N
	AF2	TIM 3/4/5					1	-			1	1	TIM5_CH1	TIM5_CH2	TIM5_CH3			
	AF1	TIM1/2																
	AFO	SYS			-	-	-	-	-	-	-	-	-	,	-	,	,	
		Port	она	PH1	PH2	PH3	PH4	PH5	РН6	2Hd PH7	PULL PH8	6Н9	PH10	PH11	PH12	PH13	PH14	PH15
4	7/											DS8	362	6 R	ev	9		1

## STM32F405xx, STM32F407xx

AF1         AF2         AF3         AF4         AF5           TIM12         TIM3/4/5         TIM8/9/10         I2C1/2/3         SP11/SP12/ S22/2S2e         SP11/SP12/ Xt           -         TIM5_CH4         -         -         SP12_NS5           -         TIM5_CH4         -         SP12_NS5           -         TIM5_CH4         -         SP12_NS5           -         -         TIM5_CH4         -         SP12_NS5           -         -         TIM5_CH4         -         SP12_NS5           -         -         TIM6_CH4         -         SP12_NS5           -         -         -         TIM6_CH4         <	AF6 SPI3/12Sext /12S3	AF7 USART1/2/3/U	AF8	AF9	AE10	A E 11	011			
TIM3:4/5         TIM8:9/10         I2C1/12/3           TIM5_CH4         ·         ·           TIM5_CH4         ·         ·           ·         TIM8_CH4         ·           ·         TIM8_CH1         ·           ·         TIM8_CH1         ·           ·         TIM8_CH1         ·           ·         TIM8_CH1         ·	SPI3/12Sext /12S3					AL	AF12	AF13		
TIM5_CH4     -     -       -     -     -       -     TIM8_CH4     -       -     TIM8_CH4     -       -     TIM8_CH4     -       -     TIM8_CH1     -			UART4/5/ T USART6	CAN1/2 TIM12/13/ 14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO /OTG_FS	DCMI	AF14	AF15
.     .     .       .     TIM8_CH4     .       .     TIM8_ETR     .       .     TIM8_BKIN     .       .     TIM8_CH1     .       .     TIM8_CH2     .       .     TIM8_CH2     .		1		,				DCMI_D13		EVENTOUT
·         TIM8_CH4         ·           ·         TIM8_ETR         ·           ·         TIM8_BKIN         ·           ·         TIM8_LCH4         ·           ·         TIM8_LCH2         ·           ·         TIM8_LCH1         ·						-	-	DCMI_D8		EVENTOUT
- TIMB_ETR TIMB_BKIN TIMB_BKIN TIMB_CH1 TIMB_CH2	I2S2ext_SD						-	DCMI_D9		EVENTOUT
- TIM8_BKIN - TIM8_BKIN - TIM8_BKIN - TIM8_CH1 - TIM8_CH2 - TIM8_CH2 - TIM8_CH3 - TIM8_C		,				,		DCMI_D10		EVENTOUT
	,							DCMI_D5	,	EVENTOUT
						-	-	DCML		EVENTOUT
- TIM8_CH3								DCMI_D6		EVENTOUT
	,			,				DCMI_D7		EVENTOUT
								-		EVENTOUT
			-	CAN1_RX			-	-		EVENTOUT
						ETH_MII_RX_ER	-			EVENTOUT
					OTG_HS_ULPI_ DIR	-	-			EVENTOUT

# Table 9 Alternate function manning (continued)

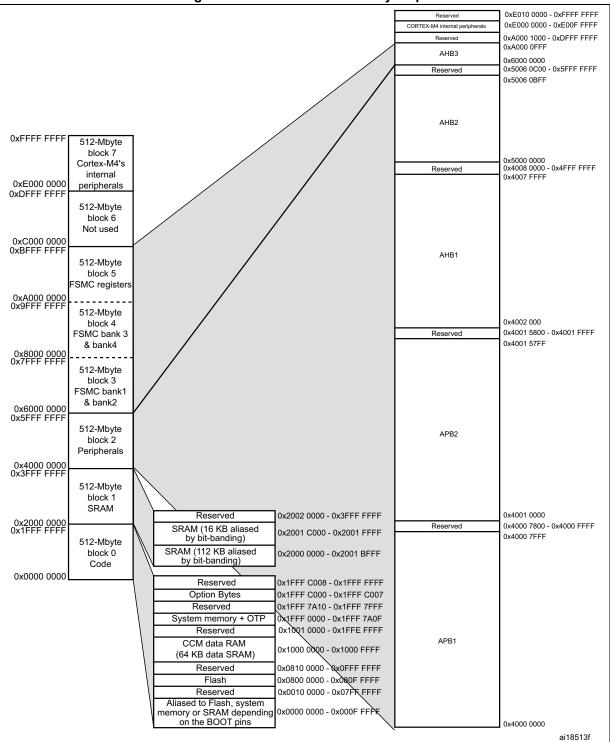
Pinouts and pin description





## 4 Memory mapping

The memory map is shown in *Figure 18*.







Bus	Boundary address	Peripheral
	0xE00F FFFF - 0xFFFF FFFF	Reserved
Cortex-M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals
	0xA000 1000 - 0xDFFF FFFF	Reserved
	0xA000 0000 - 0xA000 0FFF	FSMC control register
	0x9000 0000 - 0x9FFF FFFF	FSMC bank 4
AHB3	0x8000 0000 - 0x8FFF FFFF	FSMC bank 3
	0x7000 0000 - 0x7FFF FFFF	FSMC bank 2
	0x6000 0000 - 0x6FFF FFFF	FSMC bank 1
	0x5006 0C00- 0x5FFF FFFF	Reserved
AHB2	0x5006 0800 - 0x5006 0BFF	RNG
	0x5005 0400 - 0x5006 07FF	Reserved
	0x5005 0000 - 0x5005 03FF	DCMI
	0x5004 0000- 0x5004 FFFF	Reserved
	0x5000 0000 - 0x5003 FFFF	USB OTG FS
	0x4008 0000- 0x4FFF FFFF	Reserved

Table 10. register boundary addresses



Bus	Boundary address	Peripheral
	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 9400 - 0x4003 FFFF	Reserved
	0x4002 9000 - 0x4002 93FF	
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	ETHERNET MAC
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 5FFF	Reserved
AHB1	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2400 - 0x4002 2FFF	Reserved
	0x4002 2000 - 0x4002 23FF	GPIOI
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA
	0x4001 5800- 0x4001 FFFF	Reserved



Bus	Boundary address	Peripheral
	0x4001 4C00 - 0x4001 57FF	Reserved
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	ТІМ9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	Reserved
	0x4001 3000 - 0x4001 33FF	SPI1
APB2	0x4001 2C00 - 0x4001 2FFF	SDIO
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1 - ADC2 - ADC3
	0x4001 1800 - 0x4001 1FFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0800 - 0x4001 0FFF	Reserved
	0x4001 0400 - 0x4001 07FF	TIM8
	0x4001 0000 - 0x4001 03FF	TIM1
	0x4000 7800- 0x4000 FFFF	Reserved

Table 10. register boundary addresses (continued)



Bus	Boundary address	Peripheral
	0x4000 7800 - 0x4000 7FFF	Reserved
	0x4000 7400 - 0x4000 77FF	DAC
	0x4000 7000 - 0x4000 73FF	PWR
	0x4000 6C00 - 0x4000 6FFF	Reserved
	0x4000 6800 - 0x4000 6BFF	CAN2
	0x4000 6400 - 0x4000 67FF	CAN1
	0x4000 6000 - 0x4000 63FF	Reserved
	0x4000 5C00 - 0x4000 5FFF	I2C3
	0x4000 5800 - 0x4000 5BFF	I2C2
	0x4000 5400 - 0x4000 57FF	I2C1
	0x4000 5000 - 0x4000 53FF	UART5
	0x4000 4C00 - 0x4000 4FFF	UART4
	0x4000 4800 - 0x4000 4BFF	USART3
	0x4000 4400 - 0x4000 47FF	USART2
	0x4000 4000 - 0x4000 43FF	I2S3ext
APB1	0x4000 3C00 - 0x4000 3FFF	SPI3 / I2S3
	0x4000 3800 - 0x4000 3BFF	SPI2 / I2S2
	0x4000 3400 - 0x4000 37FF	I2S2ext
	0x4000 3000 - 0x4000 33FF	IWDG
	0x4000 2C00 - 0x4000 2FFF	WWDG
	0x4000 2800 - 0x4000 2BFF	RTC & BKP Registers
	0x4000 2400 - 0x4000 27FF	Reserved
	0x4000 2000 - 0x4000 23FF	TIM14
	0x4000 1C00 - 0x4000 1FFF	TIM13
	0x4000 1800 - 0x4000 1BFF	TIM12
	0x4000 1400 - 0x4000 17FF	TIM7
	0x4000 1000 - 0x4000 13FF	TIM6
	0x4000 0C00 - 0x4000 0FFF	TIM5
	0x4000 0800 - 0x4000 0BFF	TIM4
	0x4000 0400 - 0x4000 07FF	TIM3
	0x4000 0000 - 0x4000 03FF	TIM2

Table 10. register boundary addresses (continued)



# 5 Electrical characteristics

# 5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V<sub>SS</sub>.

#### 5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A = 25$  °C and  $T_A = T_A max$  (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\Sigma$ ).

#### 5.1.2 Typical values

Unless otherwise specified, typical data are based on T<sub>A</sub> = 25 °C, V<sub>DD</sub> = 3.3 V (for the 1.8 V  $\leq$  V<sub>DD</sub>  $\leq$  3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\Sigma$ ).

#### 5.1.3 Typical curves

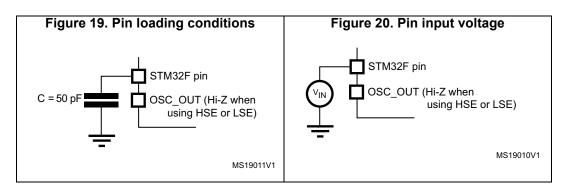
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

#### 5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 19*.

#### 5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 20*.

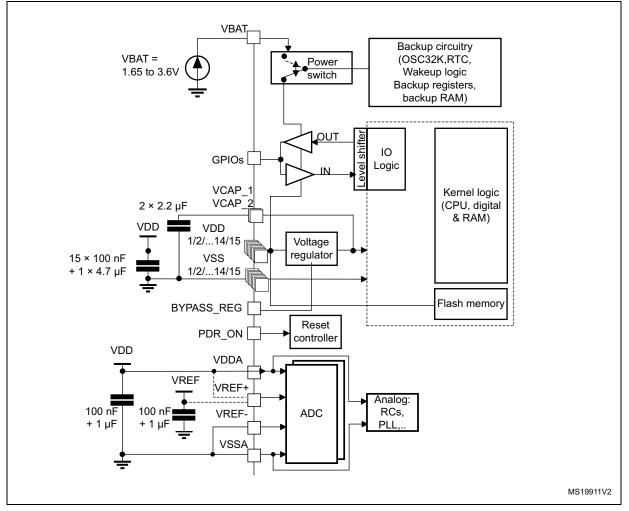




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#### 5.1.6 Power supply scheme



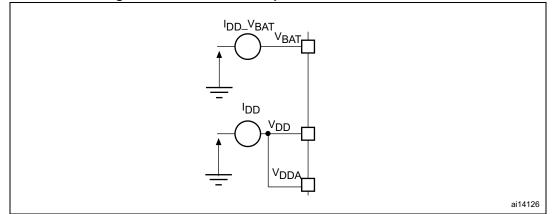
#### Figure 21. Power supply scheme

 Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

- 2. To connect BYPASS\_REG and PDR\_ON pins, refer to Section 2.2.16: Voltage regulator and Table 2.2.15: Power supply supervisor.
- The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
- 4. The 4.7  $\mu F$  ceramic capacitor must be connected to one of the  $V_{DD}$  pin.
- 5.  $V_{DDA}=V_{DD}$  and  $V_{SSA}=V_{SS}$ .



#### 5.1.7 Current consumption measurement



#### Figure 22. Current consumption measurement scheme

# 5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 11: Voltage characteristics*, *Table 12: Current characteristics*, and *Table 13: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard, extended mission profiles are available on demand.

Symbol	Ratings	Min	Мах	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including $V_{DDA}$ , $V_{DD}$ ) <sup>(1)</sup>	-0.3	4.0	
V	Input voltage on five-volt tolerant pin <sup>(2)</sup>	V <sub>SS</sub> -0.3	V <sub>DD</sub> +4	V
V <sub>IN</sub>	Input voltage on any other pin	V <sub>SS</sub> -0.3	4.0	
ΔV <sub>DDx</sub>	Variations between different V <sub>DD</sub> power pins	-	50	
V <sub>SSX</sub> – V <sub>SS</sub>	Variations between all the different ground pins including V <sub>REF</sub> _	-	50	mV
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	see Sectio Absolute n ratings (ele sensitivity)	naximum ectrical	

#### Table 11. Voltage characteristics

 All main power (V<sub>DD</sub>, V<sub>DDA</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supply, in the permitted range.

2.  $V_{IN}$  maximum value must always be respected. Refer to *Table 12* for the values of the maximum allowed injected current.



Symbol	Ratings	Max.	Unit
I <sub>VDD</sub>	Total current into V <sub>DD</sub> power lines (source) <sup>(1)</sup>	240	
I <sub>VSS</sub>	Total current out of $V_{SS}$ ground lines $(sink)^{(1)}$	240	
1	Output current sunk by any I/O and control pin	25	
IIO	Output current source by any I/Os and control pin	25	mA
ı (2)	Injected current on five-volt tolerant I/O <sup>(3)</sup>	-5/+0	
I <sub>INJ(PIN)</sub> <sup>(2)</sup>	Injected current on any other pin <sup>(4)</sup>	±5	
$\Sigma I_{\rm INJ(PIN)}^{(4)}$	Total injected current (sum of all I/O and control pins) <sup>(5)</sup>	±25	

#### Table 12. Current characteristics

1. All main power ( $V_{DD}$ ,  $V_{DDA}$ ) and ground ( $V_{SS}$ ,  $V_{SSA}$ ) pins must always be connected to the external power supply, in the permitted range.

2. Negative injection disturbs the analog performance of the device. See note in Section 5.3.21: 12-bit ADC characteristics.

3. Positive injection is not possible on these I/Os. A negative injection is induced by  $V_{IN} < V_{SS}$ .  $I_{INJ(PIN)}$  must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.

4. A positive injection is induced by  $V_{IN} > V_{DD}$  while a negative injection is induced by  $V_{IN} < V_{SS}$ .  $I_{INJ(PIN)}$  must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.

5. When several inputs are submitted to a current injection, the maximum  $\Sigma I_{INJ(PIN)}$  is the absolute sum of the positive and negative injected currents (instantaneous values).

#### Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T <sub>STG</sub>	Storage temperature range	–65 to +150	°C
TJ	Maximum junction temperature	125	°C

# 5.3 Operating conditions

# 5.3.1 General operating conditions

#### Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	Internal AHB clock frequency	VOS bit in PWR_CR register = $0^{(1)}$	0	-	144	
f <sub>HCLK</sub>	Internal AI ID Clock frequency	VOS bit in PWR_CR register= 1	0	-	168	MHz
f <sub>PCLK1</sub>	Internal APB1 clock frequency	-	0	-	42	
f <sub>PCLK2</sub>	Internal APB2 clock frequency	-	0	-	84	
V <sub>DD</sub>	Standard operating voltage	-	1.8 <sup>(2)</sup>	-	3.6	V
V <sub>DDA</sub> <sup>(3)(4)</sup>	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as	1.8 <sup>(2)</sup>	-	2.4	V
*DDA````	Analog operating voltage (ADC limited to 1.4 M samples)	V <sub>DD</sub> <sup>(5)</sup>	2.4	-	3.6	v
V <sub>BAT</sub>	Backup operating voltage	-	1.65	-	3.6	V



Symbol	Parameter	Conditions	, Min	Тур	Max	Unit	
	Regulator ON:	VOS bit in PWR_CR register = 0 <sup>(1)</sup> Max frequency 144MHz	1.08	1.14	1.20	V	
V <sub>12</sub>	1.2 V internal voltage on $V_{CAP_1}/V_{CAP_2}$ pins	VOS bit in PWR_CR register= 1 Max frequency 168MHz	1.20	1.26	1.32	V	
12	Regulator OFF:	Max frequency 144MHz	1.10	1.14	1.20	V	
	1.2 V external voltage must be supplied from external regulator on $V_{CAP_1}/V_{CAP_2}$ pins	Max frequency 168MHz	1.20	1.26	1.30	V	
	Input voltage on RST and FT	$2 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.6 \text{ V}$	-0.3	-	5.5		
	pins <sup>(6)</sup> Input voltage on TTa pins	$V_{DD} \le 2 V$	-0.3	-	5.2		
V <sub>IN</sub>		-	-0.3	-	V <sub>DDA</sub> + 0.3	V	
	Input voltage on B pin	-	-	-	5.5		
		LQFP64	-	-	435	mW	
		LQFP100	-	-	465		
PD	Power dissipation at $T_A = 85 \degree C$	LQFP144	-	-	500		
۳D	for suffix 6 or $T_A = 105 \text{ °C}$ for suffix 7 <sup>(7)</sup>	LQFP176	-	-	526		
		UFBGA176	-	-	513		
		WLCSP90	-	-	543		
	Ambient temperature for 6 suffix	Maximum power dissipation	-40	-	85	°C	
т.	version	Low-power dissipation <sup>(8)</sup>	-40	-	105	Ĵ	
ΤΑ	Ambient temperature for 7 suffix	Maximum power dissipation	-40	-	105	°C	
	version	Low-power dissipation <sup>(8)</sup>	-40	-	125	C	
TJ	Junction temperature range	6 suffix version	-40	-	105	°C	
IJ	Surveyor temperature range	7 suffix version	-40	-	125	ι.	

Table 14. General oper	rating conditions	(continued)
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1. The average expected gain in power consumption when VOS = 0 compared to VOS = 1 is around 10% for the whole temperature range, when the system clock frequency is between 30 and 144 MHz.

 V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to Section : Internal reset OFF).

3. When the ADC is used, refer to *Table 67: ADC characteristics*.

4. If V<sub>REF+</sub> pin is present, it must respect the following condition: V<sub>DDA</sub>-V<sub>REF+</sub> < 1.2 V.

5. It is recommended to power  $V_{DD}$  and  $V_{DDA}$  from the same source. A maximum difference of 300 mV between  $V_{DD}$  and  $V_{DDA}$  can be tolerated during power-up and power-down operation.

6. To sustain a voltage higher than  $V_{DD}$ +0.3, the internal pull-up and pull-down resistors must be disabled.

7. If  $T_A$  is lower, higher  $\mathsf{P}_D$  values are allowed as long as  $T_J$  does not exceed  $T_{Jmax}$ 

8. In low-power dissipation state,  $T_A$  can be extended to this range as long as  $T_J$  does not exceed  $T_{Jmax}$ .



Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait state (f <sub>Flashmax</sub> )	Maximum Flash memory access frequency with wait states <sup>(1) (2)</sup>	I/O operation	Clock output Frequency on I/O pins	Possible Flash memory operations
V <sub>DD</sub> =1.8 to 2.1 V <sup>(3)</sup>	Conversion time up to 1.2 Msps	20 MHz <sup>(4)</sup>	160 MHz with 7 wait states	<ul> <li>Degraded speed performance</li> <li>No I/O compensation</li> </ul>	up to 30 MHz	8-bit erase and program operations only
V <sub>DD</sub> = 2.1 to 2.4 V	Conversion time up to 1.2 Msps	22 MHz	168 MHz with 7 wait states	<ul> <li>Degraded speed performance</li> <li>No I/O compensation</li> </ul>	up to 30 MHz	16-bit erase and program operations
V <sub>DD</sub> = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	168 MHz with 6 wait states	<ul> <li>Degraded speed performance</li> <li>I/O compensation works</li> </ul>	up to 48 MHz	16-bit erase and program operations
V <sub>DD</sub> = 2.7 to 3.6 V <sup>(5)</sup>	Conversion time up to 2.4 Msps	30 MHz	168 MHz with 5 wait states	<ul> <li>Full-speed operation</li> <li>I/O compensation works</li> </ul>	$\begin{array}{l} - \text{ up to} \\ 60 \text{ MHz} \\ \text{when } \text{V}_{\text{DD}} = \\ 3.0 \text{ to } 3.6 \text{ V} \\ - \text{ up to} \\ 48 \text{ MHz} \\ \text{when } \text{V}_{\text{DD}} = \\ 2.7 \text{ to } 3.0 \text{ V} \end{array}$	32-bit erase and program operations

Table 15. Limitations depending on the operating power supply range

1. It applies only when code executed from Flash memory access, when code executed from RAM, no wait state is required.

2. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.

3. V<sub>DD</sub>/VDDA minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).

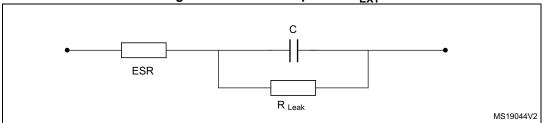
4. Prefetch is not available. Refer to AN3430 application note for details on how to adjust performance and power.

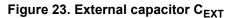
5. The voltage range for OTG USB FS can drop down to 2.7 V. However it is degraded between 2.7 and 3 V.



# 5.3.2 V<sub>CAP\_1</sub>/V<sub>CAP\_2</sub> external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor  $C_{EXT}$  to the  $V_{CAP}$   $_1/V_{CAP}$   $_2$  pins.  $C_{EXT}$  is specified in *Table 16*.





1. Legend: ESR is the equivalent series resistance.

Table 16.  $V_{CAP 1}/V_{CAP 2}$  operating conditions<sup>(1)</sup>

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 µF
ESR	ESR of external capacitor	< 2 Ω

1. When bypassing the voltage regulator, the two 2.2  $\mu$ F V<sub>CAP</sub> capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

#### 5.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T<sub>A</sub>.

Table 17. Operating conditions at power-up /	power-down (regulator ON)
--	---------------------------

Symbol	mbol Parameter		Мах	Unit
	V <sub>DD</sub> rise time rate	20	8	µs/V
τ <sub>VDD</sub>	V <sub>DD</sub> fall time rate	20	8	μο/ ν

## 5.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T<sub>A</sub>.

#### Table 18. Operating conditions at power-up / power-down (regulator OFF)<sup>(1)</sup>

			•	,	
Symbol	Parameter	Conditions	Min	Мах	Unit
+	V <sub>DD</sub> rise time rate	Power-up	20	∞	
t <sub>VDD</sub>	V <sub>DD</sub> fall time rate	Power-down	20	8	
	$V_{CAP\_1}$ and $V_{CAP\_2}$ rise time rate	Power-up	20	8	µs/V
t <sub>VCAP</sub>	$V_{CAP\_1}$ and $V_{CAP\_2}$ fall time rate	Power-down	20	8	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when  $V_{DD}$  reach below minimum value of  $V_{12}$ .



# 5.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 19* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	V
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	V
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	V
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	V
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	$\sim$
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	V
V <sub>PVD</sub>	Programmable voltage detector level selection	PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	V
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	V
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	V
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	V
		PLS[2:0]=101 (falling edge)	2.75	2.84	2.92	V
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	V
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	V
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	V
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	V
V <sub>PVDhyst</sub> <sup>(1)</sup>	PVD hysteresis	-	-	100	-	mV
	Power-on/power-down	Falling edge	1.60	1.68	1.76	V
V <sub>POR/PDR</sub>	reset threshold	Rising edge	1.64	1.72	1.80	V
V <sub>PDRhyst</sub> <sup>(1)</sup>	PDR hysteresis	-	-	40	-	mV
	Brownout level 1	Falling edge	2.13	2.19	2.24	V
V <sub>BOR1</sub>	threshold	Rising edge	2.23	2.29	2.33	V



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
N	Brownout level 2	Falling edge	2.44	2.50	2.56	V
V <sub>BOR2</sub>	threshold	Rising edge	2.53	2.59	2.63	V
V	Brownout level 3	Falling edge	2.75	2.83	2.88	V
V <sub>BOR3</sub>	threshold	Rising edge	2.85	2.92	2.97	V
V <sub>BORhyst</sub> <sup>(1)</sup>	BOR hysteresis	-	-	100	-	mV
T <sub>RSTTEMPO</sub> <sup>(1)(2)</sup>	Reset temporization	-	0.5	1.5	3.0	ms
I <sub>RUSH</sub> <sup>(1)</sup>	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
E <sub>RUSH</sub> <sup>(1)</sup>	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	V <sub>DD</sub> = 1.8 V, T <sub>A</sub> = 105 °C, I <sub>RUSH</sub> = 171 mA for 31 μs	-	-	5.4	μC

 Table 19. Embedded reset and power control block characteristics (continued)

1. Guaranteed by design.

2. The reset temporization is measured from the power-on (POR reset or wakeup from  $V_{BAT}$ ) to the instant when first instruction is read by the user application code.

#### 5.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 22: Current consumption measurement scheme*.

All Run mode current consumption measurements given in this section are performed using a CoreMark-compliant code.

#### Typical and maximum current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted to f<sub>HCLK</sub> frequency (0 wait state from 0 to 30 MHz, 1 wait state from 30 to 60 MHz, 2 wait states from 60 to 90 MHz, 3 wait states from 90 to 120 MHz, 4 wait states from 120 to 150 MHz, and 5 wait states from 150 to 168 MHz).
- When the peripherals are enabled HCLK is the system clock, f<sub>PCLK1</sub> = f<sub>HCLK</sub>/4, and f<sub>PCLK2</sub> = f<sub>HCLK</sub>/2, except is explicitly mentioned.
- The maximum values are obtained for  $V_{DD}$  = 3.6 V and maximum ambient temperature (T<sub>A</sub>), and the typical values for T<sub>A</sub>= 25 °C and V<sub>DD</sub> = 3.3 V unless otherwise specified.



				Тур	Ма	x <sup>(2)</sup>	
Symbol	Parameter	Conditions	fhclk	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit
			168 MHz	87	102	109	
			144 MHz	67	80	86	
			120 MHz	56	69	75	
			90 MHz	44	56	62	
		(2)	60 MHz	30	42	49	
		External clock <sup>(3)</sup> , all peripherals enabled <sup>(4)(5)</sup>	30 MHz	16	28	35	
			25 MHz	12	24	31	
			~	16 MHz <sup>(6)</sup>	9	20	28
			8 MHz	5	17	24	-
			4 MHz	3	15	22	
	Supply current in		2 MHz	2	14	21	m 4
I <sub>DD</sub>	Run mode		168 MHz	40	54	61	mA
			144 MHz	31	43	50	
			120 MHz	26	38	45	
			90 MHz	20	32	39	
		(2)	60 MHz	14	26	33	1
		External clock <sup>(3)</sup> , all peripherals disabled <sup>(4)(5)</sup>	30 MHz	8	20	27	
			25 MHz	6	18	25	1
			16 MHz <sup>(6)</sup>	5	16	24	
			8 MHz	3	15	22	
			4 MHz	2	14	21	
			2 MHz	2	14	21	

# Table 20. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM <sup>(1)</sup>

1. Code and data processing running from SRAM1 using boot pins.

2. Guaranteed by characterization, tested in production at V<sub>DD</sub> max and f<sub>HCLK</sub> max with peripherals enabled.

3. External clock is 4 MHz and PLL is on when f<sub>HCLK</sub> > 25 MHz.

4. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

5. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.

6. In this case HCLK = system clock/2.



0h.e.l	Demonster	O an diffion a	onditions fuci K		Ма	ax <sup>(1)</sup>	11 14	
Symbol	Parameter	Conditions	f <sub>HCLK</sub>	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit	
			168 MHz	93	109	117		
				144 MHz	76	89	96	
			120 MHz	67	79	86		
			90 MHz	53	65	73		
		External clock <sup>(2)</sup> ,	60 MHz	37	49	56		
		all peripherals	30 MHz	20	32	39		
		enabled <sup>(3)(4)</sup>	25 MHz	16	27	35		
		nt	16 MHz	11	23	30		
				8 MHz	6	18	25	
				4 MHz	4	16	23	
	Supply current			2 MHz	3	15	22	
I <sub>DD</sub>	in Run mode		168 MHz	46	61	69	mA	
			144 MHz	40	52	60		
			120 MHz	37	48	56		
			90 MHz	30	42	50		
		External clock <sup>(2)</sup> ,	60 MHz	22	33	41		
		all peripherals	30 MHz	12	24	31		
		disabled <sup>(3)(4)</sup>	25 MHz	10	21	29		
			16 MHz	7	19	26		
			8 MHz	4	16	23		
			4 MHz	3	15	22		
			2 MHz	2	14	21		

# Table 21. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

1. Guaranteed by characterization, tested in production at  $V_{DD}$  max and  $f_{HCLK}$  max with peripherals enabled.

2. External clock is 4 MHz and PLL is on when  $f_{HCLK}$  > 25 MHz.

3. When analog peripheral blocks such as (ADCs, DACs, HSE, LSE, HSI,LSI) are on, an additional power consumption should be considered.

4. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.





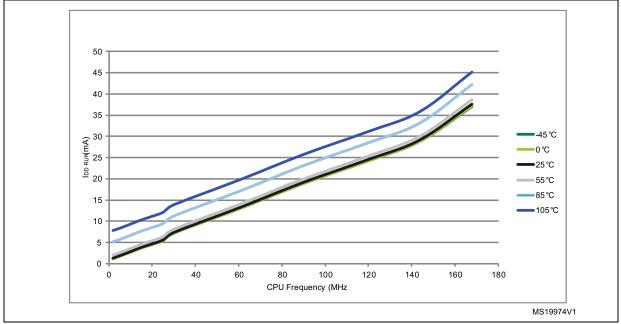
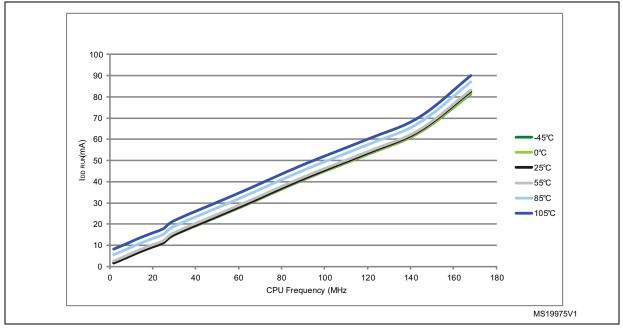


Figure 25. Typical current consumption versus temperature, Run mode, code with data processing running from Flash (ART accelerator ON) or RAM, and peripherals ON





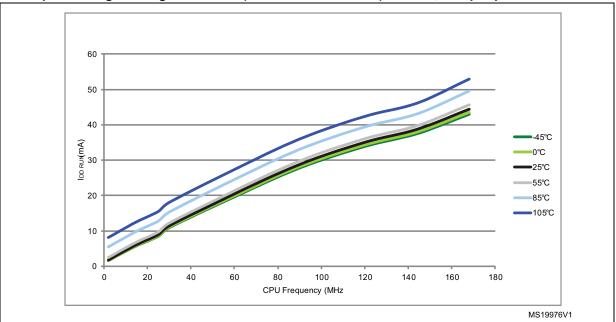
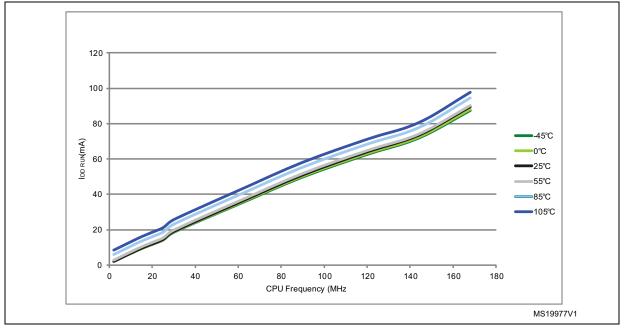


Figure 26. Typical current consumption versus temperature, Run mode, code with data processing running from Flash (ART accelerator OFF) or RAM, and peripherals OFF

# Figure 27. Typical current consumption versus temperature, Run mode, code with data processing running from Flash (ART accelerator OFF) or RAM, and peripherals ON





				Тур	Ма	x <sup>(1)</sup>			
Symbol	Parameter	Conditions	<sup>f</sup> нсlк	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit		
			168 MHz	59	77	84			
			144 MHz	46	61	67			
			120 MHz	38	53	60			
			90 MHz	30	44	51			
		(2)	60 MHz	20	34	41			
		External clock <sup>(2)</sup> , all peripherals enabled <sup>(3)</sup>	30 MHz	11	24	31			
			25 MHz	8	21	28			
					16 MHz	6	18	25	
			8 MHz	3	16	23			
			4 MHz	2	15	22			
	Supply current in		2 MHz	2	14	21	mA		
I <sub>DD</sub>	Sleep mode		168 MHz	12	27	35	ШA		
			144 MHz	9	22	29			
			120 MHz	8	20	28			
			90 MHz	7	19	26			
			60 MHz	5	17	24			
		External clock <sup>(2)</sup> , all peripherals disabled	30 MHz	3	16	23			
			25 MHz	2	15	22			
			16 MHz	2	14	21			
			8 MHz	1	14	21			
			4 MHz	1	13	21			
			2 MHz	1	13	21			

1. Guaranteed by characterization, tested in production at  $V_{DD}$  max and  $f_{HCLK}$  max with peripherals enabled.

2. External clock is 4 MHz and PLL is on when  $f_{HCLK}$  > 25 MHz.

3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC\_CR2 register).



					Max		
Symbol	Parameter	Conditions	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 25 °C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit
	Supply current in	Flash in Stop mode, low-speed and high- speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.45	1.5	11.00	20.00	
Stop mode with main regulator in Run mode	Flash in Deep power-down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.40	1.5	11.00	20.00	mA	
IDD_STOP	Supply current in Stop mode	Flash in Stop mode, low-speed and high- speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.31	1.1	8.00	15.00	
	with main regulator in Low-power mode	Flash in Deep power-down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.28	1.1	8.00	15.00	

#### Table 23. Typical and maximum current consumptions in Stop mode

#### Table 24. Typical and maximum current consumptions in Standby mode

Symbol Parameter				Тур		Ма	ıx <sup>(1)</sup>	
		Conditions	Т	A = 25 °0	0	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit
			V <sub>DD</sub> = 1.8 V	V <sub>DD</sub> = 2.4 V	V <sub>DD</sub> = 3.3 V	V <sub>DD</sub> =	= 3.6 V	
		Backup SRAM ON, low- speed oscillator and RTC ON	3.0	3.4	4.0	20	36	
	Supply current in Standby	Backup SRAM OFF, low- speed oscillator and RTC ON	2.4	2.7	3.3	16	32	
I <sub>DD_STBY</sub> In Standby mode	Backup SRAM ON, RTC OFF	2.4	2.6	3.0	12.5	24.8	μA	
		Backup SRAM OFF, RTC OFF	1.7	1.9	2.2	9.8	19.2	

1. Guaranteed by characterization.

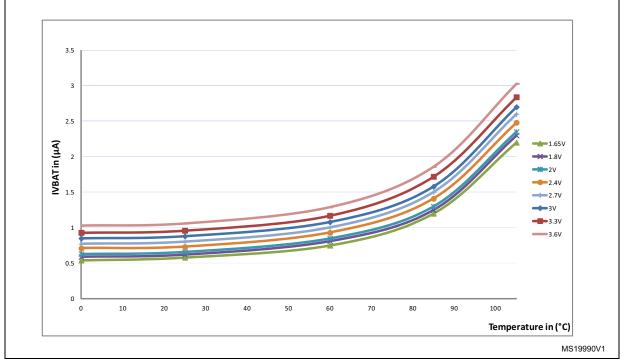


				Тур			Max <sup>(1)</sup>		
Symbol Parameter		Conditions	Т	A = 25 °	C	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit	
			V <sub>BAT</sub> = 1.8 V	V <sub>BAT</sub> = 2.4 V	V <sub>BAT</sub> = 3.3 V	V <sub>BAT</sub> =	= 3.6 V		
	Pookup	Backup SRAM ON, low-speed oscillator and RTC ON	1.29	1.42	1.68	6	11		
I <sub>DD_VBA</sub>	a constant of	Backup SRAM OFF, low-speed oscillator and RTC ON	0.62	0.73	0.96	3	5	μA	
current	Backup SRAM ON, RTC OFF	0.79	0.81	0.86	5	10			
		Backup SRAM OFF, RTC OFF	0.10	0.10	0.10	2	4		

Table 25. Typical and maximum current consumptions in V<sub>BAT</sub> mode

1. Guaranteed by characterization.







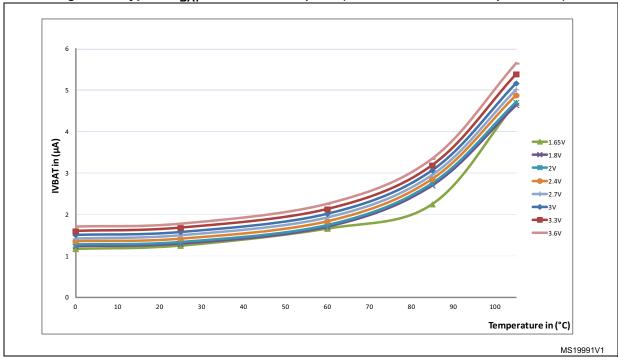


Figure 29. Typical  $V_{BAT}$  current consumption (LSE and RTC ON/backup RAM ON)



#### Additional current consumption

The MCU is placed under the following conditions:

- All I/O pins are configured in analog mode.
- The Flash memory access time is adjusted to f<sub>HCLK</sub> frequency.
- The voltage scaling is adjusted to f<sub>HCLK</sub> frequency as follows:
  - Scale 2 for f<sub>HCLK</sub> ≤ 144 MHz
  - Scale 1 for 144 MHz <  $f_{HCLK} \le 168$  MHz.
- The system clock is HCLK,  $f_{PCLK1} = f_{HCLK}/4$ , and  $f_{PCLK2} = f_{HCLK}/2$ .
- The HSE crystal clock frequency is 25 MHz.
- T<sub>A</sub>= 25 °C.

# Table 26. Typical current consumption in Run mode, code with data processing running from Flash memory, regulator ON (ART accelerator enabled except prefetch), $V_{DD} = 1.8 V^{(1)}$

Symbol	Parameter	Conditions	f <sub>HCLK</sub> (MHz)	Typ. at T <sub>A</sub> = 25 °C	Unit
			160	36.2	
			144	29.3	
			120	24.7	
IDD	Supply current in Run mode	All peripheral disabled	90	19.3	mA
			60	13.4	
			30	7.7	
			25	6.0	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC or DAC) is not included.

#### I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 48: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

**Caution:** Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to



floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 28: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

 $I_{\text{SW}}$  is the current sunk by a switching I/O to charge/discharge the capacitive load

 $V_{DD}$  is the MCU supply voltage

 $f_{\mbox{SW}}$  is the I/O switching frequency

C is the total capacitance seen by the I/O pin: C =  $C_{INT}$ +  $C_{EXT}$ 

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

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Symbol	Parameter	Conditions <sup>(1)</sup>	l/O toggling frequency (f <sub>SW</sub> )	Тур	Unit
			2 MHz	0.02	
		V <sub>DD</sub> = 3.3 V <sup>(2)</sup>	8 MHz	0.14	
		$C = C_{INT}$	25 MHz	0.51	mA
			50 MHz	0.86	
I <sub>DDIO</sub>			60 MHz	1.30	
		V <sub>DD</sub> = 3.3 V	2 MHz	0.10	
			8 MHz	0.38	
		C <sub>EXT</sub> = 0 pF	25 MHz	1.18	
		$C = C_{INT} + C_{EXT} + C_S$	50 MHz	2.47	
			60 MHz	2.86	
			2 MHz	0.17	
	I/O switching	V <sub>DD</sub> = 3.3 V	8 MHz	0.66	
	current	C <sub>EXT</sub> = 10 pF	25 MHz	1.70	mA
		$C = C_{INT} + C_{EXT} + C_S$	50 MHz	2.65	
			60 MHz	3.48	
			2 MHz	0.23	
		V <sub>DD</sub> = 3.3 V	8 MHz	0.95	
		C <sub>EXT</sub> = 22 pF	25 MHz	3.20	
		$C = C_{INT} + C_{EXT} + C_S$	50 MHz	4.69	
			60 MHz	8.06	
			2 MHz	0.30	
		V <sub>DD</sub> = 3.3 V	8 MHz	1.22	
		C <sub>EXT</sub> = 33 pF	25 MHz	3.90	
		$C = C_{INT} + C_{EXT} + C_S$	50 MHz	8.82	
			60 MHz	_(3)	

1.  $C_S$  is the PCB board capacitance including the pad pin.  $C_S$  = 7 pF (estimated value).

2. This test is performed by cutting the LQFP package pin (pad removal).

3. At 60 MHz, C maximum load is specified 30 pF.



#### **On-chip peripheral current consumption**

The current consumption of the on-chip peripherals is given in *Table 28*. The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog pins by firmware.
- All peripherals are disabled unless otherwise mentioned
- The code is running from Flash memory and the Flash memory access time is equal to 5 wait states at 168 MHz.
- The code is running from Flash memory and the Flash memory access time is equal to 4 wait states at 144 MHz, and the power scale mode is set to 2.
- The ART accelerator is ON.
- The given value is calculated by measuring the difference of current consumption
  - with all peripherals clocked off
  - with one peripheral clocked on (with only the clock applied)
- When the peripherals are enabled: HCLK is the system clock, f<sub>PCLK1</sub> = f<sub>HCLK</sub>/4, and f<sub>PCLK2</sub> = f<sub>HCLK</sub>/2.
- The typical values are obtained for V<sub>DD</sub> = 3.3 V and T<sub>A</sub>= 25 °C, unless otherwise specified.

		I <sub>DD</sub> (1	ӯр) <sup>(1)</sup>	
Peripheral		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	Unit
	GPIOA	2.70	2.40	
	GPIOB	2.50	2.22	
	GPIOC	2.54	2.28	1
	GPIOD	2.55	2.28	1
	GPIOE	2.68	2.40	1
AHB1	GPIOF	2.53	2.28	1
	GPIOG	2.51	2.22	
	GPIOH	2.51	2.22	1
	GPIOI	2.50	2.22	µA/MHz
(up to 168 MHz)	OTG_HS+ULPI	28.33	25.38	1
	CRC	0.41	0.40	1
	BKPSRAM	0.63	0.58	1
	DMA1	37.44	33.58	1
	DMA2	37.69	33.93	1
	ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	20.43	18.39	

Table 28. Peripheral current consumption

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		I <sub>DD</sub> (1	l <sub>DD</sub> (Typ) <sup>(1)</sup>		
Peripheral OTG FS		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	Unit	
	OTG_FS	26.45	26.67		
AHB2 (up to 168 MHz)	DCMI	5.87	5.35	µA/MHz	
	RNG	1.50	1.67	1	
AHB3 (up to 168 MHz)	FSMC	12.46	11.31	µA/MH2	
Bus m	atrix <sup>(2)</sup>	13.10	11.81	µA/MH	
	TIM2	16.71	16.50		
	TIM3	12.33	11.94	1	
	TIM4	13.45	12.92	1	
	TIM5	17.14	16.58		
	TIM6	2.43	3.06		
	TIM7	2.43	2.22		
	TIM12	6.62	6.83	-	
	TIM13	5.05	5.47		
	TIM14	5.26	5.61		
	PWR	1.00	0.56		
	USART2	2.69	2.78		
	USART3	2.74	2.78		
APB1 (up to 42 MHz)	UART4	3.24	3.33	µA/MH	
(up to 42 Wi 12)	UART5	2.69	2.78		
	I2C1	2.67	2.50		
	I2C2	2.83	2.78		
	I2C3	2.81	2.78	1	
	SPI2	2.43	2.22		
	SPI3	2.43	2.22	1	
	I2S2 <sup>(3)</sup>	2.43	2.22	1	
	I2S3 <sup>(3)</sup>	2.26	2.22	1	
	CAN1	5.12	5.56	1	
	CAN2	4.81	5.28	1	
	DAC <sup>(4)</sup>	1.67	1.67	1	
	WWDG	1.00	0.83	1	

Table 28. Peripheral current consumption (continued)



		I <sub>DD</sub> (1	īyp) <sup>(1)</sup>	
Peripheral		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	Unit
	SDIO	7.08	7.92	
	TIM1	16.79	15.51	
	TIM8	17.88	16.53	
APB2 (up to 84 MHz)	TIM9	7.64	7.28	
	TIM10	4.89	4.82	
	TIM11	5.19	4.82	
	ADC1 <sup>(5)</sup>	4.67	4.58	µA/MHz
	ADC2 <sup>(5)</sup>	4.67	4.58	
	ADC3 <sup>(5)</sup>	4.43	4.44	
	SPI1	1.32	1.39	
	USART1	3.51	3.72	1
	USART6	3.55	3.75	1
	SYSCFG	0.74	0.56	1

Table 28. Peripheral current consumption (continued)

1. When the I/O compensation cell is ON,  $I_{DD}$  typical value increases by 0.22 mA.

2. The BusMatrix is automatically active when at least one master is ON.

- 3. To enable an I2S peripheral, first set the I2SMOD bit and then the I2SE bit in the SPI\_I2SCFGR register.
- 4. When the DAC is ON and EN1/2 bits are set in DAC\_CR register, add an additional power consumption of 0.8 mA per DAC channel for the analog part.
- 5. When the ADC is ON (ADON bit set in the ADC\_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

#### 5.3.7 Wakeup time from low-power mode

The wakeup times given in *Table 29* is measured on a wakeup phase with a 16 MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.



Symbol	Parameter	Min <sup>(1)</sup>	Typ <sup>(1)</sup>	Max <sup>(1)</sup>	Unit
t <sub>WUSLEEP</sub> <sup>(2)</sup>	Wakeup from Sleep mode	-	5	-	CPU clock cycle
	Wakeup from Stop mode (regulator in Run mode and Flash memory in Stop mode)	-	13	-	
twustop <sup>(2)</sup>	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Stop mode)	-	17	40	us
	Wakeup from Stop mode (regulator in Run mode and Flash memory in Deep power-down mode)	-	105	-	μο
	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Deep power-down mode)	-	110	-	
t <sub>WUSTDBY</sub> <sup>(2)(3)</sup>	Wakeup from Standby mode	260	375	480	μs

Table 29. Low-power mode wakeup timir	ngs
---------------------------------------	-----

1. Guaranteed by characterization.

2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.

3.  $t_{WUSTDBY}$  minimum and maximum values are given at 105 °C and -45 °C, respectively.

## 5.3.8 External clock source characteristics

#### High-speed external user clock generated from an external source

The characteristics given in *Table 30* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSE_ext</sub>	External user clock source frequency <sup>(1)</sup>		1	-	50	MHz
V <sub>HSEH</sub>	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	$V_{DD}$	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage	_	$V_{SS}$	-	0.3V <sub>DD</sub>	v
t <sub>w(HSE)</sub> t <sub>w(HSE)</sub>	OSC_IN high or low time <sup>(1)</sup>		5	-	-	ns
t <sub>r(HSE)</sub> t <sub>f(HSE)</sub>	OSC_IN rise or fall time <sup>(1)</sup>		-	-	10	115
C <sub>in(HSE)</sub>	OSC_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
DuCy <sub>(HSE)</sub>	Duty cycle	-	45	-	55	%
١L	OSC_IN Input leakage current	$V_{SS} \! \leq \! V_{IN} \! \leq \! V_{DD}$	-	-	±1	μA

Table 30. High-speed external user clock characteristics
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1. Guaranteed by design.



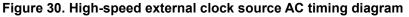
#### Low-speed external user clock generated from an external source

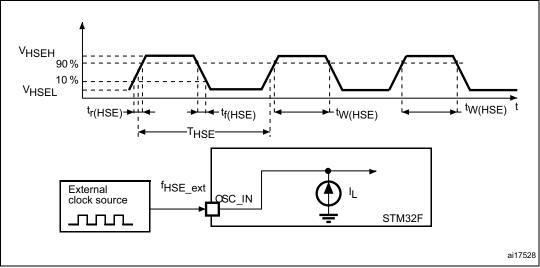
The characteristics given in *Table 31* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSE_ext</sub>	User External clock source frequency <sup>(1)</sup>		-	32.768	1000	kHz
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	-	V <sub>SS</sub>	-	0.3V <sub>DD</sub>	
t <sub>w(LSE)</sub> t <sub>f(LSE)</sub>	OSC32_IN high or low time <sup>(1)</sup>		450	-	-	ns
t <sub>r(LSE)</sub> t <sub>f(LSE)</sub>	OSC32_IN rise or fall time <sup>(1)</sup>		-	-	50	115
C <sub>in(LSE)</sub>	OSC32_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
DuCy <sub>(LSE)</sub>	Duty cycle	-	30	-	70	%
١L	OSC32_IN Input leakage current	$V_{SS}\!\le\!V_{IN}\!\le\!V_{DD}$	_	-	±1	μA

Table 31. Low-speed	external user	clock characteristics
	0/11011141 4001	

1. Guaranteed by design.







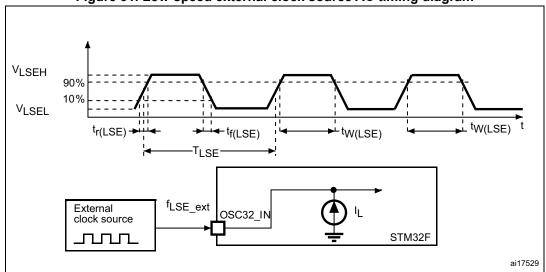


Figure 31. Low-speed external clock source AC timing diagram

#### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 32*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>OSC_IN</sub>	Oscillator frequency	-	4	-	26	MHz
R <sub>F</sub>	Feedback resistor	-	-	200	-	kΩ
G <sub>m</sub>	Oscillator transconductance	Statup	5	-	-	mA/V
G <sub>mcritmax</sub>	Maximum critical crystal G <sub>m</sub>	Startup	-	-	1	IIIAV V
t <sub>SU(HSE)</sub> <sup>(2)</sup>	Startup time	$V_{\text{DD}}$ is stabilized	-	2	-	ms

Table 32. HSE 4-26 MHz oscillator characteristics <sup>(1)</sup>

1. Guaranteed by design.

 Guaranteed by characterization. t<sub>SU(HSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and can vary significantly with the crystal manufacturer

For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 32*).  $C_{L1}$  and  $C_{L2}$  are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing  $C_{L1}$  and  $C_{L2}$ .



Note:

For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website <a href="https://www.st.com">www.st.com</a>.

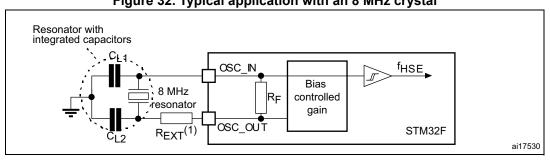


Figure 32. Typical application with an 8 MHz crystal

1. R<sub>EXT</sub> value depends on the crystal characteristics.

#### Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 33*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Parameter Conditions I		Тур	Мах	Unit	
f <sub>OSC_IN</sub>	Oscillator frequency	-	-	32.768	-	MHz	
R <sub>F</sub>	Feedback resistor	-	-	18.4	-	MΩ	
I <sub>DD</sub>	LSE current consumption	-	-	-	1	μA	
G <sub>m</sub>	Oscillator transconductance	Startup	2.8	-	-		
G <sub>mcritmax</sub>	Maximum critical crystal G <sub>m</sub>	Startup	-	-	0.56	µA/V	
$t_{SU(LSE)}^{(2)}$	startup time	$V_{\text{DD}}$ is stabilized	-	2	-	S	

Table 33. LSE oscillator characteristics (f<sub>LSE</sub> = 32.768 kHz) <sup>(1)</sup>

1. Guaranteed by design.

 Guaranteed by characterization. t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

*Note:* For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



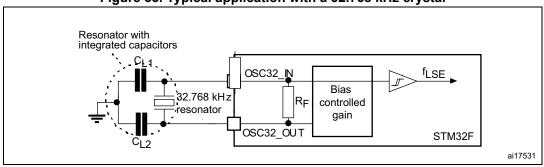


Figure 33. Typical application with a 32.768 kHz crystal

#### 5.3.9 Internal clock source characteristics

The parameters given in *Table 34* and *Table 35* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.

#### High-speed internal (HSI) RC oscillator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
f <sub>HSI</sub>	Frequency	-	-	16	-	MHz			
	_	-	-	-	1	%			
		$T_A = -40$ to 105 °C <sup>(3)</sup>	-8	-	4.5	%			
ACC <sub>HSI</sub>		$T_A = -10 \text{ to } 85 \ ^{\circ}\text{C}^{(3)}$	-4	-	4	%			
		$T_{A} = 25 \ ^{\circ}C^{(4)}$	-1	-	1	%			
t <sub>su(HSI)</sub> <sup>(2)</sup>	HSI oscillator startup time	-	-	2.2	4	μs			
I <sub>DD(HSI)</sub> <sup>(2)</sup>	HSI oscillator power consumption	-	-	60	80	μA			

Table 34. HSI oscillator characteristics <sup>(1)</sup>

1.  $V_{DD}$  = 3.3 V, PLL OFF, T<sub>A</sub> = -40 to 125 °C unless otherwise specified.

2. Guaranteed by design.

3. Guaranteed by characterization.

4. Factory calibrated, parts not soldered.

#### Low-speed internal (LSI) RC oscillator

Table 35.	LSI oscillator	characteristics	(1)
-----------	----------------	-----------------	-----

Symbol	Parameter	Min	Тур	Мах	Unit
f <sub>LSI</sub> <sup>(2)</sup>	Frequency	17	32	47	kHz
t <sub>su(LSI)</sub> <sup>(3)</sup>	LSI oscillator startup time	-	15	40	μs
I <sub>DD(LSI)</sub> <sup>(3)</sup>			0.4	0.6	μA

1.  $V_{DD}$  = 3 V,  $T_A$  = -40 to 105 °C unless otherwise specified.

2. Guaranteed by characterization.

3. Guaranteed by design.



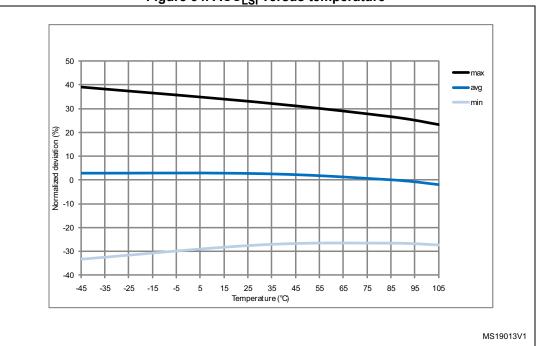


Figure 34. ACC<sub>LSI</sub> versus temperature

# 5.3.10 PLL characteristics

The parameters given in *Table 36* and *Table 37* are derived from tests performed under temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PLL_IN</sub>	PLL input clock <sup>(1)</sup>	-	0.95 <sup>(2)</sup>	1	2.10	MHz
f <sub>PLL_OUT</sub>	PLL multiplier output clock	-	24	-	168	MHz
f <sub>PLL48_OUT</sub>	48 MHz PLL multiplier output clock	-	-	48	75	MHz
f <sub>VCO_OUT</sub>	PLL VCO output	-	100	-	432	MHz
t	PLL lock time	VCO freq = 100 MHz	75	-	200	
t <sub>LOCK</sub>		VCO freq = 432 MHz	100	-	300	μs

Table 36. Main PLL characteristics



Symbol	Parameter	Conditions	•	Min	Тур	Max	Unit
			RMS	-	25	-	
	Cycle-to-cycle jitter	System clock F 120 MHz F t	peak to peak	-	±150	-	
			RMS	-	15	-	
Jitter <sup>(3)</sup>	Period Jitter		peak to peak	-	±200	-	ps
	Main clock output (MCO) for RMII Ethernet	Cycle to cycle at 5 on 1000 samples	-	32	-		
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at 25 MHz on 1000 samples		-	40	-	
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples		-	330	-	
I <sub>DD(PLL)</sub> <sup>(4)</sup>	PLL power consumption on VDD	VCO freq = 100 MHz		0.15	_	0.40	mA
·DD(PLL)		VCO freq = 432 MHz		0.45		0.75	
I <sub>DDA(PLL)</sub> <sup>(4)</sup>	PLL power consumption on VDDA		VCO freq = 100 MHz VCO freq = 432 MHz		-	0.40 0.85	mA

#### Table 36. Main PLL characteristics (continued)

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.

2. Guaranteed by design.

3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.

4. Guaranteed by characterization.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f <sub>PLLI2S_IN</sub>	PLLI2S input clock <sup>(1)</sup>	-		0.95 <sup>(2)</sup>	1	2.10	MHz
f <sub>PLLI2S_OUT</sub>	PLLI2S multiplier output clock	-		-	-	216	MHz
f <sub>VCO_OUT</sub>	PLLI2S VCO output	-		100	-	432	MHz
t <sub>LOCK</sub>	PLLI2S lock time	VCO freq = 100 MHz	Z	75	-	200	
LOCK		VCO freq = 432 MHz		100	-	300	300 µs
		Cycle to cycle at	RMS	-	90	-	
	Master I <sup>2</sup> S clock jitter	12.288 MHz on 48KHz period, N=432, R=5	peak to peak	-	±280	-	ps
Jitter <sup>(3)</sup>	Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples	of	-	90	-	ps	
	WS I <sup>2</sup> S clock jitter	Cycle to cycle at 48 on 1000 samples	Cycle to cycle at 48 KHz on 1000 samples		400	-	ps

#### Table 37. PLLI2S (audio PLL) characteristics



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
I <sub>DD(PLLI2S)</sub> <sup>(4)</sup>	PLLI2S power consumption on $V_{DD}$	VCO freq = 100 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA	
I <sub>DDA(PLLI2S)</sub> (4)	PLLI2S power consumption on V <sub>DDA</sub>	VCO freq = 100 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA	

#### Table 37. PLLI2S (audio PLL) characteristics (continued)

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.

2. Guaranteed by design.

3. Value given with main PLL running.

4. Guaranteed by characterization.

#### 5.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 44: EMI characteristics*). It is available only on the main PLL.

Symbol	Parameter	Min	Тур	Max <sup>(1)</sup>	Unit
f <sub>Mod</sub>	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP		-	-	2 <sup>15</sup> –1	-

#### Table 38. SSCG parameters constraint

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

 $MODEPER = round[f_{PLL IN}/(4 \times f_{Mod})]$ 

 $f_{\text{PLL}\ \text{IN}}$  and  $f_{\text{Mod}}$  must be expressed in Hz.

As an example:

If  $f_{PLL_IN} = 1$  MHz, and  $f_{MOD} = 1$  kHz, the modulation depth (MODEPER) is given by equation 1:

 $MODEPER = round[10^{6}/(4 \times 10^{3})] = 250$ 

#### Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

INCSTEP = round[( $(2^{15}-1) \times md \times PLLN$ )/(100×5×MODEPER)]

f<sub>VCO OUT</sub> must be expressed in MHz.

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With a modulation depth (md) =  $\pm 2$  % (4 % peak to peak), and PLLN = 240 (in MHz):

INCSTEP = round[ $((2^{15}-1) \times 2 \times 240)/(100 \times 5 \times 250)$ ] = 126md(quantitazed)%

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{quantized}$$
% = (MODEPER×INCSTEP×100×5)/((2<sup>15</sup>-1)×PLLN)

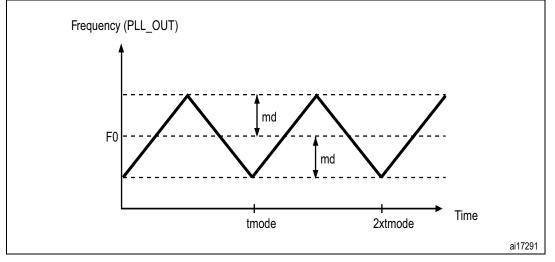
As a result:

$$md_{quantized}$$
% =  $(250 \times 126 \times 100 \times 5)/((2^{15} - 1) \times 240)$  = 2.002%(peak)

*Figure 35* and *Figure 36* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is  $f_{PLL_OUT}$  nominal. T<sub>mode</sub> is the modulation period. md is the modulation depth.







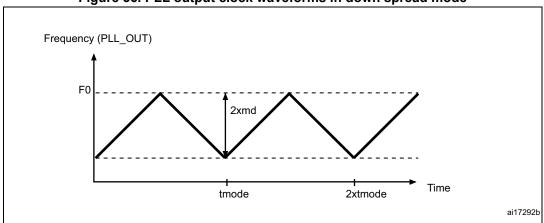


Figure 36. PLL output clock waveforms in down spread mode

#### 5.3.12 Memory characteristics

#### Flash memory

The characteristics are given at  $T_A = -40$  to 105 °C unless otherwise specified. The devices are shipped to customers with the Flash memory erased.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
	Write / Erase 8-bit mode, $V_{DD}$ = 1.8 V	-	5	-		
I <sub>DD</sub>	Supply current	Write / Erase 16-bit mode, $V_{DD}$ = 2.1 V	-	8	-	mA
		Write / Erase 32-bit mode, $V_{DD}$ = 3.3 V	-	12	-	

Table 39. Flash memory characteristics

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
t <sub>prog</sub>	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100 <sup>(2)</sup>	μs
t <sub>ERASE16KB</sub> Sector (16 KB) erase tir		Program/erase parallelism (PSIZE) = x 8	-	400	800	
	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 16	-	300	600	ms
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
		Program/erase parallelism (PSIZE) = x 8	-	1200	2400	
t <sub>ERASE64KB</sub>	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 16	-	700	1400	ms
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	

Table 40. Flash memory programming



Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
t <sub>erase128kb</sub>		Program/erase parallelism (PSIZE) = x 8	-	2	4	
	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	s
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
	Program/erase parallelism (PSIZE) = x 8	-	16	32		
t <sub>ME</sub>	Mass erase time	Program/erase parallelism (PSIZE) = x 16	-	11	22	s
		Program/erase parallelism (PSIZE) = x 32	-	8	16	
		32-bit program operation	2.7	-	3.6	V
V <sub>prog</sub>	Programming voltage	16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.8	-	3.6	V

Table 40. Flash memory programming (continued)	Table 40.	Flash memor	v programming	(continued)
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1. Guaranteed by characterization.

2. The maximum programming time is measured after 100K erase operations.



Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
t <sub>prog</sub>	Double word programming		-	16	100 <sup>(2)</sup>	μs
t <sub>ERASE16KB</sub>	Sector (16 KB) erase time	T <sub>A</sub> = 0 to +40 °C V <sub>DD</sub> = 3.3 V V <sub>PP</sub> = 8.5 V	-	230	-	
t <sub>ERASE64KB</sub>	Sector (64 KB) erase time		-	490	-	ms
t <sub>ERASE128KB</sub>	Sector (128 KB) erase time		-	875	-	
t <sub>ME</sub>	Mass erase time		-	6.9	-	s
V <sub>prog</sub>	Programming voltage	-	2.7	-	3.6	V
V <sub>PP</sub>	V <sub>PP</sub> voltage range	-	7	-	9	V
I <sub>PP</sub>	Minimum current sunk on the $V_{\rm PP}$ pin	-	10	-	-	mA
t <sub>VPP</sub> <sup>(3)</sup>	Cumulative time during which V <sub>PP</sub> is applied	-	-	-	1	hour

Table 41. Flash memor	y programming with V <sub>PI</sub>
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1. Guaranteed by design.

2. The maximum programming time is measured after 100K erase operations.

3.  $V_{PP}$  should only be connected during programming/erasing.

Symbol	Parameter	Conditions	Value Min <sup>(1)</sup>	Unit
N <sub>END</sub>	Endurance	$T_A = -40$ to +85 °C (6 suffix versions) $T_A = -40$ to +105 °C (7 suffix versions)	10	kcycles
		1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 85 °C	30	
t <sub>RET</sub> Data re	Data retention	1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 105 °C	10	Years
		10 kcycles <sup>(2)</sup> at T <sub>A</sub> = 55 °C	20	

#### Table 42. Flash memory endurance and data retention

1. Guaranteed by characterization.

2. Cycling performed over the whole temperature range.

## 5.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

#### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A burst of fast transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.



A device reset allows normal operations to be resumed.

The test results are given in *Table 43*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	ol Parameter Conditions		Level/ Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD}$ = 3.3 V, LQFP176, T <sub>A</sub> = +25 °C, f <sub>HCLK</sub> = 168 MHz, conforms to IEC 61000-4-2	2B
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100 pF on $V_{DD}$ and $V_{SS}$ pins to induce a functional disturbance	V <sub>DD</sub> = 3.3 V, LQFP176, T <sub>A</sub> = +25 °C, f <sub>HCLK</sub> = 168 MHz, conforms to IEC 61000-4-2	4A

Table	43.	EMS	chara	cteristics
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#### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

#### Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).



## **Electromagnetic Interference (EMI)**

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC<sup>?</sup> code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f <sub>HSE</sub> /f <sub>CPU</sub> ]	Unit
				25/168 MHz	
		$V_{1} = 2.2 V_{1} = 25 \circ 0.1 \text{ OED} 176$	0.1 to 30 MHz	32	
	Peak level V <sub>D</sub>	$V_{DD} = 3.3 \text{ V}, T_A = 25 \text{ °C}, LQFP176$ package, conforming to SAE J1752/3	30 to 130 MHz	25	dBµV
			130 MHz to 1GHz	29	
c			SAE EMI Level	4	-
S <sub>EMI</sub>			0.1 to 30 MHz	19	
			30 to 130 MHz	16	dBµV
		EEMBC, code running from Flash with ART accelerator and PLL spread	130 MHz to 1GHz	18	
		spectrum enabled	SAE EMI level	3.5	-

# 5.3.14 Absolute maximum ratings (electrical sensitivity)

Stresses above the absolute maximum ratings listed in *Table 11: Voltage characteristics*, *Table 12: Current characteristics*, and *Table 13: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and the functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard, extended mission profiles are available on demand.

#### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts  $\times$  (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Symbol	Ratings Conditions		Class	Maximum value <sup>(1)</sup>	Unit
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	$T_A = +25 \text{ °C conforming to JESD22-A114}$	2	2000 <sup>(2)</sup>	V
V <sub>ESD(CDM)</sub>	Electrostatic discharge voltage (charge device model)	T <sub>A</sub> = +25 °C conforming to ANSI/ESD STM5.3.1	Ш	500	v

Table 45	. ESD	absolute	maximum	ratings
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2. On V<sub>BAT</sub> pin, V<sub>ESD(HBM)</sub> is limited to 1000 V.

## **Static latchup**

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

	Symbol	Parameter	Conditions	Class
ĺ	LU	Static latch-up class	$T_A = +105 \text{ °C conforming to JESD78A}$	II level A

#### Table 46. Electrical sensitivities

# 5.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below  $V_{SS}$  or above  $V_{DD}$  (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

## Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of 5  $\mu$ A/+0  $\mu$ A range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in Table 47.



		Functional s		
Symbol	Description	Negative injection	Positive injection	Unit
I <sub>INJ</sub> (1)	Injected current on BOOT0 pin	- 0	NA	
	Injected current on NRST pin	- 0	NA	
	Injected current on PE2, PE3, PE4, PE5, PE6, PI8, PC13, PC14, PC15, PI9, PI10, PI11, PF0, PF1, PF2, PF3, PF4, PF5, PF10, PH0/OSC_IN, PH1/OSC_OUT, PC0, PC1, PC2, PC3, PB6, PB7, PB8, PB9, PE0, PE1, PI4, PI5, PI6, PI7, PDR_ON, BYPASS_REG	- 0	NA	mA
	Injected current on all FT pins	- 5	NA	
	Injected current on any other pin	- 5	+5	1

#### Table 47. I/O current injection susceptibility

1. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

# 5.3.16 I/O port characteristics

## General input/output characteristics

Unless otherwise specified, the parameters given in *Table 48* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Note: For information on GPIO configuration, refer to application note AN4899 "STM32 GPIO configuration for hardware settings and low-power consumption" available from the ST website www.st.com.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
	FT, TTa and NRST I/O input low	1.7 V≤V <sub>DD</sub> ≤3.6 V	-	-	0.3V <sub>DD</sub> -0.04 <sup>(1)</sup>	
	level voltage	$1.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.0 \text{ V}$	-	-	0.3V <sub>DD</sub> <sup>(2)</sup>	
V <sub>IL</sub>	BOOT0 I/O input low level voltage	$1.75 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ -40 °C≤ T <sub>A</sub> ≤ 105 °C	-	-	0.1V <sub>DD</sub> -+0.1 <sup>(1)</sup>	
		$1.7 V \le V_{DD} \le 3.6 V$ 0 °C≤ T <sub>A</sub> ≤ 105 °C	-	-	0.1V <sub>DD</sub> -+0.1V	v
	FT, TTa and NRST I/O input low level voltage BOOT0 I/O input low level	$1.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	0.45V <sub>DD</sub> +0.3 <sup>(1)</sup>	-	-	V
			0.7V <sub>DD</sub> <sup>(2)</sup>	-	-	
V <sub>IH</sub>		$1.75 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$ -40 °C≤ T <sub>A</sub> ≤ 105 °C	$0.171( \pm 0.7^{(1)})$	-	-	
	voltage	$1.7 V \le V_{DD} \le 3.6 V$ $0 C \le T_A \le 105 C$	- 0.17V <sub>DD</sub> +0.7 <sup>(1)</sup>	-	-	

114/203



Symbol	Paran	neter	Conditions	Min	Тур	Max	Unit
	FT, TTa and NRST I/O input hysteresis		$1.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	10%V <sub>DD</sub> <sup>(3)</sup>	-	-	
V <sub>HYS</sub>	BOOT0 I/O input	hystoresis	$1.75 V \le V_{DD} \le 3.6 V$ -40 °C≤ T <sub>A</sub> ≤ 105 °C	0.1			V
		Inysteresis	$\begin{array}{c} 1.7 \ V \leq V_{DD} \leq 3.6 \ V \\ 0 \ ^{\circ}C \leq T_{A} \leq 105 \ ^{\circ}C \end{array}$	0.1	-	-	
	I/O input leakage	e current <sup>(4)</sup>	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	
l <sub>lkg</sub>	I/O FT input leak	age current <sup>(5)</sup>	V <sub>IN</sub> = 5 V	-	-	3	μA
R <sub>PU</sub> e	equivalent resistor <sup>(6)</sup> PA10 and PB12 (OTG_FS_ID	except for PA10 and	$V_{IN} = V_{SS}$	30	40	50	
			-	7	10	14	kΩ
R <sub>PD</sub>		except for PA10 and	$V_{IN} = V_{DD}$	30	40	50	
			-	7	10	14	
C <sub>IO</sub> <sup>(8)</sup>	I/O pin capacitance			-	5	-	pF

 Table 48. I/O static characteristics (continued)

1. Guaranteed by design.

2. Tested in production.

3. With a minimum of 200 mV.

- 4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins.Refer to Table 47: I/O current injection susceptibility
- To sustain a voltage higher than V<sub>DD</sub> + 0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to Table 47: I/O current injection susceptibility.
- Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
- 7. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
- 8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters.



#### **Output driving current**

The GPIOs (general purpose input/outputs) can sink or source up to  $\pm 8$  mA, and sink or source up to  $\pm 20$  mA (with a relaxed V<sub>OL</sub>/V<sub>OH</sub>) except PC13, PC14 and PC15 which can sink or source up to  $\pm 3$ mA. When using the PC13 to PC15 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 5.2*. In particular:

- The sum of the currents sourced by all the I/Os on V<sub>DD</sub>, plus the maximum Run consumption of the MCU sourced on V<sub>DD</sub>, cannot exceed the absolute maximum rating I<sub>VDD</sub> (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V<sub>SS</sub> plus the maximum Run consumption of the MCU sunk on V<sub>SS</sub> cannot exceed the absolute maximum rating I<sub>VSS</sub> (see *Table 12*).

## Output voltage levels

Unless otherwise specified, the parameters given in *Table 49* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>OL</sub> <sup>(2)</sup>	Output low level voltage	CMOS port	-	0.4	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage	I <sub>IO</sub> = +8 mA 2.7 V < V <sub>DD</sub> < 3.6 V	V <sub>DD</sub> -0.4	-	V
V <sub>OL</sub> <sup>(2)</sup>	Output low level voltage	TTL port	-	0.4	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage	I <sub>IO</sub> =+ 8mA 2.7 V < V <sub>DD</sub> < 3.6 V	2.4	-	V
V <sub>OL</sub> <sup>(2)(4)</sup>	Output low level voltage	I <sub>IO</sub> = +20 mA	-	1.3	v
V <sub>OH</sub> <sup>(3)(4)</sup>	Output high level voltage	2.7 V < V <sub>DD</sub> < 3.6 V	V <sub>DD</sub> -1.3	-	v
V <sub>OL</sub> <sup>(2)(4)</sup>		I <sub>IO</sub> = +6 mA	-	0.4	v
V <sub>OH</sub> <sup>(3)(4)</sup>	Output high level voltage	2 V < V <sub>DD</sub> < 2.7 V	V <sub>DD</sub> -0.4	-	v

Table 49. Output voltage characteristics<sup>(1)</sup>

1. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited: the speed should not exceed 2 MHz with a maximum load of 30 pF and these I/Os must not be used as a current source (e.g. to drive an LED).

2. The I<sub>IO</sub> current sunk by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I<sub>IO</sub> (I/O ports and control pins) must not exceed I<sub>VSS</sub>.

3. The I<sub>IO</sub> current sourced by the device must always respect the absolute maximum rating specified in Table 12 and the sum of I<sub>IO</sub> (I/O ports and control pins) must not exceed I<sub>VDD</sub>.



## Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 37* and *Table 50*, respectively.

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.

OSPEEDRy [1:0] bit value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
			C <sub>L</sub> = 50 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	4		
	f	Maximum frequency <sup>(3)</sup>	C <sub>L</sub> = 50 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	2	MHz	
	'max(IO)out		C <sub>L</sub> = 10 pF, V <sub>DD</sub> > 2.70 V	-	-	8		
00			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	4		
	t <sub>f(IO)out</sub> / t <sub>r(IO)out</sub>	Output high to low level fall time and output low to high level rise time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.8 V to 3.6 V	-	-	100	ns	
			C <sub>L</sub> = 50 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	25		
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>	C <sub>L</sub> = 50 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	12.5	MHz	
			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	50 <sup>(4)</sup>		
01			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	20		
01	t <sub>f(IO)out</sub> / t <sub>r(IO)out</sub>	Output high to low level fall time and output low to high level rise time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> >2.7 V	-	-	10	- ns	
			C <sub>L</sub> = 50 pF, V <sub>DD</sub> > 1.8 V	-	-	20		
			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	6		
			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	10		
			C <sub>L</sub> = 40 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	50 <sup>(4)</sup>		
	£	Maximum frequency <sup>(3)</sup>	C <sub>L</sub> = 40 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	25	MHz	
	f <sub>max(IO)out</sub>		C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	100 <sup>(4)</sup>		
10			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	50 <sup>(4)</sup>		
10			C <sub>L</sub> = 40 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	6		
	t <sub>f(IO)out</sub> /	Output high to low level fall	C <sub>L</sub> = 40 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	10	- ns	
	t <sub>r(IO)out</sub>	time and output low to high level rise time	C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	4		
			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	6		

Table 50. I/O AC characteristics<sup>(1)(2)</sup>



OSPEEDRy [1:0] bit value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		Maximum frequency <sup>(3)</sup>	C <sub>L</sub> = 30 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	100 <sup>(4)</sup>	
	<b>E</b>		C <sub>L</sub> = 30 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	50 <sup>(4)</sup>	MHz
	rmax(IO)out		C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	180 <sup>(4)</sup>	
			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	100 <sup>(4)</sup>	1
11	t <sub>f(IO)out</sub> /	Output high to low level fall time and output low to high level rise time	C <sub>L</sub> = 30 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	4	ns
			C <sub>L</sub> = 30 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	6	
	t <sub>r(IO)out</sub>		C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 2.70 V	-	-	2.5	
			C <sub>L</sub> = 10 pF, V <sub>DD &gt;</sub> 1.8 V	-	-	4	
-	t <sub>EXTIpw</sub>	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

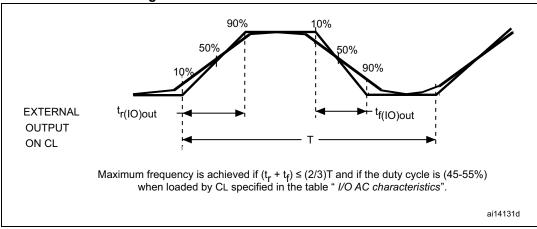
Table 50. I/O AC characteristics<sup>(1)(2)</sup> (continued)

1. Guaranteed by characterization.

 The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx\_SPEEDR GPIO port output speed register.

3. The maximum frequency is defined in *Figure* 37.

4. For maximum frequencies above 50 MHz, the compensation cell should be used.



#### Figure 37. I/O AC characteristics definition

# 5.3.17 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor,  $R_{PU}$  (see *Table 48*).

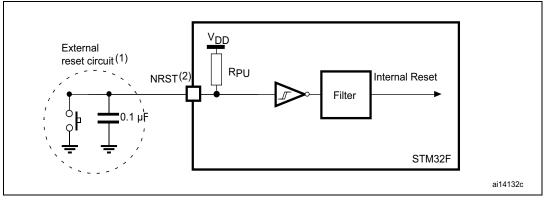
Unless otherwise specified, the parameters given in *Table 51* are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST Input low level voltage	TTL ports	-	-	0.8	
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST Input high level voltage	2.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	2	-	-	v
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST Input low level voltage	CMOS ports	-	-	0.3V <sub>DD</sub>	v
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST Input high level voltage	1.8 V ≤ V <sub>DD</sub> ≤ 3.6 V	$0.7V_{DD}$	-	-	
V <sub>hys(NRST)</sub>	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(2)</sup>	$V_{IN} = V_{SS}$	30	40	50	kΩ
V <sub>F(NRST)</sub> <sup>(1)</sup>	NRST Input filtered pulse		-	-	100	ns
V <sub>NF(NRST)</sub> <sup>(1)</sup>	NRST Input not filtered pulse	V <sub>DD</sub> > 2.7 V	300	-	-	ns
T <sub>NRST_OUT</sub>	Generated reset pulse duration	Internal Reset source	20	-	-	μs

Table 51. NRST pin characteristics

1. Guaranteed by design.

2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).



#### Figure 38. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets.
- The user must ensure that the level on the NRST pin can go below the V<sub>IL(NRST)</sub> max level specified in Table 51. Otherwise the reset is not taken into account by the device.



# 5.3.18 TIM timer characteristics

The parameters given in Table 52 and Table 53 are guaranteed by design.

Refer to *Section 5.3.16: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Max	Unit
t <sub>res(TIM)</sub>		AHB/APB1	1	-	t <sub>TIMxCLK</sub>
	Timer resolution time	prescaler distinct from 1, f <sub>TIMxCLK</sub> = 84 MHz	11.9	-	ns
, , , , , , , , , , , , , , , , , , ,		AHB/APB1	1	-	t <sub>TIMxCLK</sub>
		prescaler = 1, f <sub>TIMxCLK</sub> = 42 MHz	23.8	-	ns
f	Timer external clock		0	f <sub>TIMxCLK</sub> /2	MHz
f <sub>EXT</sub>	frequency on CH1 to CH4		0	42	MHz
Res <sub>TIM</sub>	Timer resolution		-	16/32	bit
	16-bit counter clock		1	65536	t <sub>TIMxCLK</sub>
t	period when internal clock is selected	f <sub>TIMxCLK</sub> = 84 MHz APB1= 42 MHz	0.0119	780	μs
<sup>t</sup> COUNTER	32-bit counter clock		1	-	t <sub>TIMxCLK</sub>
	period when internal clock is selected		0.0119	51130563	μs
t <sub>MAX_COUNT</sub>	Maximum possible count		-	65536 × 65536	t <sub>TIMxCLK</sub>
	Maximum possible count		-	51.1	s

 Table 52. Characteristics of TIMx connected to the APB1 domain<sup>(1)</sup>

1. TIMx is used as a general term to refer to the TIM2, TIM3, TIM4, TIM5, TIM6, TIM7, and TIM12 timers.



Symbol	Parameter	Conditions	Min	Мах	Unit
Gymbol	i di difietei	Conditions	WIIII	Max	Onit
		AHB/APB2	1	-	t <sub>TIMxCLK</sub>
t <sub>res(TIM)</sub>	Timer resolution time	prescaler distinct from 1, f <sub>TIMxCLK</sub> = 168 MHz	5.95	-	ns
		AHB/APB2	1	-	t <sub>TIMxCLK</sub>
		prescaler = 1, f <sub>TIMxCLK</sub> = 84 MHz	11.9	-	ns
	Timer external clock		0	f <sub>TIMxCLK</sub> /2	MHz
f <sub>EXT</sub>	frequency on CH1 to CH4		0	84	MHz
Res <sub>TIM</sub>	Timer resolution	f <sub>TIMxCLK</sub> = 168 MHz	-	16	bit
t <sub>COUNTER</sub>	16-bit counter clock period when internal clock is selected	APB2 = 84 MHz	1	65536	t <sub>TIMxCLK</sub>
t <sub>MAX_COUNT</sub>	Maximum possible count		-	32768	t <sub>TIMxCLK</sub>

 Table 53. Characteristics of TIMx connected to the APB2 domain<sup>(1)</sup>

1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

# 5.3.19 Communications interfaces

# I<sup>2</sup>C interface characteristics

The  $I^2C$  interface meets the timings requirements of the  $I^2C$ -bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s.

The I<sup>2</sup>C timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0090 reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and  $V_{DD}$  is disabled, but is still present. Refer to Section 5.3.16: I/O port characteristics for more details on the I<sup>2</sup>C I/O characteristics.

All I<sup>2</sup>C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Symbol	Parameter	Min	Мах	Unit
t <sub>AF</sub>	Maximum pulse width of spikes that are suppressed by the analog filter	50 <sup>(2)</sup>	260 <sup>(3)</sup>	ns

Table 54. I2C analog filter characteristics<sup>(1)</sup>

1. Guaranteed by design.

2. Spikes with widths below t<sub>AF(min)</sub> are filtered.

3. Spikes with widths above  $t_{AF(max)}$  are not filtered



## SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 55* for SPI are derived from tests performed under the ambient temperature,  $f_{PCLKx}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 14* with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 V<sub>DD</sub>

Refer to Section 5.3.16: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
fscк		Master mode, SPI1, 2.7V < V <sub>DD</sub> < 3.6V			42	MHz
	- SPI clock frequency	Slave mode, SPI1, 2.7V < V <sub>DD</sub> < 3.6V	-	-	42	
1/t <sub>c(SCK)</sub>		Master mode, SPI1/2/3, 1.7V < V <sub>DD</sub> < 3.6V		-	21	IVILITZ
		Slave mode, SPI1/2/3, 1.7V < V <sub>DD</sub> < 3.6V	-		21	
Duty(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>w(SCKH)</sub>	SCK high and low time	Master mode, SPI presc = 2, 2.7V < V <sub>DD</sub> < 3.6V	T <sub>PCLK</sub> -0.5	T <sub>PCLK</sub>	T <sub>PCLK</sub> +0.5	
t <sub>w(SCKL)</sub>	SCK high and low time	Master mode, SPI presc = 2, 1.7V < V <sub>DD</sub> < 3.6V	T <sub>PCLK</sub> -2	T <sub>PCLK</sub>	T <sub>PCLK</sub> +2	
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI presc = 2	4 x T <sub>PCLK</sub>			
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI presc = 2	2 x T <sub>PCLK</sub>	-	-	
t <sub>su(MI)</sub>	Data input setup time	Master mode	6.5	-	-	
t <sub>su(SI)</sub>	Data input setup time	Slave mode	2.5	-	-	
t <sub>h(MI)</sub>	Data input hold time	Master mode	2.5	-	-	
t <sub>h(SI)</sub>	Data input hold time	Slave mode	4	-	-	
$t_{a(SO)}^{(2)}$	Data output access time	Slave mode, SPI presc = 2	0	-	4 x T <sub>PCLK</sub>	
	Data output disable time	Slave mode, SPI1, 2.7V < V <sub>DD</sub> < 3.6V	0	-	7.5	
t <sub>dis(SO)</sub> <sup>(3)</sup>	Data output disable time	Slave mode, SPI1/2/3 1.7V < V <sub>DD</sub> < 3.6V	0	-	16.5	ns
		Slave mode (after enable edge), SPI1, 2.7V < V <sub>DD</sub> < 3.6V	-	11	13	
t <sub>v(SO)</sub>	Data output valid/hold time	Slave mode (after enable edge), SPI2/3, 2.7V < $V_{DD}$ < 3.6V	-	12	16.5	
t <sub>h(SO)</sub>	Data output valid/hold time	Slave mode (after enable edge), SPI1, 1.7V < V <sub>DD</sub> < 3.6V	-	15.5	19	
		Slave mode (after enable edge), SPI2/3, $1.7V < V_{DD} < 3.6V$	-	18	20.5	
		Master mode (after enable edge), SPI1, 2.7V < V <sub>DD</sub> < 3.6V	-	-	2.5	
t <sub>v(MO)</sub>	Data output valid time	Master mode (after enable edge), SPI1/2/3, 1.7V < V <sub>DD</sub> < 3.6V	-	-	4.5	
t <sub>h(MO)</sub>	Data output hold time	Master mode (after enable edge)	0	-	-	

Table 55. SP	dynamic	characteristics <sup>(1)</sup>	(continued)
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1. Guaranteed by characterization.

2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.

3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.



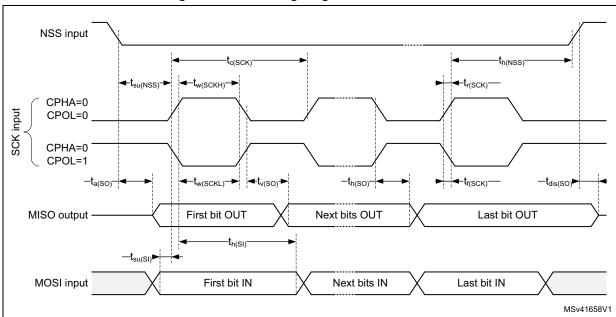
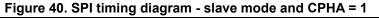
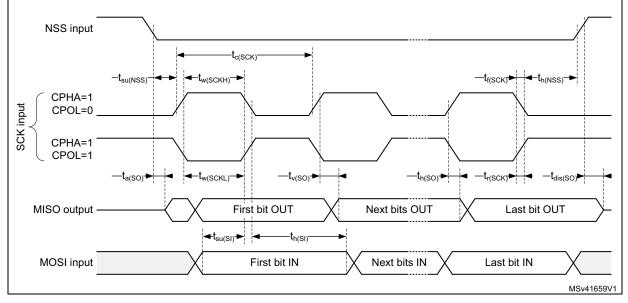
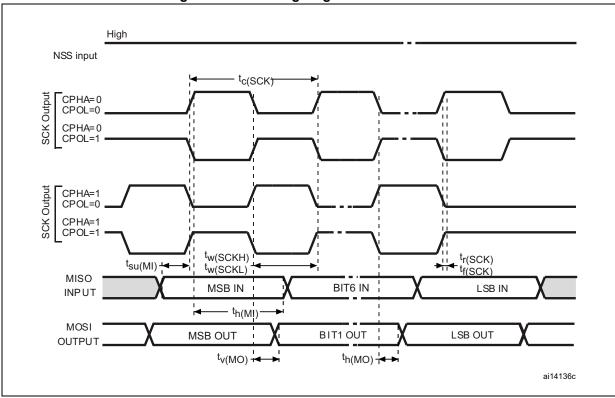


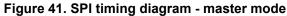
Figure 39. SPI timing diagram - slave mode and CPHA = 0













# I<sup>2</sup>S interface characteristics

Unless otherwise specified, the parameters given in *Table 56* for the i<sup>2</sup>S interface are derived from tests performed under the ambient temperature,  $f_{PCLKx}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 14*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 V<sub>DD</sub>

Refer to Section 5.3.16: I/O port characteristics for more details on the input/output alternate function characteristics (CK, SD, WS).

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>MCK</sub>	I <sup>2</sup> S main clock output	-	256 x 8K	256 x F <sub>S</sub> <sup>(2)</sup>	MHz
f.	I <sup>2</sup> S clock frequency	Master data: 32 bits	-	64 x F <sub>S</sub>	MHz
f <sub>CK</sub>		Slave data: 32 bits	-	64 x F <sub>S</sub>	
D <sub>CK</sub>	I <sup>2</sup> S clock frequency duty cycle	Slave receiver	30	70	%
t <sub>v(WS)</sub>	WS valid time	Master mode	0	6	
t <sub>h(WS)</sub>	WS hold time	Master mode	0	-	
t <sub>su(WS)</sub>	WS setup time	Slave mode	1	-	
t <sub>h(WS)</sub>	WS hold time	Slave mode	0	-	
t <sub>su(SD_MR)</sub>	Dete innut exturn time	Master receiver	7.5	-	
t <sub>su(SD_SR)</sub>	Data input setup time	Slave receiver	2	-	ns
t <sub>h(SD_MR)</sub>	Data input hold time	Master receiver	0	-	110
t <sub>h(SD_SR)</sub>	Data input hold time	Slave receiver	0	-	
t <sub>v(SD_ST)</sub> t <sub>h(SD_ST)</sub>	Data output valid time	Slave transmitter (after enable edge)	-	27	
t <sub>v(SD_MT)</sub>		Master transmitter (after enable edge)	-	20	
t <sub>h(SD_MT)</sub>	Data output hold time	Master transmitter (after enable edge)	2.5	-	

1. Guaranteed by characterization.

2. The maximum value of 256 x F<sub>S</sub> is 42 MHz (APB1 maximum frequency).

Note: Refer to the  $l^2S$  section of RM0090 reference manual for more details on the sampling frequency ( $F_S$ ).  $f_{MCK}$ ,  $f_{CK}$ , and  $D_{CK}$  values reflect only the digital peripheral behavior. The value of these parameters might be slightly impacted by the source clock accuracy.  $D_{CK}$ depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of I2SDIV / (2 x I2SDIV + ODD) and a maximum value of (I2SDIV + ODD) / (2 x I2SDIV + ODD).  $F_S$  maximum value is supported for each mode/condition.



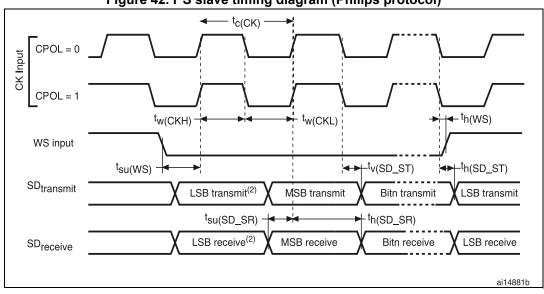
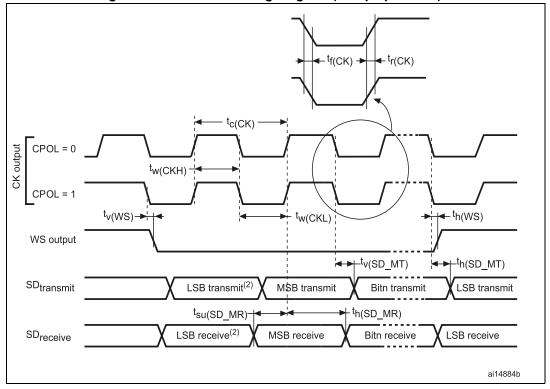


Figure 42. I<sup>2</sup>S slave timing diagram (Philips protocol)

LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.



## Figure 43. I<sup>2</sup>S master timing diagram (Philips protocol)<sup>(1)</sup>

- 1. Guaranteed by characterization.
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.



## **USB OTG FS characteristics**

This interface is present in both the USB OTG HS and USB OTG FS controllers.

Symbol	Parameter	Мах	Unit
t <sub>STARTUP</sub> <sup>(1)</sup>	USB OTG FS transceiver startup time	1	μs

Table 57. USB OTG FS startup time

1. Guaranteed by design.

Sym	bol	Parameter	Conditions	Min. <sup>(1)</sup>	Тур.	Max. <sup>(1)</sup>	Unit
	$V_{DD}$	USB OTG FS operating voltage	-	3.0 <sup>(2)</sup>	-	3.6	V
Input	V <sub>DI</sub> <sup>(3)</sup>	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	
levels	V <sub>CM</sub> <sup>(3)</sup>	Differential common mode range	Includes V <sub>DI</sub> range	0.8	-	2.5	V
	$V_{SE}^{(3)}$	Single ended receiver threshold	-	1.3	-	2.0	
Output	$V_{OL}$	Static output level low	$\rm R_L$ of 1.5 k\Omega to 3.6 $\rm V^{(4)}$	-	-	0.3	V
levels	V <sub>OH</sub>	Static output level high	${\sf R}_{\sf L}$ of 15 k $\Omega$ to ${\sf V}_{\sf SS}{}^{(4)}$	2.8	-	3.6	v
P		PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	V <sub>IN</sub> = V <sub>DD</sub>	17	21	24	
R <sub>PD</sub> R <sub>PU</sub>		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	VIN - VDD	0.65	1.1	2.0	kΩ
		PA12, PB15 (USB_FS_DP, USB_HS_DP)	V <sub>IN</sub> = V <sub>SS</sub>	1.5	1.8	2.1	
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	V <sub>IN</sub> = V <sub>SS</sub>	0.25	0.37	0.55	

#### Table 58. USB OTG FS DC electrical characteristics

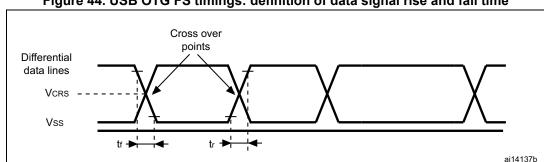
1. All the voltages are measured from the local ground potential.

2. The STM32F405xx and STM32F407xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V  $V_{DD}$  voltage range.

3. Guaranteed by design.

4.  $\ensuremath{\mathsf{R}_{\mathsf{L}}}$  is the load connected on the USB OTG FS drivers





#### Figure 44. USB OTG FS timings: definition of data signal rise and fall time

## Table 59. USB OTG FS electrical characteristics<sup>(1)</sup>

Driver characteristics							
Symbol Parameter		Conditions		Max	Unit		
t <sub>r</sub>	Rise time <sup>(2)</sup>	C <sub>L</sub> = 50 pF	4	20	ns		
t <sub>f</sub>	Fall time <sup>(2)</sup>	C <sub>L</sub> = 50 pF	4	20	ns		
t <sub>rfm</sub>	Rise/ fall time matching	t <sub>r</sub> /t <sub>f</sub>	90	110	%		
V <sub>CRS</sub>	Output signal crossover voltage	_	1.3	2.0	V		

1. Guaranteed by design.

Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0). 2.

#### **USB HS characteristics**

Unless otherwise specified, the parameters given in Table 62 for ULPI are derived from tests performed under the ambient temperature, fHCLK frequency summarized in Table 61 and  $V_{DD}$  supply voltage conditions summarized in *Table 60*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>.

Refer to Section Section 5.3.16: I/O port characteristics for more details on the input/output characteristics.

Symbol		Parameter	Min. <sup>(1)</sup>	Max. <sup>(1)</sup>	Unit		
Input level	$V_{DD}$	USB OTG HS operating voltage	2.7	3.6	V		

#### Table 60. USB HS DC electrical characteristics

1. All the voltages are measured from the local ground potential.

Table 61. USB HS clock timing parameters <sup>(</sup>
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	• •					
Parameter	Symbol	Min	Nominal	Max	Unit	
f <sub>HCLK</sub> value to guarantee prop USB HS interface	-	30	-	-	MHz	
Frequency (first transition) 8-bit ±10%		F <sub>START_8BIT</sub>	54	60	66	MHz



Parameter		Symbol	Min	Nominal	Max	Unit
Frequency (steady state) ±500 ppm		F <sub>STEADY</sub>	59.97	60	60.03	MHz
Duty cycle (first transition) 8-bit ±10%		D <sub>START_8BIT</sub>	40	50	60	%
Duty cycle (steady state) ±500	D <sub>STEADY</sub>	49.975	50	50.025	%	
Time to reach the steady state duty cycle after the first transit	T <sub>STEADY</sub>	-	-	1.4	ms	
Clock startup time after the	Peripheral	T <sub>START_DEV</sub>	-	-	5.6	80
de-assertion of SuspendM	Host	T <sub>START_HOST</sub>	-	-	-	ms
PHY preparation time after the first transition of the input clock		T <sub>PREP</sub>	-	-	-	μs

## Table 61. USB HS clock timing parameters<sup>(1)</sup>

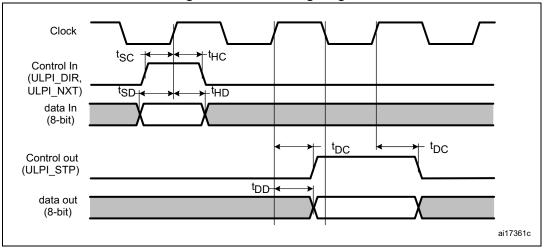
1. Guaranteed by design.

Parameter	Symbol	Valu	Unit		
Falameter	Symbol	Min.	Max.	Unit	
Control in (ULPI_DIR) setup time	+	-	2.0		
Control in (ULPI_NXT) setup time	t <sub>sc</sub>	-	1.5		
Control in (ULPI_DIR, ULPI_NXT) hold time	t <sub>HC</sub>	0	-		
Data in setup time	t <sub>SD</sub>	-	2.0	ns	
Data in hold time	t <sub>HD</sub>	0	-		
Control out (ULPI_STP) setup time and hold time	t <sub>DC</sub>	-	9.2		
Data out available from clock rising edge	t <sub>DD</sub>	-	10.7		

## Table 62. ULPI timing

1. V<sub>DD</sub> = 2.7 V to 3.6 V and T<sub>A</sub> = –40 to 85 °C.

#### Figure 45. ULPI timing diagram



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#### **Ethernet characteristics**

Unless otherwise specified, the parameters given in *Table 64*, *Table 65* and *Table 66* for SMI, RMII and MII are derived from tests performed under the ambient temperature, f<sub>HCLK</sub> frequency summarized in *Table 14* and VDD supply voltage conditions summarized in *Table 63*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>.

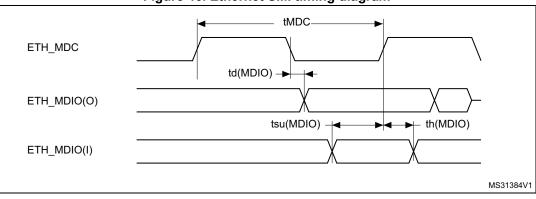
Refer to Section 5.3.16: I/O port characteristics for more details on the input/output characteristics.

Symbol		Parameter	Min. <sup>(1)</sup>	Max. <sup>(1)</sup>	Unit
Input level	V <sub>DD</sub>	Ethernet operating voltage	2.7	3.6	V

Table 63. Ethernet DC electrical characteristics

1. All the voltages are measured from the local ground potential.

*Table 64* gives the list of Ethernet MAC signals for the SMI (station management interface) and *Figure 46* shows the corresponding timing diagram.



#### Figure 46. Ethernet SMI timing diagram

Table 64. D	ynamic characteristics: Ethernet MAC signals for SMI <sup>(1)</sup>
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Symbol	Parameter	Min	Тур	Мах	Unit
t <sub>MDC</sub>	MDC cycle time(2.38 MHz)	411	420	425	
T <sub>d(MDIO)</sub>	Write data valid time	6	10	13	ne
t <sub>su(MDIO)</sub>	Read data setup time	12	-	-	ns
t <sub>h(MDIO)</sub>	Read data hold time	0	-	-	

1. Guaranteed by characterization.

*Table 65* gives the list of Ethernet MAC signals for the RMII and *Figure 47* shows the corresponding timing diagram.



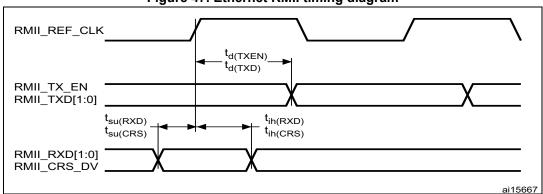


Figure 47. Ethernet RMII timing diagram



Symbol	Rating	Min	Тур	Мах	Unit
t <sub>su(RXD)</sub>	Receive data setup time	2	-	-	ns
t <sub>ih(RXD)</sub>	Receive data hold time	1	-	-	ns
t <sub>su(CRS)</sub>	Carrier sense set-up time	0.5	-	-	ns
t <sub>ih(CRS)</sub>	Carrier sense hold time	2	-	-	ns
t <sub>d(TXEN)</sub>	Transmit enable valid delay time	8	9.5	11	ns
t <sub>d(TXD)</sub>	Transmit data valid delay time		10	11.5	ns

*Table 66* gives the list of Ethernet MAC signals for MII and *Figure 47* shows the corresponding timing diagram.

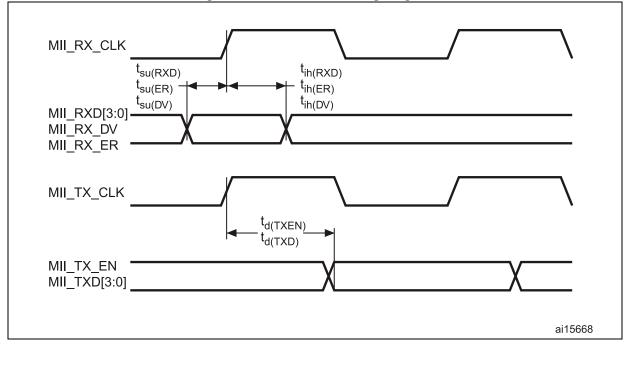


Figure 48. Ethernet MII timing diagram

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Symbol	Parameter	Min	Тур	Max	Unit
t <sub>su(RXD)</sub>	Receive data setup time	9		-	
t <sub>ih(RXD)</sub>	Receive data hold time	10		-	
t <sub>su(DV)</sub>	Data valid setup time	9		-	
t <sub>ih(DV)</sub>	Data valid hold time	8		-	
t <sub>su(ER)</sub>	Error setup time	6		-	– ns
t <sub>ih(ER)</sub>	Error hold time	8		-	
t <sub>d(TXEN)</sub>	Transmit enable valid delay time	0	10	14	
t <sub>d(TXD)</sub>	Transmit data valid delay time	0	10	15	

 Table 66. Dynamic characteristics: Ethernet MAC signals for MII<sup>(1)</sup>

1. Guaranteed by characterization.

# 5.3.20 CAN (controller area network) interface

Refer to Section 5.3.16: I/O port characteristics for more details on the input/output alternate function characteristics (CANTX and CANRX).

# 5.3.21 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table* 67 are derived from tests performed under the ambient temperature,  $f_{PCLK2}$  frequency and  $V_{DDA}$  supply voltage conditions summarized in *Table* 14.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DDA</sub>	Power supply	-	1.8 <sup>(1)</sup>	-	3.6	
V <sub>REF+</sub>	Positive reference voltage	-	1.8 <sup>(1)(2)(3)</sup>	-	V <sub>DDA</sub>	V
$V_{REF-}$	Negative reference voltage	-	-	0	-	
f <sub>ADC</sub>	ADC clock frequency	V <sub>DDA</sub> = 1.8 <sup>(1)(3)</sup> to 2.4 V	0.6	15	18	MHz
		$V_{DDA}$ = 2.4 to 3.6 V <sup>(3)</sup>	0.6	30	36	MHz
f <sub>TRIG</sub> <sup>(4)</sup>	External trigger frequency	f <sub>ADC</sub> = 30 MHz, 12-bit resolution	-	-	1764	kHz
		-	-	-	17	1/f <sub>ADC</sub>
V <sub>AIN</sub>	Conversion voltage range <sup>(5)</sup>	-	0 (V <sub>SSA</sub> or V <sub>REF-</sub> tied to ground)	-	V <sub>REF+</sub>	V
R <sub>AIN</sub> <sup>(4)</sup>	External input impedance	See <i>Equation 1</i> for details	-	-	50	κΩ
$R_{ADC}^{(4)(6)}$	Sampling switch resistance	-	-	-	6	кΩ
C <sub>ADC</sub> <sup>(4)</sup>	Internal sample and hold capacitor	-	-	4	-	pF



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>lat</sub> <sup>(4)</sup>	Injection trigger conversion	f <sub>ADC</sub> = 30 MHz	-	-	0.100	μs
<sup>l</sup> lat` ′	latency		-	-	3 <sup>(7)</sup>	1/f <sub>ADC</sub>
t <sub>latr</sub> (4)	Regular trigger conversion	f <sub>ADC</sub> = 30 MHz	-	-	0.067	μs
'latr` ´	latency		-	-	2 <sup>(7)</sup>	1/f <sub>ADC</sub>
t <sub>S</sub> <sup>(4)</sup>	Sampling time	f <sub>ADC</sub> = 30 MHz	0.100	-	16	μs
'S'		-	3	-	480	1/f <sub>ADC</sub>
t <sub>STAB</sub> <sup>(4)</sup>	Power-up time	-	-	2	3	μs
		f <sub>ADC</sub> = 30 MHz 12-bit resolution	0.50	-	16.40	μs
		f <sub>ADC</sub> = 30 MHz 10-bit resolution	0.43	-	16.34	μs
t <sub>CONV</sub> <sup>(4)</sup>	Total conversion time (including sampling time)	f <sub>ADC</sub> = 30 MHz 8-bit resolution	0.37	-	16.27	μs
		f <sub>ADC</sub> = 30 MHz 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t <sub>S</sub> for sampling approximation)	+n-bit resolution f	or succes	ssive	1/f <sub>ADC</sub>
		12-bit resolution Single ADC	-	-	2	Msps
f <sub>S</sub> <sup>(4)</sup>	Sampling rate (f <sub>ADC</sub> = 30 MHz, and t <sub>S</sub> = 3 ADC cycles)	12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msps
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msps
I <sub>VREF+</sub> (4)	ADC V <sub>REF</sub> DC current consumption in conversion mode	-	-	300	500	μA
I <sub>VDDA</sub> <sup>(4)</sup>	ADC V <sub>DDA</sub> DC current consumption in conversion mode	-	-	1.6	1.8	mA

#### Table 67. ADC characteristics (continued)

 V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to Section : Internal reset OFF).

2. It is recommended to maintain the voltage difference between V\_{REF+} and V\_{DDA} below 1.8 V.

3.  $V_{DDA} - V_{REF+} < 1.2 V.$ 

4. Guaranteed by characterization.

5.  $V_{REF+}$  is internally connected to  $V_{DDA}$  and  $V_{REF-}$  is internally connected to  $V_{SSA}$ .

6.  $R_{ADC}$  maximum value is given for  $V_{DD}\mbox{=}1.8$  V, and minimum value for  $V_{DD}\mbox{=}3.3$  V.

7. For external triggers, a delay of 1/f<sub>PCLK2</sub> must be added to the latency specified in *Table* 67.

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# Equation 1: R<sub>AIN</sub> max formula

$$\mathsf{R}_{\mathsf{AIN}} \, = \, \frac{(k-0.5)}{f_{\mathsf{ADC}} \times C_{\mathsf{ADC}} \times \ln(2^{N+2})} - \mathsf{R}_{\mathsf{ADC}}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC\_SMPR1 register.

7 700					
Symbol	Parameter	Test conditions	Тур	Max <sup>(1)</sup>	Unit
ET	Total unadjusted error		±2	±5	
EO	Offset error	f <sub>PCLK2</sub> = 60 MHz,	±1.5	±2.5	
EG	Gain error	$f_{ADC} = 30 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega, V_{DDA} = 1.8^{(2)} \text{ to } 3.6 \text{ V}$	±1.5	±3	LSB
ED	Differential linearity error	$V_{DDA} = 1.8^{(2)}$ to 3.6 V	±1	±2	
EL	Integral linearity error		±1.5	±3	
1 0					

Table 68	ADC	accuracy	at f <sub>ADC</sub> :	= 30 MHz
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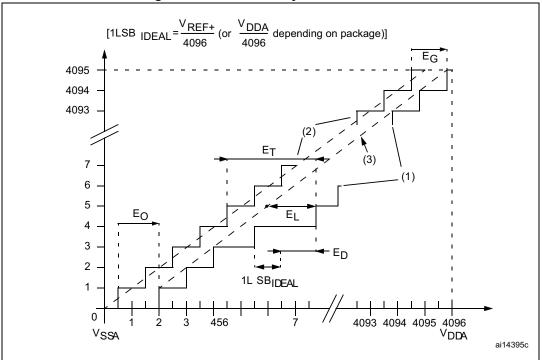
1. Guaranteed by characterization.

 V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to Section : Internal reset OFF).

Note:

te: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents. Any positive injection current within the limits specified for I<sub>INJ(PIN)</sub> and SI<sub>INJ(PIN)</sub> in Section 5.3.16 does not affect the ADC accuracy.



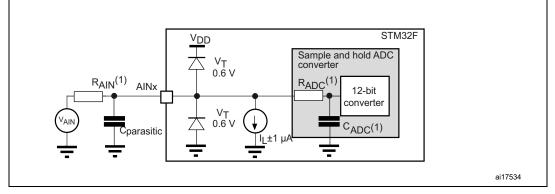




- See also Table 68. 1.
- 2. Example of an actual transfer curve.
- Ideal transfer curve. 3.
- 4. End point correlation line.
- $E_T$  = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves. 5. EO = Offset Error: deviation between the first actual transition and the first ideal one. EG = Gain Error: deviation between the last ideal transition and the last actual one. ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.

EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.





- Refer to Table 67 for the values of  $\mathsf{R}_{AIN},\,\mathsf{R}_{ADC}$  and  $\mathsf{C}_{ADC}.$ 1.
- $C_{parasitic}$  represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high  $C_{parasitic}$  value downgrades conversion accuracy. To remedy this, f<sub>ADC</sub> should be reduced. 2.



## **General PCB design guidelines**

Power supply decoupling should be performed as shown in *Figure 51* or *Figure 52*, depending on whether V<sub>REF+</sub> is connected to V<sub>DDA</sub> or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

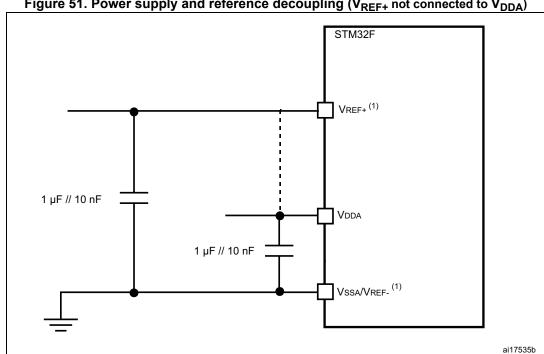


Figure 51. Power supply and reference decoupling (V<sub>REF+</sub> not connected to V<sub>DDA</sub>)

 $V_{REF+}$  and  $V_{REF-}$  inputs are both available on UFBGA176.  $V_{REF+}$  is also available on LQFP100, LQFP144, and LQFP176. When  $V_{REF+}$  and  $V_{REF-}$  are not available, they are internally connected to  $V_{DDA}$  and  $V_{SSA}$ . 1.



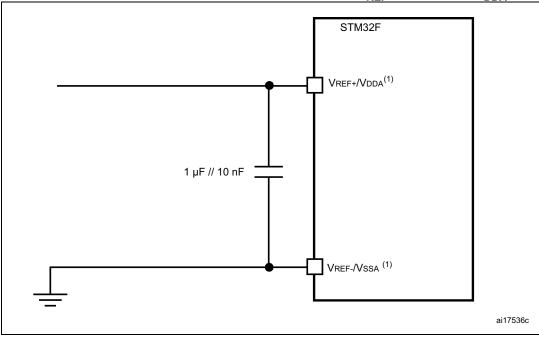


Figure 52. Power supply and reference decoupling (V<sub>REF+</sub> connected to V<sub>DDA</sub>)

1.  $V_{REF+}$  and  $V_{REF-}$  inputs are both available on UFBGA176.  $V_{REF+}$  is also available on LQFP100, LQFP144, and LQFP176. When  $V_{REF+}$  and  $V_{REF-}$  are not available, they are internally connected to  $V_{DDA}$  and  $V_{SSA}$ .

# 5.3.22 Temperature sensor characteristics

Table 69.	Temperature	sensor	characteristics
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Symbol	Parameter		Тур	Max	Unit
T <sub>L</sub> <sup>(1)</sup>	V <sub>SENSE</sub> linearity with temperature	-	±1	±2	°C
Avg_Slope <sup>(1)</sup>	Average slope	-	2.5		mV/°C
V <sub>25</sub> <sup>(1)</sup>	Voltage at 25 °C	-	0.76		V
t <sub>START</sub> <sup>(2)</sup>	Startup time	-	6	10	μs
T <sub>S_temp</sub> <sup>(2)</sup>	ADC sampling time when reading the temperature (1 °C accuracy)	10	-	-	μs

1. Guaranteed by characterization.

2. Guaranteed by design.

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 $^\circ$ C, V <sub>DDA</sub> =3.3 V	0x1FFF 7A2C - 0x1FFF 7A2D
TS_CAL2	TS ADC raw data acquired at temperature of 110 $^{\circ}$ C, V <sub>DDA</sub> =3.3 V	0x1FFF 7A2E - 0x1FFF 7A2F

## Table 70. Temperature sensor calibration values



# 5.3.23 V<sub>BAT</sub> monitoring characteristics

Symbol	Parameter		Тур	Мах	Unit
R	Resistor bridge for V <sub>BAT</sub>	-	50	-	KΩ
Q	Ratio on V <sub>BAT</sub> measurement	-	2	-	
Er <sup>(1)</sup>	Error on Q	-1	-	+1	%
T <sub>S_vbat</sub> <sup>(2)(2)</sup>	ADC sampling time when reading the V <sub>BAT</sub> 1 mV accuracy	5	-	-	μs

Table 71. V<sub>BAT</sub> monitoring characteristics

1. Guaranteed by design.

2. Shortest sampling time can be determined in the application by multiple iterations.

# 5.3.24 Embedded reference voltage

The parameters given in *Table 72* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>REFINT</sub>	Internal reference voltage	–40 °C < T <sub>A</sub> < +105 °C	1.18	1.21	1.24	V
T <sub>S_vrefint</sub> <sup>(1)</sup>	ADC sampling time when reading the internal reference voltage	-	10	-	-	μs
V <sub>RERINT_s</sub> <sup>(2)</sup>	Internal reference voltage spread over the temperature range	V <sub>DD</sub> = 3 V	-	3	5	mV
T <sub>Coeff</sub> <sup>(2)</sup>	Temperature coefficient	-	-	30	50	ppm/°C
t <sub>START</sub> <sup>(2)</sup>	Startup time	-	-	6	10	μs

Table 72. Embedded internal reference voltage

1. Shortest sampling time can be determined in the application by multiple iterations.

2. Guaranteed by design.

#### Table 73. Internal reference voltage calibration values

Symbol	Parameter	Memory address
$V_{REFIN\_CAL}$	Raw data acquired at temperature of 30 °C, V <sub>DDA</sub> =3.3 V	0x1FFF 7A2A - 0x1FFF 7A2B

# 5.3.25 DAC electrical characteristics

Symbol	Parameter	Min	Тур	Max	Unit	Comments
V <sub>DDA</sub>	Analog supply voltage	1.8 <sup>(1)</sup>	-	3.6	V	
V <sub>REF+</sub>	Reference supply voltage	1.8 <sup>(1)</sup>	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V <sub>SSA</sub>	Ground	0	-	0	V	



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#### **Electrical characteristics**

Symbol	Parameter	Min	Тур	Max	Unit	Comments
R <sub>LOAD</sub> <sup>(2)</sup>	Resistive load with buffer ON	5	-	-	kΩ	
R <sub>0</sub> <sup>(2)</sup>	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and $V_{SS}$ to have a 1% accuracy is 1.5 $M\Omega$
C <sub>LOAD</sub> <sup>(2)</sup>	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min <sup>(2)</sup>	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V <sub>REF+</sub> =
DAC_OUT max <sup>(2)</sup>	Higher DAC_OUT voltage with buffer ON	-	-	V <sub>DDA</sub> – 0.2	V	3.6 V and (0x1C7) to (0xE38) at $V_{REF+} = 1.8 V$
DAC_OUT min <sup>(2)</sup>	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output
DAC_OUT max <sup>(2)</sup>	Higher DAC_OUT voltage with buffer OFF	-	-	V <sub>REF+</sub> – 1LSB	V	excursion of the DAC.
I <sub>VREF+</sub> <sup>(4)</sup>	DAC DC V <sub>REF</sub> current consumption in quiescent	-	170	240	μA	With no load, worst code (0x800) at $V_{REF+}$ = 3.6 V in terms of DC consumption on the inputs
'VREF+`´	mode (Standby mode)	-	50	75	μΑ	With no load, worst code (0xF1C) at $V_{REF+}$ = 3.6 V in terms of DC consumption on the inputs
	DAC DC VDDA current	-	280	380	μA	With no load, middle code (0x800) on the inputs
I <sub>DDA</sub> <sup>(4)</sup>	consumption in quiescent mode <sup>(3)</sup>	-	475	625	μΑ	With no load, worst code (0xF1C) at $V_{REF+}$ = 3.6 V in terms of DC consumption on the inputs
DNL <sup>(4)</sup>	Differential non linearity Difference between two	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration.
	consecutive code-1LSB)	-	-	±2	LSB	Given for the DAC in 12-bit configuration.
	Integral non linearity (difference between	-	-	±1	LSB	Given for the DAC in 10-bit configuration.
INL <sup>(4)</sup>	measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±4	LSB	Given for the DAC in 12-bit configuration.

# Table 74. DAC characteristics (continued)

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Table 74. DAC characteristics (continued)								
Symbol	Parameter	Min	Тур	Мах	Unit	Comments		
	Offset error	-	-	±10	mV	Given for the DAC in 12-bit configuration		
Offset <sup>(4)</sup>	(difference between measured value at Code (0x800) and the ideal value	-	-	±3	LSB	Given for the DAC in 10-bit at $V_{REF+}$ = 3.6 V		
	= V <sub>REF+</sub> /2)	-	-	±12	LSB	Given for the DAC in 12-bit at $V_{REF+}$ = 3.6 V		
Gain error <sup>(4)</sup>	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration		
t <sub>SETTLING</sub> <sup>(4)</sup>	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±4LSB	-	3	6	μs	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$		
THD <sup>(4)</sup>	Total Harmonic Distortion Buffer ON	-	-	-	dB	$\begin{array}{l} C_{LOAD} \leq ~50~\text{pF}, \\ R_{LOAD} \geq 5~\text{k}\Omega \end{array}$		
Update rate <sup>(2)</sup>	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \le 50 \text{ pF},$ $R_{LOAD} \ge 5 \text{ k}\Omega$		
t <sub>WAKEUP</sub> <sup>(4)</sup>	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	μs	$\begin{split} C_{LOAD} &\leq ~50~\text{pF},~R_{LOAD} \geq 5~\text{k}\Omega \\ \text{input code between lowest and} \\ \text{highest possible ones.} \end{split}$		
PSRR+ <sup>(2)</sup>	Power supply rejection ratio (to $V_{DDA}$ ) (static DC measurement)	-	-67	-40	dB	No R <sub>LOAD</sub> , C <sub>LOAD</sub> = 50 pF		

 V<sub>DD</sub>/V<sub>DDA</sub> minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to Section : Internal reset OFF).

2. Guaranteed by design.

3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.



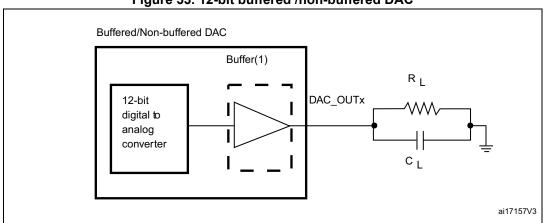


Figure 53. 12-bit buffered /non-buffered DAC

1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC\_CR register.

## 5.3.26 FSMC characteristics

Unless otherwise specified, the parameters given in *Table 75* to *Table 86* for the FSMC interface are derived from tests performed under the ambient temperature,  $f_{HCLK}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 14*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>

Refer to Section Section 5.3.16: I/O port characteristics for more details on the input/output characteristics.

#### Asynchronous waveforms and timings

*Figure 54* through *Figure 57* represent asynchronous waveforms and *Table 75* through *Table 78* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- AddressSetupTime = 1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1
- BusTurnAroundDuration = 0x0

In all timing tables, the  $T_{HCLK}$  is the HCLK clock period.



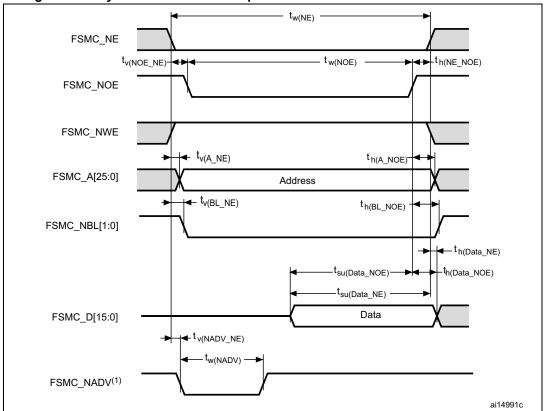


Figure 54. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms

1. Mode 2/B, C and D only. In Mode 1, FSMC\_NADV is not used.

# Table 75. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FSMC_NE low time	2T <sub>HCLK</sub> -0.5	2 T <sub>HCLK</sub> +1	ns
t <sub>v(NOE_NE)</sub>	FSMC_NEx low to FSMC_NOE low	0.5	3	ns
t <sub>w(NOE)</sub>	FSMC_NOE low time	2T <sub>HCLK</sub> –2	2T <sub>HCLK</sub> + 2	ns
t <sub>h(NE_NOE)</sub>	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
t <sub>v(A_NE)</sub>	FSMC_NEx low to FSMC_A valid	-	4.5	ns
t <sub>h(A_NOE)</sub>	Address hold time after FSMC_NOE high	4	-	ns
t <sub>v(BL_NE)</sub>	FSMC_NEx low to FSMC_BL valid	-	1.5	ns
t <sub>h(BL_NOE)</sub>	FSMC_BL hold time after FSMC_NOE high	0	-	ns
t <sub>su(Data_NE)</sub>	Data to FSMC_NEx high setup time	T <sub>HCLK</sub> +4	-	ns
t <sub>su(Data_NOE)</sub>	Data to FSMC_NOEx high setup time	T <sub>HCLK</sub> +4	-	ns
t <sub>h(Data_NOE)</sub>	Data hold time after FSMC_NOE high	0	-	ns
t <sub>h(Data_NE)</sub>	Data hold time after FSMC_NEx high	0	-	ns
t <sub>v(NADV_NE)</sub>	FSMC_NEx low to FSMC_NADV low	-	2	ns
t <sub>w(NADV)</sub>	FSMC_NADV low time	-	T <sub>HCLK</sub>	ns

1. C<sub>L</sub> = 30 pF.



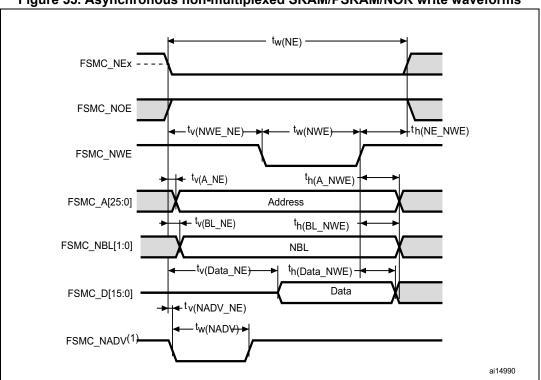


Figure 55. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms

1. Mode 2/B, C and D only. In Mode 1, FSMC\_NADV is not used.

Table 76. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings <sup>(1)(2</sup>	2)
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Symbol	Parameter	Min	Мах	Unit
t <sub>w(NE)</sub>	FSMC_NE low time	3T <sub>HCLK</sub>	3T <sub>HCLK</sub> + 4	ns
t <sub>v(NWE_NE)</sub>	FSMC_NEx low to FSMC_NWE low	T <sub>HCLK</sub> –0.5	T <sub>HCLK</sub> +0.5	ns
t <sub>w(NWE)</sub>	FSMC_NWE low time	T <sub>HCLK</sub> –1	T <sub>HCLK</sub> +2	ns
t <sub>h(NE_NWE)</sub>	FSMC_NWE high to FSMC_NE high hold time	T <sub>HCLK</sub> –1	-	ns
t <sub>v(A_NE)</sub>	FSMC_NEx low to FSMC_A valid	-	0	ns
t <sub>h(A_NWE)</sub>	Address hold time after FSMC_NWE high	T <sub>HCLK</sub> – 2	-	ns
t <sub>v(BL_NE)</sub>	FSMC_NEx low to FSMC_BL valid	-	1.5	ns
t <sub>h(BL_NWE)</sub>	FSMC_BL hold time after FSMC_NWE high	T <sub>HCLK</sub> – 1	-	ns
t <sub>v(Data_NE)</sub>	Data to FSMC_NEx low to Data valid	-	T <sub>HCLK</sub> +3	ns
t <sub>h(Data_NWE)</sub>	Data hold time after FSMC_NWE high	T <sub>HCLK</sub> –1	-	ns
t <sub>v(NADV_NE)</sub>	FSMC_NEx low to FSMC_NADV low	-	2	ns
t <sub>w(NADV)</sub>	FSMC_NADV low time	-	T <sub>HCLK</sub> +0.5	ns

1. C<sub>L</sub> = 30 pF.



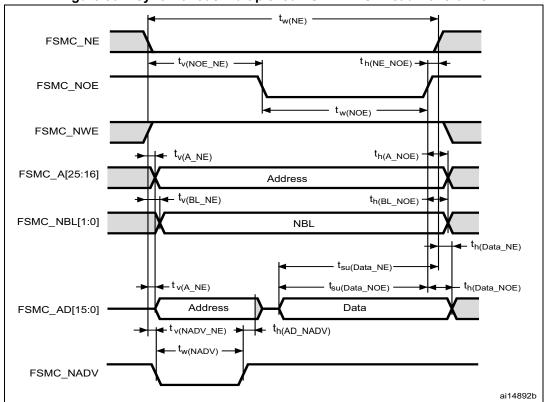


Figure 56. Asynchronous multiplexed PSRAM/NOR read waveforms

# Table 77. Asynchronous multiplexed PSRAM/NOR read timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Мах	Unit
t <sub>w(NE)</sub>	FSMC_NE low time	3T <sub>HCLK</sub> –1	3T <sub>HCLK</sub> +1	ns
t <sub>v(NOE_NE)</sub>	FSMC_NEx low to FSMC_NOE low	2T <sub>HCLK</sub> -0.5	2T <sub>HCLK</sub> +0.5	ns
t <sub>w(NOE)</sub>	FSMC_NOE low time	T <sub>HCLK</sub> –1	T <sub>HCLK</sub> +1	ns
t <sub>h(NE_NOE)</sub>	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
t <sub>v(A_NE)</sub>	FSMC_NEx low to FSMC_A valid	-	3	ns
t <sub>v(NADV_NE)</sub>	FSMC_NEx low to FSMC_NADV low	1	2	ns
t <sub>w(NADV)</sub>	FSMC_NADV low time	T <sub>HCLK</sub> – 2	T <sub>HCLK</sub> +1	ns
t <sub>h(AD_NADV)</sub>	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T <sub>HCLK</sub>	-	ns
t <sub>h(A_NOE)</sub>	Address hold time after FSMC_NOE high	T <sub>HCLK</sub> –1	-	ns
t <sub>h(BL_NOE)</sub>	FSMC_BL time after FSMC_NOE high	0	-	ns
t <sub>v(BL_NE)</sub>	FSMC_NEx low to FSMC_BL valid	-	2	ns
t <sub>su(Data_NE)</sub>	Data to FSMC_NEx high setup time	T <sub>HCLK</sub> +4	-	ns
t <sub>su(Data_NOE)</sub>	Data to FSMC_NOE high setup time	T <sub>HCLK</sub> +4	-	ns
t <sub>h(Data_NE)</sub>	Data hold time after FSMC_NEx high	0	-	ns
t <sub>h(Data_NOE)</sub>	Data hold time after FSMC_NOE high	0	-	ns

1. C<sub>L</sub> = 30 pF.



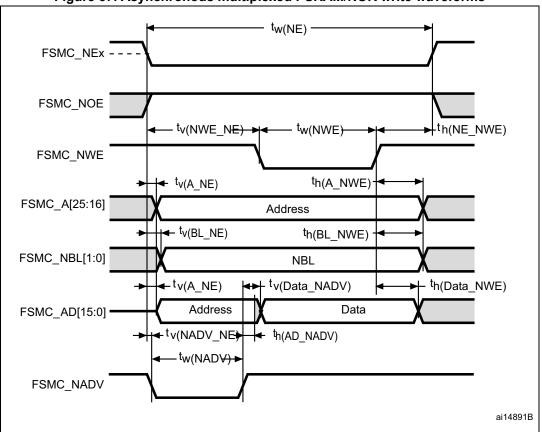


Figure 57. Asynchronous multiplexed PSRAM/NOR write waveforms

Table 79 Ac	unabranava multi	played DSDAM/N	OR write timings <sup>(1)(2)</sup>
Table 78. As	ynchronous muiti	piexea PSRAM/N	OR write timings

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FSMC_NE low time	4T <sub>HCLK</sub> –0.5	4T <sub>HCLK</sub> +3	ns
t <sub>v(NWE_NE)</sub>	FSMC_NEx low to FSMC_NWE low	T <sub>HCLK</sub> –0.5	T <sub>HCLK</sub> -0.5	ns
t <sub>w(NWE)</sub>	FSMC_NWE low tim e	2T <sub>HCLK</sub> –0.5	2T <sub>HCLK</sub> +3	ns
t <sub>h(NE_NWE)</sub>	FSMC_NWE high to FSMC_NE high hold time	T <sub>HCLK</sub>	-	ns
t <sub>v(A_NE)</sub>	FSMC_NEx low to FSMC_A valid	-	0	ns
t <sub>v(NADV_NE)</sub>	FSMC_NEx low to FSMC_NADV low	1	2	ns
t <sub>w(NADV)</sub>	FSMC_NADV low time	T <sub>HCLK</sub> – 2	T <sub>HCLK</sub> + 1	ns
t <sub>h(AD_NADV)</sub>	FSMC_AD(address) valid hold time after FSMC_NADV high)	T <sub>HCLK</sub> –2	-	ns
t <sub>h(A_NWE)</sub>	Address hold time after FSMC_NWE high	T <sub>HCLK</sub>	-	ns
t <sub>h(BL_NWE)</sub>	FSMC_BL hold time after FSMC_NWE high	T <sub>HCLK</sub> –2	-	ns
t <sub>v(BL_NE)</sub>	FSMC_NEx low to FSMC_BL valid	-	1.5	ns
t <sub>v(Data_NADV)</sub>	FSMC_NADV high to Data valid	-	T <sub>HCLK</sub> –0.5	ns
t <sub>h(Data_NWE)</sub>	Data hold time after FSMC_NWE high	T <sub>HCLK</sub>	-	ns



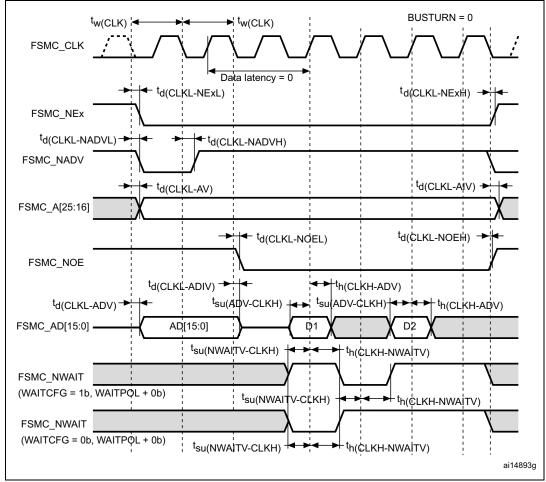
2. Guaranteed by characterization.

### Synchronous waveforms and timings

*Figure 58* through *Figure 61* represent synchronous waveforms and *Table 80* through *Table 82* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FSMC\_BurstAccessMode\_Enable;
- MemoryType = FSMC\_MemoryType\_CRAM;
- WriteBurst = FSMC\_WriteBurst\_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F40xxx/41xxx reference manual)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the  $T_{HCLK}$  is the HCLK clock period (with maximum FSMC\_CLK = 60 MHz).







Symbol	Parameter	Min	Мах	Unit
t <sub>w(CLK)</sub>	FSMC_CLK period	2T <sub>HCLK</sub>	-	ns
t <sub>d(CLKL-NExL)</sub>	FSMC_CLK low to FSMC_NEx low (x=02)	-	0	ns
t <sub>d(CLKL-NExH)</sub>	FSMC_CLK low to FSMC_NEx high (x= 02)	2	-	ns
t <sub>d(CLKL-NADVL)</sub>	FSMC_CLK low to FSMC_NADV low	-	2	ns
t <sub>d(CLKL-NADVH)</sub>	FSMC_CLK low to FSMC_NADV high	2	-	ns
t <sub>d(CLKL-AV)</sub>	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	ns
t <sub>d(CLKL-AIV)</sub>	FSMC_CLK low to FSMC_Ax invalid (x=1625)	0	-	ns
$t_{d(CLKL-NOEL)}$	FSMC_CLK low to FSMC_NOE low	-	0	ns
t <sub>d(CLKL-NOEH)</sub>	FSMC_CLK low to FSMC_NOE high	2	-	ns
t <sub>d(CLKL-ADV)</sub>	FSMC_CLK low to FSMC_AD[15:0] valid	-	4.5	ns
t <sub>d(CLKL-ADIV)</sub>	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
t <sub>su(ADV-CLKH)</sub>	FSMC_A/D[15:0] valid data before FSMC_CLK high	6	-	ns
t <sub>h(CLKH-ADV)</sub>	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	ns
t <sub>su(NWAIT-CLKH)</sub>	FSMC_NWAIT valid before FSMC_CLK high	4	-	ns
t <sub>h(CLKH-NWAIT)</sub>	FSMC_NWAIT valid after FSMC_CLK high	0	-	ns

Table 79. Synchronous multiplexed NOR/PSRAM read timings<sup>(1)(2)</sup>

2. Guaranteed by characterization.

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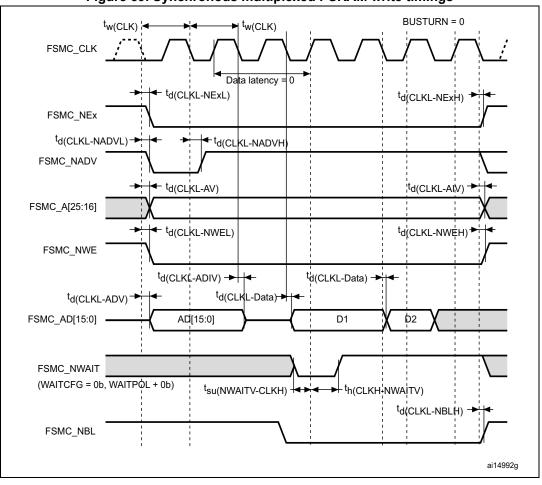


Figure 59. Synchronous multiplexed PSRAM write timings

lable 80. Synchronous multiplexed PSRAM write timinds '//-/	Table 80, Synchronous multi	plexed PSRAM write timings <sup>(1)(2)</sup>
---	-----------------------------	--

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FSMC_CLK period	2T <sub>HCLK</sub>	-	ns
t <sub>d(CLKL-NExL)</sub>	FSMC_CLK low to FSMC_NEx low (x=02)	-	1	ns
t <sub>d(CLKL-NExH)</sub>	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	ns
t <sub>d(CLKL-NADVL)</sub>	FSMC_CLK low to FSMC_NADV low	-	0	ns
t <sub>d(CLKL-</sub> NADVH)	FSMC_CLK low to FSMC_NADV high	0	-	ns
t <sub>d(CLKL-AV)</sub>	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	ns
t <sub>d(CLKL-AIV)</sub>	FSMC_CLK low to FSMC_Ax invalid (x=1625)	8	-	ns
t <sub>d(CLKL-NWEL)</sub>	FSMC_CLK low to FSMC_NWE low	-	0.5	ns
t <sub>d(CLKL-NWEH)</sub>	FSMC_CLK low to FSMC_NWE high	0	-	ns
t <sub>d(CLKL-ADIV)</sub>	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
t <sub>d(CLKL-DATA)</sub>	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	3	ns

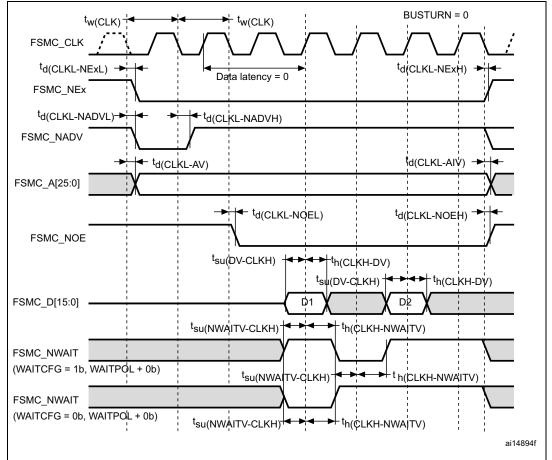


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Symbol	Parameter	Min	Max	Unit
t <sub>d(CLKL-NBLH)</sub>	FSMC_CLK low to FSMC_NBL high	0	-	ns
t <sub>su(NWAIT-</sub> CLKH)	FSMC_NWAIT valid before FSMC_CLK high	4	-	ns
$t_{h(CLKH-NWAIT)}$	FSMC_NWAIT valid after FSMC_CLK high	0	-	ns

Table 80. Synchronous multiplexed PSRAM write timings<sup>(1)(2)</sup> (continued)

2. Guaranteed by characterization.



## Figure 60. Synchronous non-multiplexed NOR/PSRAM read timings

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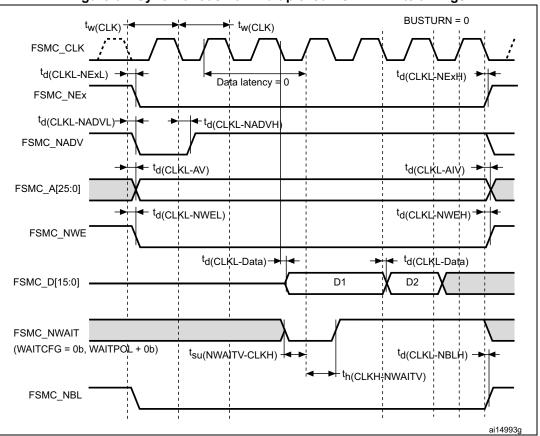


Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FSMC_CLK period	2T <sub>HCLK</sub> –0.5	-	ns
t <sub>d(CLKL-NExL)</sub>	FSMC_CLK low to FSMC_NEx low (x=02)	-	0.5	ns
t <sub>d(CLKL-NExH)</sub>	FSMC_CLK low to FSMC_NEx high (x= 02)	0	-	ns
t <sub>d(CLKL-NADVL)</sub>	FSMC_CLK low to FSMC_NADV low	-	2	ns
t <sub>d(CLKL-NADVH)</sub>	FSMC_CLK low to FSMC_NADV high	3	-	ns
t <sub>d(CLKL-AV)</sub>	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	ns
t <sub>d(CLKL-AIV)</sub>	FSMC_CLK low to FSMC_Ax invalid (x=1625)	2	-	ns
t <sub>d(CLKL-NOEL)</sub>	FSMC_CLK low to FSMC_NOE low	-	0.5	ns
t <sub>d(CLKL-NOEH)</sub>	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
t <sub>su(DV-CLKH)</sub>	FSMC_D[15:0] valid data before FSMC_CLK high	6	-	ns
t <sub>h(CLKH-DV)</sub>	FSMC_D[15:0] valid data after FSMC_CLK high	3	-	ns
t <sub>su(NWAIT-CLKH)</sub>	FSMC_NWAIT valid before FSMC_CLK high	4	-	ns
t <sub>h(CLKH-NWAIT)</sub>	FSMC_NWAIT valid after FSMC_CLK high	0	-	ns

Table 81. Synchronous non-multiplexed NOR/PSRAM read timings  $^{(1)(2)}$ 

2. Guaranteed by characterization.







### Table 82. Synchronous non-multiplexed PSRAM write timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FSMC_CLK period	2T <sub>HCLK</sub>	-	ns
t <sup>d(CLKL-NExL)</sup>	FSMC_CLK low to FSMC_NEx low (x=02)	-	1	ns
t <sub>d(CLKL-NExH)</sub>	FSMC_CLK low to FSMC_NEx high (x= 02)	1	-	ns
t <sub>d(CLKL-NADVL)</sub>	FSMC_CLK low to FSMC_NADV low	-	7	ns
t <sub>d(CLKL-NADVH)</sub>	FSMC_CLK low to FSMC_NADV high	6	-	ns
t <sub>d(CLKL-AV)</sub>	FSMC_CLK low to FSMC_Ax valid (x=1625)	-	0	ns
t <sub>d(CLKL-AIV)</sub>	FSMC_CLK low to FSMC_Ax invalid (x=1625)	6	-	ns
t <sub>d(CLKL-NWEL)</sub>	FSMC_CLK low to FSMC_NWE low	-	1	ns
t <sub>d(CLKL-NWEH)</sub>	FSMC_CLK low to FSMC_NWE high	2	-	ns
t <sub>d(CLKL-Data)</sub>	FSMC_D[15:0] valid data after FSMC_CLK low	-	3	ns
t <sub>d(CLKL-NBLH)</sub>	FSMC_CLK low to FSMC_NBL high	3	-	ns
t <sub>su(NWAIT-CLKH)</sub>	FSMC_NWAIT valid before FSMC_CLK high	4	-	ns
t <sub>h(CLKH-NWAIT)</sub>	FSMC_NWAIT valid after FSMC_CLK high	0	-	ns

1. C<sub>L</sub> = 30 pF.

2. Guaranteed by characterization.



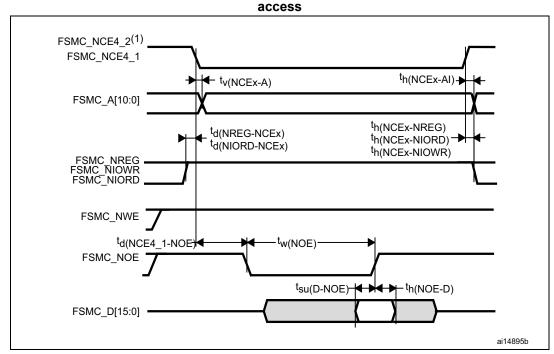
## PC Card/CompactFlash controller waveforms and timings

*Figure 62* through *Figure 67* represent synchronous waveforms, and *Table 83* and *Table 84* provide the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC\_SetupTime = 0x04;
- COM.FSMC\_WaitSetupTime = 0x07;
- COM.FSMC\_HoldSetupTime = 0x04;
- COM.FSMC\_HiZSetupTime = 0x00;
- ATT.FSMC\_SetupTime = 0x04;
- ATT.FSMC\_WaitSetupTime = 0x07;
- ATT.FSMC\_HoldSetupTime = 0x04;
- ATT.FSMC\_HiZSetupTime = 0x00;
- IO.FSMC\_SetupTime = 0x04;
- IO.FSMC\_WaitSetupTime = 0x07;
- IO.FSMC\_HoldSetupTime = 0x04;
- IO.FSMC\_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

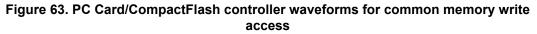
In all timing tables, the  $T_{HCLK}$  is the HCLK clock period.

## Figure 62. PC Card/CompactFlash controller waveforms for common memory read



#### 1. FSMC\_NCE4\_2 remains high (inactive during 8-bit access.





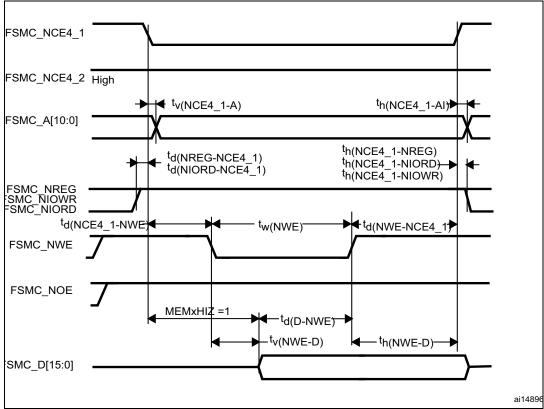
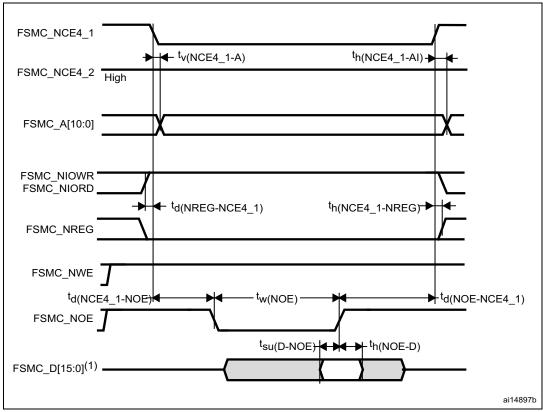




Figure 64. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).



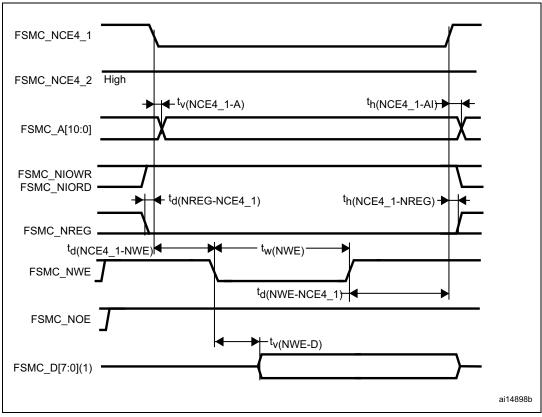
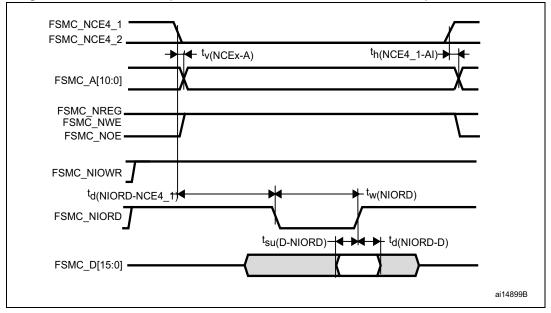


Figure 65. PC Card/CompactFlash controller waveforms for attribute memory write access

1. Only data bits 0...7 are driven (bits 8...15 remains Hi-Z).

#### Figure 66. PC Card/CompactFlash controller waveforms for I/O space read access



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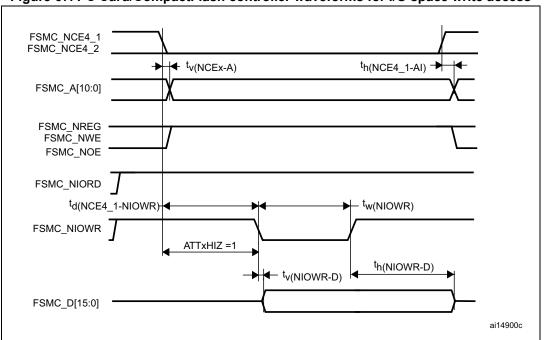


Figure 67. PC Card/CompactFlash controller waveforms for I/O space write access

Table 83. Switching characteristics for PC Card/CF read and write cycles in attribute/common space  $^{(1)(2)}$ 

Symbol	Parameter	Min	Мах	Unit
t <sub>v(NCEx-A)</sub>	FSMC_Ncex low to FSMC_Ay valid	-	0	ns
t <sub>h(NCEx_AI)</sub>	FSMC_NCEx high to FSMC_Ax invalid	4	-	ns
t <sub>d(NREG-NCEx)</sub>	FSMC_NCEx low to FSMC_NREG valid	-	3.5	ns
t <sub>h(NCEx-NREG)</sub>	FSMC_NCEx high to FSMC_NREG invalid	T <sub>HCLK</sub> +4	-	ns
t <sub>d(NCEx-NWE)</sub>	FSMC_NCEx low to FSMC_NWE low	-	5T <sub>HCLK</sub> +0.5	ns
t <sub>d(NCEx-NOE)</sub>	FSMC_NCEx low to FSMC_NOE low	-	5T <sub>HCLK</sub> +0.5	ns
t <sub>w(NOE)</sub>	FSMC_NOE low width	8T <sub>HCLK</sub> –1	8T <sub>HCLK</sub> +1	ns
t <sub>d(NOE_NCEx)</sub>	FSMC_NOE high to FSMC_NCEx high	5T <sub>HCLK</sub> +2.5	-	ns
t <sub>su (D-NOE)</sub>	FSMC_D[15:0] valid data before FSMC_NOE high	4.5	-	ns
t <sub>h(N0E-D)</sub>	FSMC_N0E high to FSMC_D[15:0] invalid	3	-	ns
t <sub>w(NWE)</sub>	FSMC_NWE low width	8T <sub>HCLK</sub> –0.5	8T <sub>HCLK</sub> + 3	ns
t <sub>d(NWE_NCEx)</sub>	FSMC_NWE high to FSMC_NCEx high	5T <sub>HCLK</sub> –1	-	ns
t <sub>d(NCEx-NWE)</sub>	FSMC_NCEx low to FSMC_NWE low	-	5T <sub>HCLK</sub> + 1	ns
t <sub>v(NWE-D)</sub>	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
t <sub>h</sub> (NWE-D)	FSMC_NWE high to FSMC_D[15:0] invalid	8T <sub>HCLK</sub> –1	-	ns
t <sub>d</sub> (D-NWE)	FSMC_D[15:0] valid before FSMC_NWE high	13T <sub>HCLK</sub> –1	-	ns

2. Guaranteed by characterization.



Table 84. Switching characteristics for PC Card/CF read and write cycles	
in I/O space <sup>(1)(2)</sup>	

Symbol	Parameter	Min	Max	Unit
t <sub>w(NIOWR)</sub>	FSMC_NIOWR low width	8T <sub>HCLK</sub> –1	-	ns
t <sub>v(NIOWR-D)</sub>	FSMC_NIOWR low to FSMC_D[15:0] valid	-	5T <sub>HCLK</sub> – 1	ns
t <sub>h(NIOWR-D)</sub>	FSMC_NIOWR high to FSMC_D[15:0] invalid	8T <sub>HCLK</sub> – 2	-	ns
t <sub>d(NCE4_1-NIOWR)</sub>	FSMC_NCE4_1 low to FSMC_NIOWR valid	-	5T <sub>HCLK</sub> + 2.5	ns
t <sub>h(NCEx-NIOWR)</sub>	FSMC_NCEx high to FSMC_NIOWR invalid	5T <sub>HCLK</sub> –1.5	-	ns
t <sub>d(NIORD-NCEx)</sub>	FSMC_NCEx low to FSMC_NIORD valid	-	5T <sub>HCLK</sub> + 2	ns
t <sub>h(NCEx-NIORD)</sub>	FSMC_NCEx high to FSMC_NIORD) valid	5T <sub>HCLK</sub> – 1.5	-	ns
t <sub>w(NIORD)</sub>	FSMC_NIORD low width	8T <sub>HCLK</sub> –0.5	-	ns
t <sub>su(D-NIORD)</sub>	FSMC_D[15:0] valid before FSMC_NIORD high	9	-	ns
t <sub>d(NIORD-D)</sub>	FSMC_D[15:0] valid after FSMC_NIORD high	0	-	ns

2. Guaranteed by characterization.

## NAND controller waveforms and timings

*Figure 68* through *Figure 71* represent synchronous waveforms, and *Table 85* and *Table 86* provide the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC\_SetupTime = 0x01;
- COM.FSMC\_WaitSetupTime = 0x03;
- COM.FSMC\_HoldSetupTime = 0x02;
- COM.FSMC\_HiZSetupTime = 0x01;
- ATT.FSMC\_SetupTime = 0x01;
- ATT.FSMC\_WaitSetupTime = 0x03;
- ATT.FSMC\_HoldSetupTime = 0x02;
- ATT.FSMC\_HiZSetupTime = 0x01;
- Bank = FSMC\_Bank\_NAND;
- MemoryDataWidth = FSMC\_MemoryDataWidth\_16b;
- ECC = FSMC\_ECC\_Enable;
- ECCPageSize = FSMC\_ECCPageSize\_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the  $T_{HCLK}$  is the HCLK clock period.



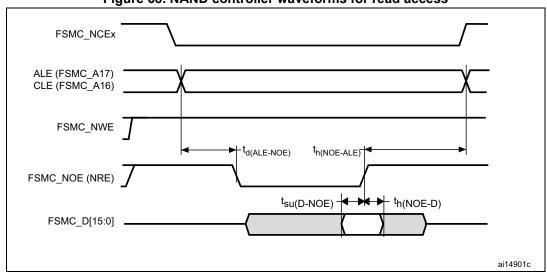
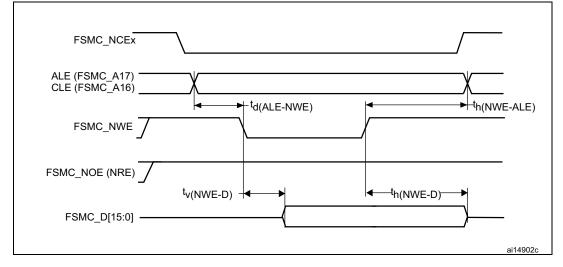


Figure 68. NAND controller waveforms for read access

Figure 69. NAND controller waveforms for write access





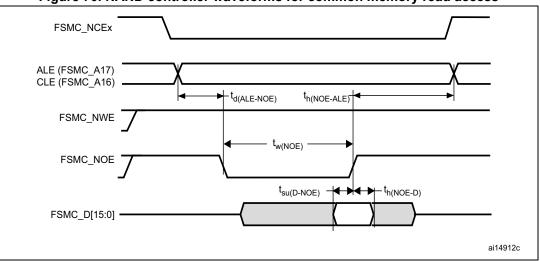


Figure 70. NAND controller waveforms for common memory read access

Figure 71. NAND controller waveforms for common memory write access

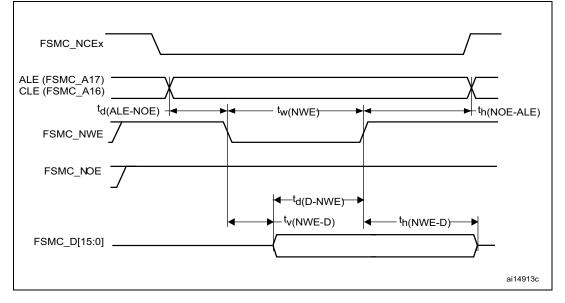


Table 85. Switching characteristics for NAND Flash read cycles<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NOE)</sub>	FSMC_NOE low width	4T <sub>HCLK</sub> – 0.5	4T <sub>HCLK</sub> + 3	ns
t <sub>su(D-NOE)</sub>	FSMC_D[15-0] valid data before FSMC_NOE high	10	-	ns
t <sub>h(NOE-D)</sub>	FSMC_D[15-0] valid data after FSMC_NOE high	0	-	ns
t <sub>d(ALE-NOE)</sub>	FSMC_ALE valid before FSMC_NOE low	-	3T <sub>HCLK</sub>	ns
t <sub>h(NOE-ALE)</sub>	FSMC_NWE high to FSMC_ALE invalid	3T <sub>HCLK</sub> – 2	-	ns



Symbol	Parameter	Min	Мах	Unit
t <sub>w(NWE)</sub>	FSMC_NWE low width	4T <sub>HCLK</sub> –1	4T <sub>HCLK</sub> + 3	ns
t <sub>v(NWE-D)</sub>	FSMC_NWE low to FSMC_D[15-0] valid	-	0	ns
t <sub>h(NWE-D)</sub>	FSMC_NWE high to FSMC_D[15-0] invalid	3T <sub>HCLK</sub> –2	-	ns
t <sub>d(D-NWE)</sub>	FSMC_D[15-0] valid before FSMC_NWE high	5T <sub>HCLK</sub> –3	-	ns
t <sub>d(ALE-NWE)</sub>	FSMC_ALE valid before FSMC_NWE low	-	3T <sub>HCLK</sub>	ns
t <sub>h(NWE-ALE)</sub>	FSMC_NWE high to FSMC_ALE invalid	3T <sub>HCLK</sub> –2	-	ns

 Table 86. Switching characteristics for NAND Flash write cycles<sup>(1)</sup>

## 5.3.27 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in *Table 87* for DCMI are derived from tests performed under the ambient temperature,  $f_{HCLK}$  frequency and  $V_{DD}$  supply voltage summarized in *Table 13*, with the following configuration:

- PCK polarity: falling
- VSYNC and HSYNC polarity: high
- Data format: 14 bits

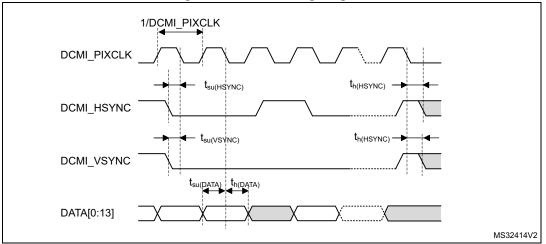
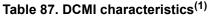


Figure 72. DCMI timing diagram



Symbol	Parameter	Min	Max	Unit
	Frequency ratio DCMI_PIXCLK/f <sub>HCLK</sub>	-	0.4	
DCMI_PIXCLK	Pixel clock input	-	54	MHz
D <sub>pixel</sub>	Pixel clock input duty cycle	30	70	%



Symbol	Parameter	Min	Мах	Unit	
t <sub>su(DATA)</sub>	Data input setup time	2.5	-		
t <sub>h(DATA)</sub>	Data hold time	1	-		
<sup>t</sup> su(HSYNC) <sup>,</sup> t <sub>su(VSYNC)</sub>	HSYNC/VSYNC input setup time	2	-	ns	
t <sub>h(HSYNC)</sub> , t <sub>h(VSYNC)</sub>	HSYNC/VSYNC input hold time	0.5	-		

Table 87. DCMI characteristics<sup>(1)</sup> (continued)

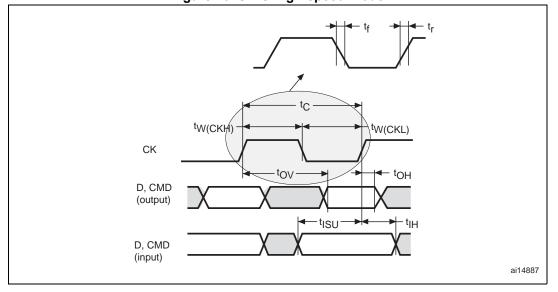
1. Guaranteed by characterization.

## 5.3.28 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 88* are derived from tests performed under ambient temperature,  $f_{PCLKx}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 14* with the following configuration:

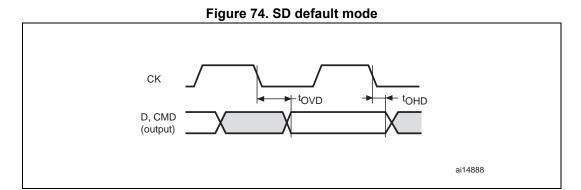
- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>

Refer to Section 5.3.16: I/O port characteristics for more details on the input/output characteristics.



### Figure 73. SDIO high-speed mode





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PP</sub>	Clock frequency in data transfer mode		0		48	MHz
	SDIO_CK/f <sub>PCLK2</sub> frequency ratio		-	-	8/3	-
t <sub>W(CKL)</sub>	Clock low time	f <sub>PP</sub> = 48 MHz	8.5	9	-	ns
t <sub>W(CKH)</sub>	Clock high time $f_{PP} = 48 \text{ MHz}$		8.3	10	-	115
CMD, D inpu	uts (referenced to CK) in MMC and SD HS mod	9				
t <sub>ISU</sub>	Input setup time HS	f <sub>PP</sub> = 48 MHz	3	-	-	200
t <sub>IH</sub>	Input hold time HS f <sub>PP</sub> = 48 MHz 0		0	-	-	ns
CMD, D out	outs (referenced to CK) in MMC and SD HS mo	de				
t <sub>OV</sub>	Output valid time HS	f <sub>PP</sub> = 48 MHz	-	4.5	6	20
t <sub>OH</sub>	Output hold time HS	f <sub>PP</sub> = 48 MHz	1	-	-	ns
CMD, D inpu	its (referenced to CK) in SD default mode					
t <sub>ISUD</sub>	Input setup time SD	f <sub>PP</sub> = 24 MHz	1.5	-	-	20
t <sub>IHD</sub>	Input hold time SD	f <sub>PP</sub> = 24 MHz	0.5	-	-	ns
CMD, D out	outs (referenced to CK) in SD default mode			·		•
t <sub>OVD</sub>	Output valid default time SD	f <sub>PP</sub> = 24 MHz	-	4.5	7	200
t <sub>OHD</sub>	Output hold default time SD	f <sub>PP</sub> = 24 MHz	0.5	-	-	ns

## Table 88. Dynamic characteristics: SD / MMC characteristics<sup>(1)</sup>

1. Guaranteed by characterization.

## 5.3.29 RTC characteristics

### Table 89. RTC characteristics

S	ymbol	Parameter	Conditions	Min	Мах
	-	f <sub>PCLK1</sub> /RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-



## 6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK is an ST trademark.

## 6.1 WLCSP90 package information

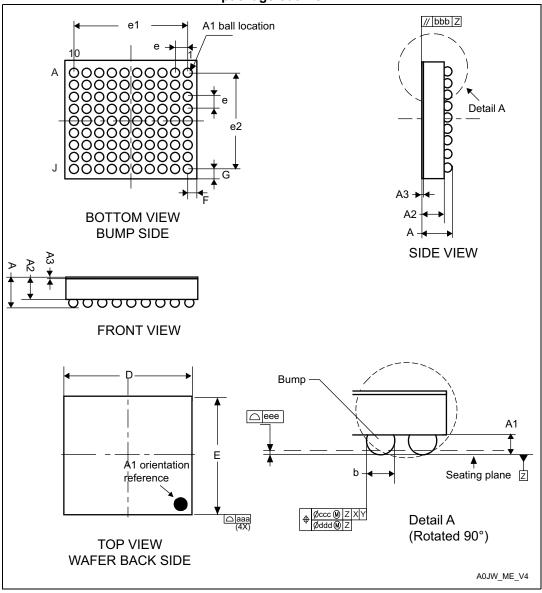


Figure 75. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package outline

1. Drawing is not to scale.



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		раска	je mechanic			
Symbol		millimeters			inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max
А	0.540	0.570	0.600	0.0213	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	-	0.380	-	-	0.0150	-
A3 <sup>(2)</sup>	-	0.025	-	-	0.0010	-
b <sup>(3)</sup>	0.240	0.270	0.300	0.0094	0.0106	0.0118
D	4.188	4.223	4.258	0.1649	0.1663	0.1676
E	3.934	3.969	4.004	0.1549	0.1563	0.1576
е	-	0.400	-	-	0.0157	-
e1	-	3.600	-	-	0.1417	-
e2	-	3.200	-	-	0.1260	-
F	-	0.3115	-	-	0.0123	-
G	-	0.3845	-	-	0.0151	-
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ссс	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

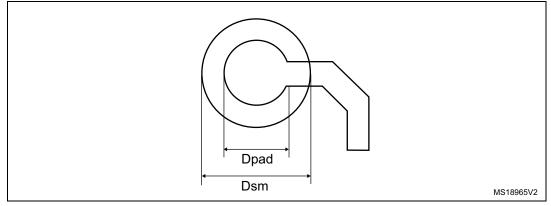
## Table 90. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. Back side coating.

3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

# Figure 76. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale recommended footprint





Dimension	Recommended values			
Pitch	0.4 mm			
Dpad	260 μm max. (circular) 220 μm recommended			
Dsm	300 μm min. (for 260 μm diameter pad)			
PCB pad design	Non-solder mask defined via underbump allowed			

 Table 91. WLCSP90 recommended PCB design rules

## **Device marking for WLCSP90**

The following figure gives an example of topside marking and ball A1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

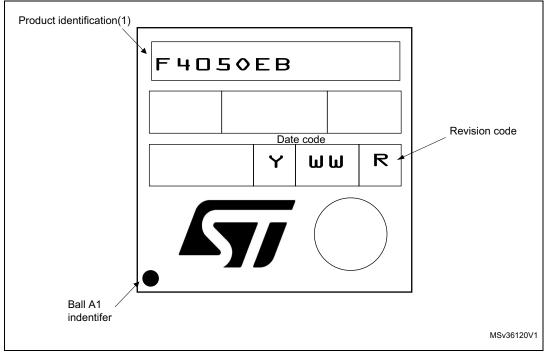


Figure 77. WLCSP90 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 6.2 LQFP64 package information

SEATING PLANE С <[₽] 0.25 mm GAUGE PLANE ¥ Ł Ā D Łκ D1 L1 D3 48 33 32 49 b ШШШ <u>-</u> 17 64 <u>₩₩₩₩₩₩₩₩₩₩₩₩₩₩₩</u> 16 PIN 1 IDENTIFICATION 1 5W\_ME\_V3

Figure 78. LQFP64 – 64-pin, 10 x 10 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 92. LQFP64 – 64-pin 10 x 10 mm low-profile quad flat package
mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
с	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

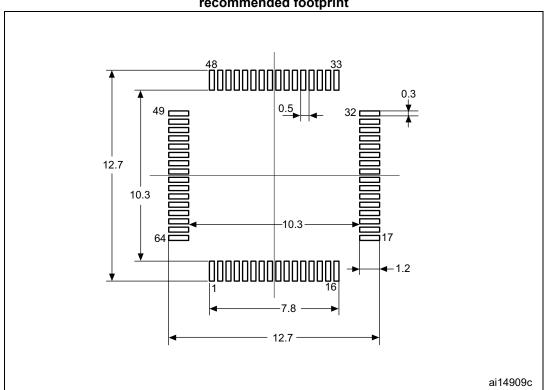


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Symbol		millimeters		inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
E3	-	7.500	-	-	0.2953	-
е	-	0.500	-	-	0.0197	-
К	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
CCC	-	-	0.080	-	-	0.0031

# Table 92. LQFP64 – 64-pin 10 x 10 mm low-profile quad flat package mechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.





1. Dimensions are in millimeters.



#### **Device marking for LQFP64**

The following figure gives an example of topside marking and pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

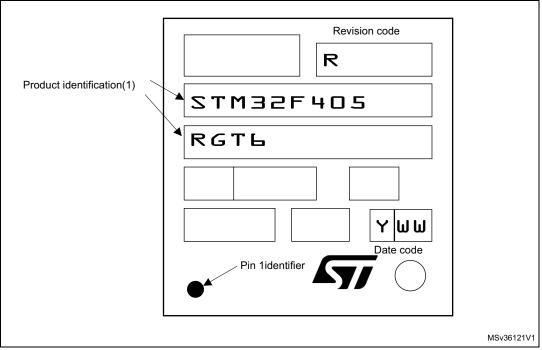


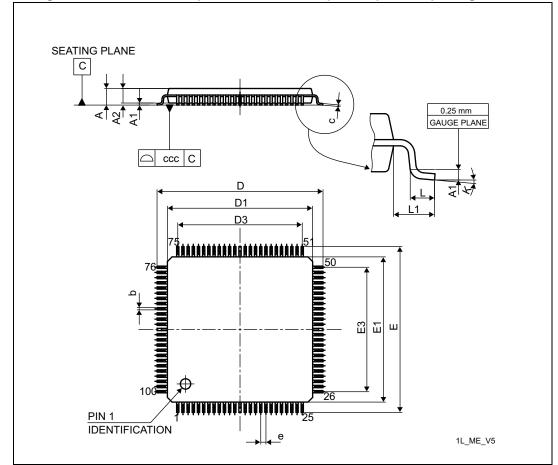
Figure 80. LPQF64 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 6.3 LQFP100 package information

Figure 81. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 93. LQFP100 – 100-pin, 14 x 14 mm low-profile quad flat package
mechanical data <sup>(1)</sup>

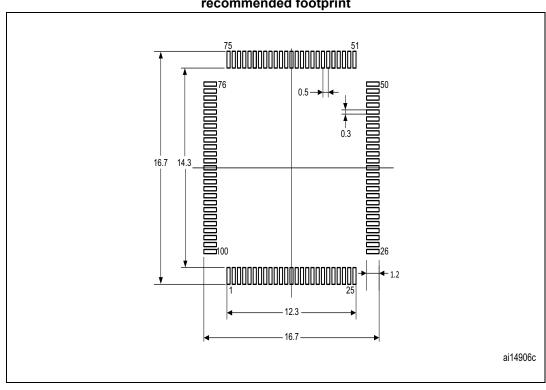
Symbol		millimeters		inches		
	Min	Тур	Мах	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.80	16.000	16.200	0.6220	0.6299	0.6378

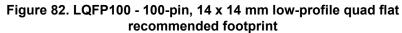


meenanour auta (continued)							
Symbol		millimeters		inches	inches		
	Min	Тур	Мах	Min	Тур	Max	
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591	
E3	-	12.000	-	-	0.4724	-	
е	-	0.500	-	-	0.0197	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0°	3.5°	7°	0°	3.5°	7°	
CCC	-	-	0.080	-	-	0.0031	

# Table 93. LQFP100 – 100-pin, 14 x 14 mm low-profile quad flat package mechanical data<sup>(1)</sup> (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.





1. Dimensions are expressed in millimeters.

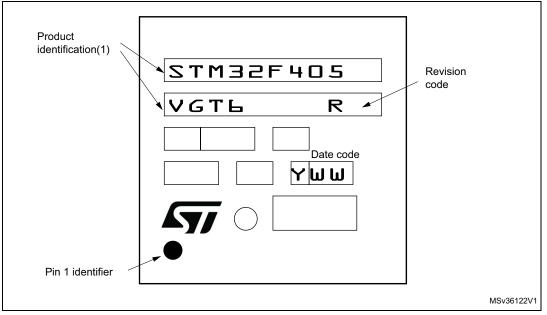


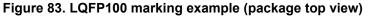
#### **Device marking for LFP100**

The following figure gives an example of topside marking and pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.



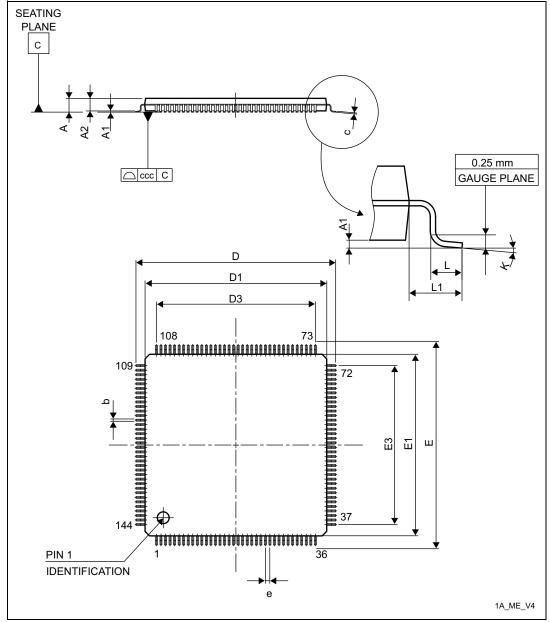


 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 6.4 LQFP144 package information

Figure 84. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.

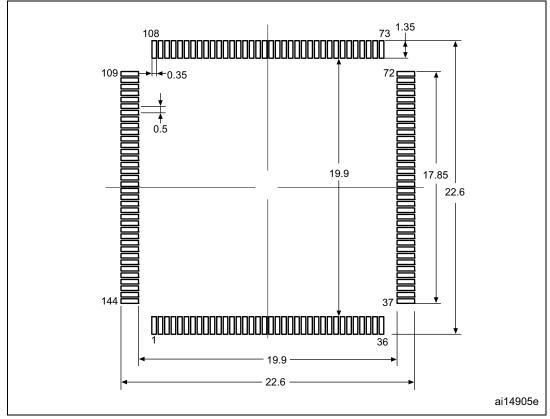


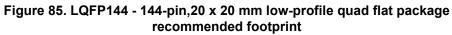
Symbol		millimeters			inches <sup>(1)</sup>	
	Min	Тур	Мах	Min	Тур	Мах
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
с	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.874
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.689	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ссс	-	-	0.080	-	-	0.0031

# Table 94. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat packagemechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.







1. Dimensions are in millimeters.

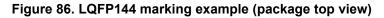


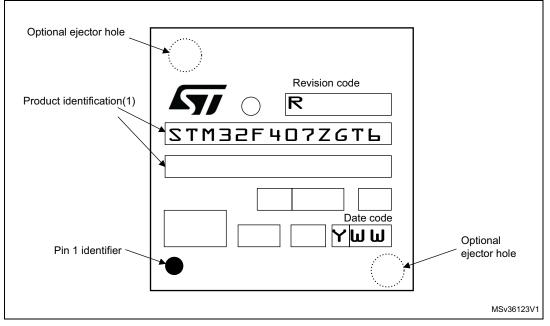
#### **Device marking for LQFP144**

The following figure gives an example of topside marking and pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 6.5 UFBGA176+25 package information

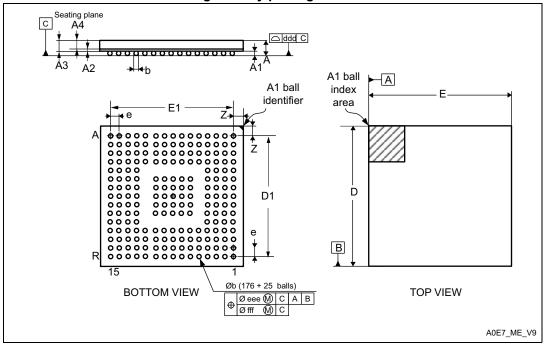


Figure 87. UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline

1. Drawing is not to scale.

## Table 95. UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitchball grid array mechanical data

Symbol		millimeters		inches <sup>(1)</sup>		
	Min	Тур	Мах	Min	Тур	Мах
А	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.130	-	-	0.0051	-
A3	-	0.450	-	-	0.0177	-
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	9.100	-	-	0.3583	-
E	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	9.100	-	-	0.3583	-
е	-	0.650	-	-	0.0256	-
Z	-	0.450	-	-	0.0177	-
ddd	-	-	0.080	-	-	0.0031



Table 95. UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch	
ball grid array mechanical data (continued)	

Symbol		millimeters			inches <sup>(1)</sup>			
Symbol	Min	Тур	Мах	Min	Тур	Max		
eee	-	-	0.150	-	-	0.0059		
fff	-	-	0.050	-	-	0.0020		

1. Values in inches are converted from mm and rounded to 4 decimal digits.

# Figure 88. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array recommended footprint

OOOOOOOOOOOOOOOOOOOOOOOOOOOOOOOOOOOO
--------------------------------------

#### Table 96. UFBGA176+2 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values		
Pitch	0.65		
Dpad	0.300 mm		
Dsm	0.400 mm typ. (depends on the soldermask registration tolerance)		

Note:

Non solder mask defined (NSMD) pads are recommended.
 4 to 6 mils solder paste screen printing process.
 Stencil opening is 0.300 mm.
 Stencil thickness is between 0.100 mm and 0.125 mm.
 Pad trace width is 0.100 mm.



## **Device marking for UFBGA176+25**

The following figure gives an example of topside marking and ball A 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

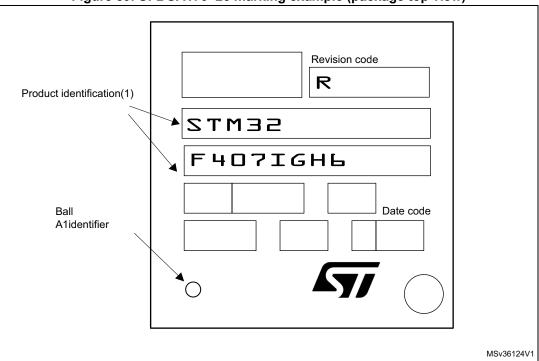


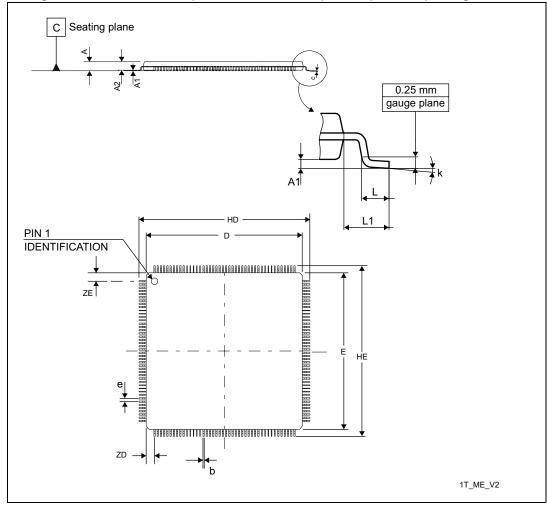
Figure 89. UFBGA176+25 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



## 6.6 LQFP176 package information

Figure 90. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package outline



1. Drawing is not to scale.

## Table 97. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package mechanical data

Symbol		millimeters		inches <sup>(1)</sup>		
	Min	Тур	Мах	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488
HD	25.900	-	26.100	1.0197	-	1.0276



mechanical data (continued)							
Symbol		millimeters		inches <sup>(1)</sup>			
	Min	Тур	Мах	Min	Тур	Max	
ZD	-	1.250	-	-	0.0492	-	
Е	23.900	-	24.100	0.9409	-	0.9488	
HE	25.900	-	26.100	1.0197	-	1.0276	
ZE	-	1.250	-	-	0.0492	-	
е	-	0.500	-	-	0.0197	-	
L <sup>(2)</sup>	0.450	-	0.750	0.0177	-	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0°	-	7°	0°	-	7°	
CCC	-	-	0.080	-	-	0.0031	

# Table 97. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat packagemechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. L dimension is measured at gauge plane at 0.25 mm above the seating plane.



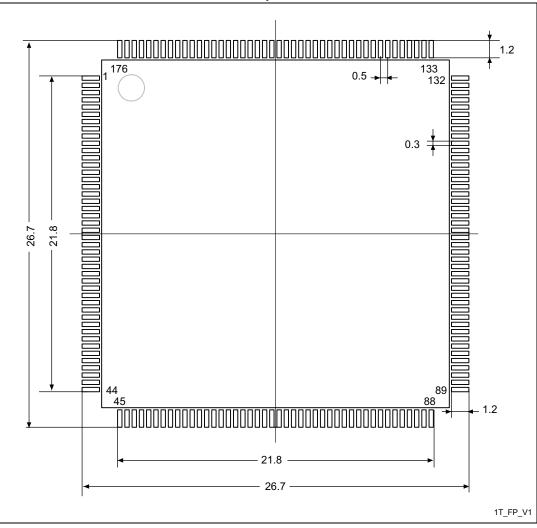


Figure 91. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat recommended footprint

1. Dimensions are expressed in millimeters.

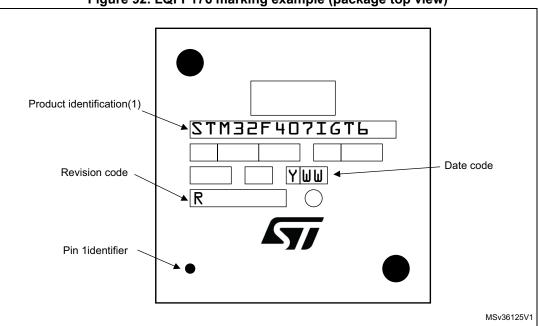


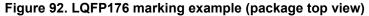
#### **Device marking for LQFP176**

The following figure gives an example of topside marking and pin 1 position identifier location.

The printed markings may differ depending on the supply chain.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



### 6.7 Thermal characteristics

The maximum chip-junction temperature,  $T_J$  max, in degrees Celsius, may be calculated using the following equation:

 $T_J \max = T_A \max + (P_D \max x \Theta_{JA})$ 

Where:

- T<sub>A</sub> max is the maximum ambient temperature in °C,
- $\Theta_{JA}$  is the package junction-to-ambient thermal resistance, in °C/W,
- P<sub>D</sub> max is the sum of P<sub>INT</sub> max and P<sub>I/O</sub> max (P<sub>D</sub> max = P<sub>INT</sub> max + P<sub>I/O</sub>max),
- P<sub>INT</sub> max is the product of I<sub>DD</sub> and V<sub>DD</sub>, expressed in Watts. This is the maximum chip internal power.

P<sub>I/O</sub> max represents the maximum power dissipation on output pins where:

 $\mathsf{P}_{\mathsf{I}/\mathsf{O}} \max = \Sigma \left( \mathsf{V}_{\mathsf{OL}} \times \mathsf{I}_{\mathsf{OL}} \right) + \Sigma ((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) \times \mathsf{I}_{\mathsf{OH}}),$ 

taking into account the actual V\_{OL} / I\_{OL} and V\_{OH} / I\_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient LQFP64 - 10 × 10 mm / 0.5 mm pitch	46	
	<b>Thermal resistance junction-ambient</b> LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	
0	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	°C/W
$\Theta_{JA}$	<b>Thermal resistance junction-ambient</b> LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	C/W
	Thermal resistance junction-ambient UFBGA176 - 10× 10 mm / 0.65 mm pitch	39	
	Thermal resistance junction-ambient WLCSP90 - 0.400 mm pitch	38.1	

Table 98. Package thermal characteristics

### **Reference document**

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.



## 7 Ordering information

Example:	STM32	F	405 R	Е	т	6 xxx
Device family						
STM32 = Arm-based 32-bit microcontroller						
STM32 - Ann-based 32-bit microcontroller						
Product type						
F = general-purpose						
Device subfamily						
405 = STM32F40xxx, connectivity						
407= STM32F40xxx, connectivity, camera interface, Ethernet						
Pin count						
R = 64 pins						
O = 90 pins						
V = 100 pins						
Z = 144 pins						
I = 176 pins						
Flash memory size						
E = 512 Kbytes of Flash memory						
G = 1024 Kbytes of Flash memory						
Package						
T = LQFP						
H = UFBGA						
Y = WLCSP						
Temperature range						
6 = Industrial temperature range, $-40$ to 85 °C.						
7 = Industrial temperature range, $-40$ to $105 ^{\circ}$ C.						
Options						

xxx = programmed parts

TR = tape and reel

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

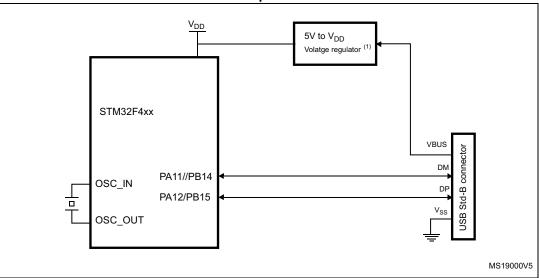


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## Appendix A Application block diagrams

### A.1 USB OTG full speed (FS) interface solutions

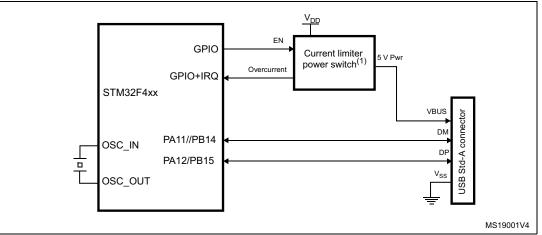
Figure 93. USB controller configured as peripheral-only and used in Full speed mode



1. External voltage regulator only needed when building a  $V_{\mbox{BUS}}$  powered device.

2. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.

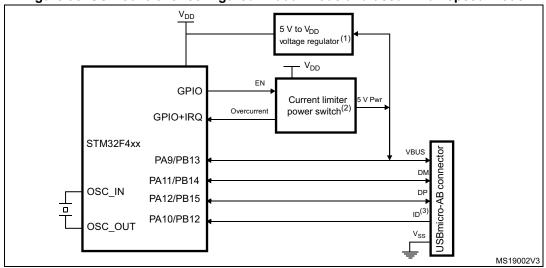




 The current limiter is required only if the application has to support a V<sub>BUS</sub> powered device. A basic power switch can be used if 5 V are available on the application board.

2. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.





#### Figure 95. USB controller configured in dual mode and used in full speed mode

- 1. External voltage regulator only needed when building a  $\mathrm{V}_{\mathrm{BUS}}$  powered device.
- The current limiter is required only if the application has to support a V<sub>BUS</sub> powered device. A basic power switch can be used if 5 V are available on the application board.
- 3. The ID pin is required in dual role only.
- 4. The same application can be developed using the OTG HS in FS mode to achieve enhanced performance thanks to the large Rx/Tx FIFO and to a dedicated DMA controller.



### A.2 USB OTG high speed (HS) interface solutions

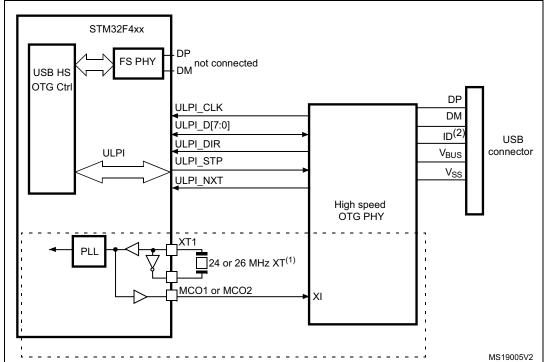


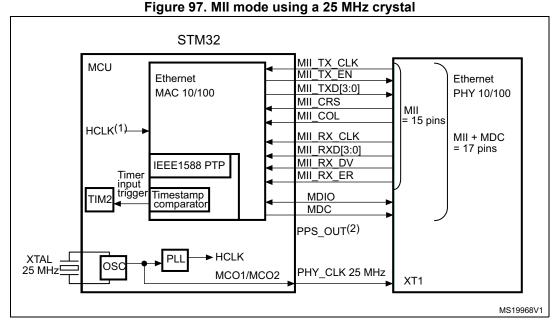
Figure 96. USB controller configured as peripheral, host, or dual-mode and used in high speed mode

 It is possible to use MCO1 or MCO2 to save a crystal. It is however not mandatory to clock the STM32F40xxx with a 24 or 26 MHz crystal when using USB HS. The above figure only shows an example of a possible connection.

2. The ID pin is required in dual role only.

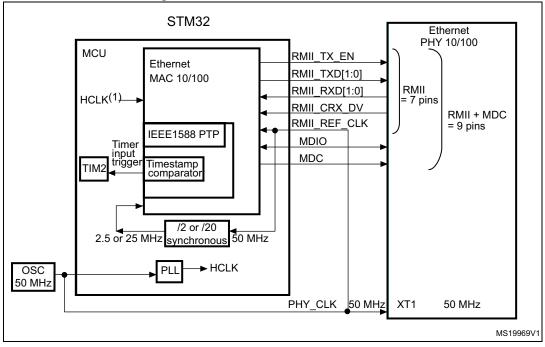


### A.3 Ethernet interface solutions



1.  $f_{\mbox{HCLK}}$  must be greater than 25 MHz.

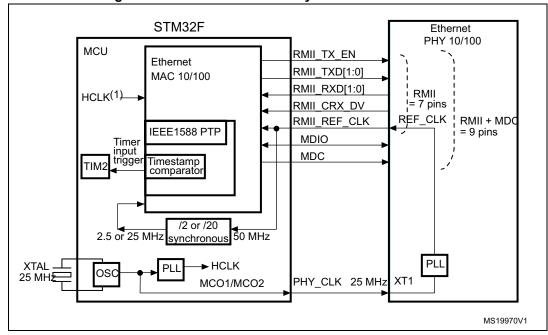
2. Pulse per second when using IEEE1588 PTP optional signal.



#### Figure 98. RMII with a 50 MHz oscillator

1. f<sub>HCLK</sub> must be greater than 25 MHz.







1. f<sub>HCLK</sub> must be greater than 25 MHz.

2. The 25 MHz (PHY\_CLK) must be derived directly from the HSE oscillator, before the PLL block.



# 8 Revision history

Date	Revision	Changes
15-Sep-2011	1	Initial release.
24-Jan-2012	2	Added WLCSP90 package on cover page. Renamed USART4 and USART5 into UART4 and UART5, respectively. Updated number of USB OTG HS and FS in <i>Table 2: STM32F405xx</i> and <i>STM32F407xx: features and peripheral counts.</i> Updated <i>Figure 3: Compatible board design between</i> <i>STM32F10xx/STM32F2/STM32F40xx for LQFP144 package</i> and <i>Figure 4: Compatible board design between</i> <i>STM32F10xx/STM32F2/STM32F40xx for LQFP144 package</i> and <i>Figure 4: Compatible board design between</i> <i>STM32F40xxx for LQFP176 and BGA176 packages,</i> and removed note 1 and 2. Updated <i>Section 2.2.9: Flexible static memory controller (FSMC).</i> Modified I/Os used to reprogram the Flash memory for CAN2 and USB OTG FS in <i>Section 2.2.13: Boot modes.</i> Updated note in <i>Section 2.2.14: Power supply schemes.</i> PDR_ON no more available on LQFP100 package. Updated <i>Section 2.2.16: Voltage regulator.</i> Updated condition to obtain a minimum supply voltage of 1.7 V in the whole document. Renamed USART4/5 to UART4/5 and added LIN and IrDA feature for UART4 and UART5 in <i>Table 5: USART feature comparison.</i> Removed support of I2C for OTG PHY in <i>Section 2.2.30: Universal</i> <i>serial bus on-the-go full-speed (OTG_FS).</i> Added <i>Table 6: Legend/abbreviations used in the pinout table.</i> <i>Table 7: STM32F40xxx pin and ball definitions:</i> replaced V <sub>SS_3</sub> , V <sub>SS_4</sub> , and V <sub>SS_8</sub> 8 by V <sub>SS</sub> ; reformatted <i>Table 7: STM32F40xxx pin and</i> <i>ball definitions</i> to better highlight I/O structure, and alternate functions versus additional functions; signal corresponding to LQFP100 pin 99 changed from PDR_ON to V <sub>SS</sub> ; EVENTOUT added in the list of alternate functions for all I/OS; ADC3_IN8 added as alternate functions for PD11 and PD12, respectively; PH10 alternate function TIM15_CH1_ETR renamed TIM5_CH1; updated PA4 and PA5 I/O structure to TTa. Removed OTG_HS_SCL, OTG_HS_SDA, OTG_FS_INTN in <i>Table 7:</i> <i>STM32F40xxx pin and ball definitions</i> and <i>Table 9: Alternate function</i> <i>mapping.</i> Changed TCM data RAM to CCM data RAM in <i>Figure 18:</i> <i>STM32F40xxx pin and ball de</i>

### Table 99. Document revision history



Date	Revision	Changes
Date 24-Jan-2012	Revision 2 (continued)	Changes         Added V <sub>12</sub> in Table 19: Embedded reset and power control block characteristics.         Updated Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled) and Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM. Added Figure , Figure 25, Figure 26, and Figure 27.         Updated Table 22: Typical and maximum current consumption in Sleep mode and removed Note 1.         Updated Table 23: Typical and maximum current consumptions in Stop mode and rable 24: Typical and maximum current consumptions in Standby mode, Table 27: Switching output I/O current consumptions in V <sub>BAT</sub> mode, and Table 27: Switching output I/O current consumptions, and updated Table 28: Peripheral current consumption and Note 2.         Changed f <sub>HSE_ext</sub> to 50 MHz and t <sub>r(HSE)</sub> /t <sub>t(HSE)</sub> maximum value in Table 30: High-speed external user clock characteristics.         Added C <sub>in(LSE)</sub> in Table 31: Low-speed external user clock characteristics.         Updated maximum PLL input clock frequency, removed related note, and deleted jitter for MCO for RMII Ethernet typical value in Table 36: Main PLL characteristics. Updated maximum PLLI2S input clock frequency and removed related note in Table 37: PLLI2S (audio PLL) characteristics.         Updated Section : Flash memory to specify that the devices are shipped to customers with the Flash memory erased. Updated Table 39: Flash memory characteristics, and added t <sub>ME</sub> in Table 40: Flash memory programming.         Updated Table 56: IZS dynamic characteristics         Updated Table 56: I



Date	Revision	Changes
24-Jan-2012	2 (continued)	Updated Table 61: USB HS clock timing parameters Updated Table 67: ADC characteristics. Updated Table 68: ADC accuracy at f <sub>ADC</sub> = 30 MHz. Updated Note 1 in Table 74: DAC characteristics. Section 5.3.26: FSMC characteristics: updated Table 75 to Table 86, changed C <sub>L</sub> value to 30 pF, and modified FSMC configuration for asynchronous timings and waveforms. Updated Figure 59: Synchronous multiplexed PSRAM write timings. Updated Table 98: Package thermal characteristics. Appendix A.1: USB OTG full speed (FS) interface solutions: modified Figure 93: USB controller configured as peripheral-only and used in Full speed mode added Note 2, updated Figure 94: USB controller configured as host-only and used in full speed mode and added Note 2, changed Figure 95: USB controller configured in dual mode and used in full speed mode and added Note 3. Appendix A.2: USB OTG high speed (HS) interface solutions: removed figures USB OTG HS device-only connection in FS mode and USB OTG HS host-only connection in FS mode, and updated Figure 96: USB controller configured as peripheral, host, or dual-mode and used in high speed mode and added Note 2. Added Appendix A.3: Ethernet interface solutions.

Table 99. Document revision history (continued)
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Table 99. Document revision history (continued)		
Date	Revision	Changes
31-May-2012	3	Updated Figure 5: STM32F40xxx block diagram and Figure 7: Power supply supervisor interconnection with internal reset OFF Added SDIO, added notes related to FSMC and SPI/I2S in Table 2: STM32F405xx and STM32F407xx: features and peripheral counts. Starting from Silicon revision Z, USB OTG full-speed interface is now available for all STM32F405xx devices. Added full information on WLCSP90 package together with corresponding part numbers. Changed number of AHB buses to 3. Modified available Flash memory sizes in Section 2.2.4: Embedded Flash memory. Modified available Flash memory sizes in Section 2.2.4: Embedded Flash memory. Modified number of maskable interrupt channels in Section 2.2.10: Nested vectored interrupt controller (NVIC). Updated case of Regulator ON/internal reset ON, Regulator ON/internal reset OFF, and Regulator OFF/internal reset ON in Section 2.2.16: Voltage regulator. Updated standby mode description in Section 2.2.19: Low-power modes. Added Note 1 below Figure 16: STM32F40xxx UFBGA176 ballout. Added Note 1 below Figure 16: STM32F40xxx WLCSP90 ballout. Updated Table 7: STM32F40xxx pin and ball definitions. Added Table 8: FSMC pin definition. Removed OTG_HS_INTN alternate function in Table 7: STM32F40xxx pin and ball definitions and Table 9: Alternate function mapping. Replaced JTRST by NJTRST, removed ETH_RMII_TX_CLK, and modified I2S3ext_SD on PC11 in Table 9: Alternate function mapping. Added Table 10: register boundary addresses. Updated Figure 18: STM32F40xxx memory map. Updated V <sub>DDA</sub> and V <sub>REF+</sub> decoupling capacitor in Figure 21: Power supply scheme. Added power dissipation maximum value for WLCSP90 in Table 14: General operating conditions. Updated V <sub>POR/PDR</sub> in Table 19: Embedded reset and power control block characteristics. Updated notes in Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM, and Table 22: Typical and maximum current consumption in Sleep mode. Updated maximum current consum

Table 99. Document revision history (continued)



Date	Revision	Changes
Date 31-May-2012	Revision 3 (continued)	Removed $f_{HSE\_ext}$ typical value in <i>Table 30: High-speed external user clock characteristics</i> . Updated <i>Table 32: HSE 4-26 MHz oscillator characteristics</i> and <i>Table 33: LSE oscillator characteristics (f_{LSE} = 32.768 kHz)</i> . Added $f_{PLL48\_OUT}$ maximum value in <i>Table 36: Main PLL characteristics</i> . Modified equation 1 and 2 in <i>Section 5.3.11: PLL spread spectrum clock generation (SSCG) characteristics</i> . Updated <i>Table 39: Flash memory characteristics, Table 40: Flash memory programming,</i> and <i>Table 41: Flash memory programming with VPP</i> . Updated <i>Section : Output driving current.</i> <i>Table 56: I<sup>2</sup>C characteristics: Note 4</i> updated and applied to $t_{h(SDA)}$ in Fast mode, and removed note 4 related to $t_{h(SDA)}$ minimum value. Updated <i>Table 67: ADC characteristics.</i> Updated note concerning ADC
		accuracy vs. negative injection current below Table 68: ADC accuracy at $f_{ADC} = 30$ MHz. Added WLCSP90 thermal resistance in Table 98: Package thermal characteristics. Updated Table 90: WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data. Updated Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline and Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data. Added Figure 91: LQFP176 - 176-pin, 24 x 24 mm low profile quad flat recommended footprint. Removed 256 and 768 Kbyte Flash memory density from Table : .

Table 99. Document revision history (continued)



Table 99. Document revision history (continued)		
Date	Revision	Changes
Date		
		Corrected wrong reference manual in Section 2.2.28: Ethernet MAC interface with dedicated DMA and IEEE 1588 support Updated Table 15: Limitations depending on the operating power supply range Updated Table 24: Typical and maximum current consumptions in
		mode Updated Table 37: PLLI2S (audio PLL) characteristics Updated Table 44: EMI characteristics
		Updated Table 49: Output voltage characteristics Updated Table 51: NRST pin characteristics Updated Table 55: SPI dynamic characteristics Updated Table 56: I2S dynamic characteristics Deleted Table 59
		Updated <i>Table 62: ULPI timing</i> Updated <i>Figure 46: Ethernet SMI timing diagram</i>



Date	Revision	Changes
04-Jun-2013	4 (continued)	Updated Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline Updated Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data Updated Section 2: Description Updated footnote <sup>(3)</sup> in Table 2: STM32F405xx and STM32F407xx: features and peripheral counts. Updated Figure 3: Compatible board design between STM32F10xx/STM32F2/STM32F40xx for LQFP144 package Updated Figure 3: Compatible board design between STM32F40xx/STM32F2/STM32F40xx for LQFP144 package Updated Section 2.2.14: Power supply schemes Updated Section 2.2.15: Power supply schemes Updated Section 2.2.16: Voltage regulator, including footnote <sup>(2)</sup> . Updated Table 15: Limitations depending on the operating power supply range, including footnote <sup>(3)</sup> . Updated footnote <sup>(1)</sup> in Table 67: ADC characteristics. Updated footnote <sup>(1)</sup> in Table 67: ADC characteristics. Updated footnote <sup>(1)</sup> in Table 67: ADC characteristics. Updated footnote <sup>(2)</sup> in Table 68: ADC accuracy at f <sub>ADC</sub> = 30 MHz. Updated footnote <sup>(2)</sup> in Table 68: ADC accuracy at f <sub>ADC</sub> = 30 MHz. Updated footnote <sup>(2)</sup> of Figure 21: Power supply scheme. Replaced Figure 9: Regulator ON/OFF and internal reset ON/OFF Added Section 2.2.17: Regulator ON/OFF and internal reset ON/OFF Added Section 2.2.17: Regulator ON/OFF and internal reset ON/OFF Added TeVENTOUT" as alternate function mapping Replaced respectively "I2S3S_WS" by "I2S3_WS", "I2S3S_CK" by "I2S3_CK" and "FSMC_BLN1" by "FSMC_NBL1" in Table 9: Alternate function mapping. Removed the following sentence from Section : I2C interface characteristics: "Unless otherwise specified, the parameters given in Table 56 are derived from tests performed under the ambient temperature, f <sub>PCLK1</sub> frequency and V <sub>DD</sub> supply voltage conditions. Removed the following sentence from Section : I2C interface characteristics: "Unless otherwise specified, the parameters given in Table 56 are derived from tests performed under the ambi

Table 99. Document revision history (cor	ntinued)
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Date	Revision	Changes
		Updated Figure 6: Multi-AHB matrix.
		Updated Figure 7: Power supply supervisor interconnection with internal reset OFF
		Changed 1.2 V to V <sub>12</sub> in Section : Regulator OFF
		Updated LQFP176 pin 48.
		Updated Section 1: Introduction.
		Updated Section 2: Description.
		Updated operating voltage in <i>Table 2:</i> STM32F405xx and STM32F407xx: features and peripheral counts.
		Updated Note 1.
		Updated Section 2.2.15: Power supply supervisor.
		Updated Section 2.2.16: Voltage regulator.
		Updated Figure 9: Regulator OFF.
		Updated Table 3: Regulator ON/OFF and internal reset ON/OFF availability.
		Updated Section 2.2.19: Low-power modes.
		Updated Section 2.2.20: V <sub>BAT</sub> operation.
		Updated Section 2.2.22: Inter-integrated circuit interface (I <sup>2</sup> C).
		Updated pin 48 in Figure 15: STM32F40xxx LQFP176 pinout.
		Updated Table 6: Legend/abbreviations used in the pinout table.
		Updated Table 7: STM32F40xxx pin and ball definitions.
		Updated Table 14: General operating conditions.
04-Jun-2013	4	Updated Table 15: Limitations depending on the operating power
04 0011 2010	(continued)	supply range.
		Updated Section 5.3.7: Wakeup time from low-power mode.
		Updated Table 34: HSI oscillator characteristics.
		Updated Section 5.3.15: I/O current injection characteristics.
		Updated Table 48: I/O static characteristics.
		Updated Table 51: NRST pin characteristics.
		Updated Table 56: I <sup>2</sup> C characteristics.
		Updated Figure 39: I <sup>2</sup> C bus AC waveforms and measurement circuit.
		Updated Section 5.3.19: Communications interfaces.
		Updated Table 67: ADC characteristics.
		Added Table 70: Temperature sensor calibration values.
		Added Table 73: Internal reference voltage calibration values.
		Updated Section 5.3.26: FSMC characteristics.
		Updated Section 5.3.28: SD/SDIO MMC card host interface (SDIO) characteristics.
		Updated Table 23: Typical and maximum current consumptions in Stormode.
		Updated Section : SPI interface characteristics included Table 55.
		Updated Section : I2S interface characteristics included Table 56.
		Updated Table 64: Dynamic characteristics: Ethernet MAC signals for SMI.
		Updated Table 66: Dynamic characteristics: Ethernet MAC signals for MII.

Table 99.	Document	revision	historv	(continued)
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Date	Revision	Changes
04-Jun-2013 4 (continued)		Updated Table 64: Dynamic characteristics: Ethernet MAC signals for SMI. Updated Table 66: Dynamic characteristics: Ethernet MAC signals for MII. Updated Table 79: Synchronous multiplexed NOR/PSRAM read
	timings. Updated Table 80: Synchronous multiplexed PSRAM write timings. Updated Table 81: Synchronous non-multiplexed NOR/PSRAM read timings. Updated Table 82: Synchronous non-multiplexed PSRAM write timings.	
		Updated Section 5.3.27: Camera interface (DCMI) timing specifications including Table 87: DCMI characteristics and addition of Figure 72: DCMI timing diagram. Updated Section 5.3.28: SD/SDIO MMC card host interface (SDIO)
		<i>characteristics</i> including <i>Table</i> 88. Updated <i>Chapter Figure</i> 9.

Table 99. Document revision history (continued)



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Date
Date 06-Mar-2015

Table 99.	. Document	revision	history	(continued)	
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Date	Revision	Changes		
22-Oct-2015	6	In the whole document, updated notes related to values guaranteed by design or by characterization. Updated <i>Table 34: HSI oscillator characteristics</i> . Changed $f_{VCO_OUT}$ minimum value and VCO freq to 100 MHz in <i>Table 36: Main PLL characteristics</i> and <i>Table 37: PLLI2S (audio PLL) characteristics</i> . Updated <i>Figure 39: SPI timing diagram - slave mode and CPHA = 0</i> . Updated <i>Figure 53: 12-bit buffered /non-buffered DAC</i> . Removed note 1 related to better performance using a restricted V <sub>DD</sub> range in <i>Table 68: ADC accuracy at f<sub>ADC</sub> = 30 MHz</i> . Upated <i>Figure 84: LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline</i> . Updated <i>Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline</i> and <i>Table 95: UFBGA176+25 ball, 10 x 10 x 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data</i> .		
16-Mar-2016	7	Updated Figure 2: Compatible board design STM32F10xx/STM32F2/STM32F40xxx for LQFP100 package. Updated  Vssx-Vss  in Table 11: Voltage characteristics to add V <sub>REF-</sub> . Added V <sub>REF-</sub> in Table 67: ADC characteristics. Updated Table 90: WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data.		

Table 99. Document revision history (continued)



Date	Revision	Changes
09-Sep-2016	8	Removed note 1 below <i>Figure 5: STM32F40xxx block diagram</i> . Updated definition of stresses above maximum ratings in <i>Section 5.2: Absolute maximum ratings</i> . Updated $t_{h(NSS)}$ in <i>Figure 39: SPI timing diagram - slave mode and CPHA = 0</i> and <i>Figure 40: SPI timing diagram - slave mode and CPHA = 1</i> . Added note related to optional marking and inset/upset marks in all package marking sections. Updated <i>Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline</i> and <i>Table 95:</i> <i>UFBGA176+25 ball, 10 x 10 x 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data.</i>
14-Aug-2020	9	<ul> <li>Renamed Section 2.2 and Section 7 into Functional overview and Ordering information, respectively.</li> <li>Added Arm logo and legal notice in Section 1: Introduction and updated Arm wordmark in the whole document. Removed USB certified logos.</li> <li>Updated camera interfaces for STM32F405OE in Table 2: STM32F405xx and STM32F407xx: features and peripheral counts.</li> <li>Added OTP memory in Features and Section 2.2.4: Embedded Flash memory.</li> <li>Changed random number generator to true random number generator in the whole document and updated Section 2.2.3: True random number generator (RNG).</li> <li>Added Note 1 related to UFBGA176 in Table 7: STM32F40xxx pin and ball definitions.</li> <li>Updated Section 5.2: Absolute maximum ratings introduction.</li> <li>Updated V<sub>PVD</sub> minimum value for PLS[2:0]=101 (falling edge) in Table 19: Embedded reset and power control block characteristics.</li> <li>Updated Note 1 in Table 34: HSI oscillator characteristics.</li> <li>Added reference to application note AN4899 in Section 5.3.16: I/O port characteristics.</li> <li>Replaced DCMI_PIXCK by DCMI_PIXCLK in Table 9: Alternate function mapping.</li> <li>Renamed Section 7 into Ordering information.</li> <li>Updated D1 in Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline.</li> </ul>



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